ITE



IDW '10 THE 17TH INTERNATIONAL DISPLAY WORKSHOPS

Workshops on

- LC Science and Technologies (LCT)
- Active Matrix Displays (AMD)
- FPD Manufacturing, Materials and Components (FMC)
- Plasma Displays (PDP)
- EL Displays and Phosphors (PH)
- Field Emission Display and CRT (FED)
- Organic LED Displays (OLED)
- 3D/Hyper-Realistic Displays and Systems (3D)
- Applied Vision and Human Factors (VHF)
- Projection and Large-Area Displays and Their Components (PRJ)
- Electronic Paper (EP)
- MEMS and Emerging Technologies for Future Displays and Devices (MEET)
- Display Electronic Systems (DES)
- Flexible Displays (FLX)

Topical Sessions on

- Touch Panels and Input Technologies (INP)
- Lighting Optics, Devices and Systems (LIT)

Final Program

Fukuoka International Congress Center Fukuoka, Japan December 1(Wed) – 3(Fri), 2010

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PROGRAM HIGHLIGHTS

Scientific and technological advances in research and development on information displays can be found at the 17th International Display Workshops (IDW '10). Features of the IDW '10 include the integration of the following fourteen workshops as well as two topical sessions focusing on recent progress of lighting and input technologies.

Workshops on

- LC Science and Technologies
- Active Matrix Displays
- · FPD Manufacturing, Materials and Components
- Plasma Displays
- EL Displays and Phosphors
- Field Emission Display and CRT
- Organic LED Displays
- 3D/Hyper-Realistic Displays and Systems
- Applied Vision and Human Factors
- Projection and Large-Area Displays and Their Components
- Electronic Paper
- MEMS and Emerging Technologies for Future Displays and Devices
- Display Electronic Systems
- Flexible Displays

Topical Sessions on

- Touch Panels and Input Technologies
- Lighting Optics, Devices and Systems

The three-day conference will feature 599 papers, including a keynote address, an invited address, 99 invited papers, 220 oral presentations, and 278 poster presentations. Following plenary session of keynote and invited addresses in the Wednesday morning, presentations will begin and continue in eight parallel oral sessions through Friday. Poster sessions and author interviews will enable participants to discuss topics in detail. IDW '10 will also present "IDW Best Paper Awards" and "IDW Outstanding Poster Paper Awards" based on paper originality and technical significance to information displays. Exhibits by universities and display industry-related businesses will also be featured from Wednesday to Friday in parallel with workshops. IDW '10 should be of interest to not only researchers and engineers, but also managers of companies and institutions in the display community.

Workshop on LC Science and Technologies (LCT)

Recent advances in LC materials and device technologies are presented. The sessions cover from fundamental studies to recent development in LCD technologies. New LC materials & modes including blue phase display, LC alignment processes, display measurement, fast-response LCDs, high performance LCDs and emerging new applications are discussed.

Workshop on Active Matrix Displays (AMD)

AMD is the workshop for the core technologies of most advanced FPD applications, covering the various technologies of Si-TFT, Oxide TFT, Organic TFT, OLED, integrated sensors, flexible devices and novel applications. It is recognized as one of the largest workshop in IDW. The recent trend in paper presentations tends to focus on Oxide TFT, which are expected to find applications in the next generation of OLED and flexible devices. This year, we devote seven for AMD alone, and three for joint sessions, which cover a broader range of device/process to applications. Given the expectations surrounding environmental aspects, a range of interesting paper presentations are expected.

Workshop on FPD Manufacturing, Materials and Components (FMC)

The FMC workshop covers the recent developments and achievements in the field of flat panel displays. The cutting-edge technologies of the optical films, color filters, LCD backlighting systems, optical components, manufacturing technologies, and measurement systems are highlighted. Recycling of FPD materials and environmental safety technologies are included as highlighted topics.

Workshop on Plasma Displays (PDP)

The PDP workshop consists of 15 oral and 10 poster presentations. Similar to the last year, there will be many excellent presentations on protecting layers. Improvements in conventional MgO, as well as the understanding of the high-efficiency and long-life operation of new materials including SrCaO, are investigated. We will have many presentations from China. Dr. Yan, in his invited talk, will introduce R&D as well as business trends in PDP activities in China. Other invited talks include presentations on 3D PDP from LG Electronics, green PDP from Samsung SDI, and improvement of picture quality of 2D/3D PDP from Panasonic. It should be noted that Pusan National University is going to introduce a high-resolution Quad-FHD PDP.

Workshop on EL Displays and Phosphors (PH)

This workshop covers the latest R&D achievements in inorganic ELDs, phosphors for emissive displays and solid-state illumination as well as LEDs. The workshop consists of invited talks, contributed papers and poster papers. These will present phosphors for LEDs, PDPs, ELDs, FEDs, lighting and computational approaches for phosphors including interesting topics such as quantum dot EL and synthesis techniques for phosphors.

Workshop on Field Emission Display and CRT (FED)

This workshop covers the entire field of CRT and field emission display technologies. Recent progress in various backlight units for LCD equipped with carbon nanotube (CNT) field emitter arrays is presented. Structures of field emitters with focusing electrodes, field emission characteristics and various field emitter materials, such as CNTs, HfN, and nanocrystalline silicon, are also discussed.

Workshop on Organic LED Displays (OLED)

This workshop includes recent developments in OLED materials, devices, display systems, solution process technologies and new device architecture. OLED materials and technologies based on printing methods are expected for large size and low cost applications. Device fabrication process and architecture for mass productions are also presented.

Workshop on 3D/Hyper-Realistic Displays and Systems (3D)

This workshop focuses on recent progress in 3D/hyper-realistic image systems and related visual technologies. It also covers stereoscopic/3D display, holography, 3D image quality, and 3D contents. This year, two sessions are held together with the "Display Electronic Systems (DES)" and "Applied Vision and Human Factors (VHF)" workshops. Invited talks include topics from the forefront of 3D imaging technologies, and recent research into advanced display systems.

Workshop on Applied Vision and Human Factors (VHF)

This workshop provides a forum for lively discussion of the latest academic and industrial R&D in the field of applied vision and human factors associated with display technology, covering a wide range from fundamental theory to commercial applications, including methods for improved contrast, multi-primary displays, color reproduction, dynamic characteristics, and the assessment and improvement of image quality and the viewing environment. This year sees four invited talks, held jointly with the DES and 3D workshops, on color reproduction, multi-primary displays, and the safety of 3D systems. Excluding Late News, there will be 29 oral presentations over eight sessions, plus 11 posters. A particular feature of this year's workshop is the number of topical papers related to color, including multi-primary displays.

Workshop on Projection and Large-Area Displays and Their Components (PRJ)

In this workshop, the latest technologies in the field of projection display will be discussed. Rapidly growing technologies such as pico-projectors with newly developed green laser and novel optical systems are highlighted. As laser technologies applied to projection displays become popular, new despeckling methods will be proposed. Also, near-eye and other applications based on projection technologies that are becoming a reality, and new methods are presented. Ongoing progress in the fields of large-area displays for applications such as 3D systems and digital signage will be discussed as well.

Workshop on Electronic Paper (EP)

This workshop focuses on current topics in electronic paper including rewritable paper, paper-like displays and flexible displays. There is currently an eager demand for developments in e-paper technologies due to the emergence of e-books, e-newspapers, electronic shelf labels, and other applications. Various novel technologies in electrophoretic, liquid crystal, electrowetting, electrochromic, liquid powder and toner display systems will be reported on. Systems, devices, materials, human factors and applications in this field are expected to be discussed.

Workshop on MEMS and Emerging Technologies for Future Displays and Devices (MEET)

The workshop is unique in covering all aspects of MEMS, nanotechnologies and emerging technologies concerning future displays, imaging devices, and emerging electron devices. It seeks to broaden the horizons of display and imaging technologies into cutting-edge technologies. Research areas such as materials, basic physics and fabrication process are included. Among all the MEMS and display conferences in the world, this is the only opportunity for MEMS and cutting-edge technology researchers to gather and discuss such devices. Authorities in this field are invited from top research institutions around the world. The invited speakers are from Univ. of Cambridge, QD Vision (MIT's venture company), Ecole Polytech, Uni-Pixel Displays, Qualcomm, Nagoya Univ., Kyushu Univ., Univ. of Tokyo and Toyota Technological Institute. With excellent contributed papers, this workshop invites participants who wish to open a new field of displays, imaging devices and emerging devices.

Workshop on Display Electronic Systems (DES)

This workshop covers all aspects of display systems in relation to electronics of video data processing, interface technologies, cooperative operations between display components such as cells and backlights, sensors, and applications in the new areas such as 3D video. We have set up a new session on visible light communications, which are emerging technologies for the promotion of new applications. In addition, the systems for a wide and high dynamic range of color reproduction such as multi primary color systems, high-fidelity, high-frame-rate, high-resolution, and low power consumption systems, are focused on.

Workshop on Flexible Displays (FLX)

Recently, there is much attention on flexible display technologies. The technologies are spread in a wide range of fields from material science to a practical application. The hottest sessions cover all aspects of flexible display technologies including electronic paper, flexible flat panel display, display materials, TFT and substrate technologies, which are interrelated with AMD, FMC, OLED and EP-WS.

Topical Session on Touch Panels and Input Technologies (INP)

This topical session covers all aspects of input technologies including materials, devices and systems. We expect that INP will open up brand new fields by fusing input and display technologies. INP sessions will be held by the related workshops on DES, AMD, FMC and EP. In addition to the recent activities in the popular touch panel technology, 3D input systems for 3D displays, new user interface technologies and the most advanced image sensor technologies are featured in this year's session.

Topical Session on Lighting Optics, Devices and Systems (LIT)

The LIT is a topical session that covers all aspects of lighting related to displays and eco-friendly illumination systems. The cutting-edge technologies of light sources, such as the lasers for projectors, the backlights for LCDs, and the corresponding materials, are topics that will be looked at closely.

IDW Best Paper Award and IDW Outstanding Poster Paper Award

IDW will present "IDW Best Paper Award" and "IDW Outstanding Poster Paper Award". The award committee of IDW will select the most outstanding papers from those presented at IDW '10. The award winners will be announced on the IDW website and given a plaque after the conference.

Exhibition

The IDW '10 Exhibition, which will be held from December 1 through December 3, covers materials, components, manufacturing and measuring equipments, software systems and other related products for display devices. Please join-in and enjoy discussions at exhibitors' booths (2F Lobby, 4F Lobby).

December 1:12:00 – 18:00 December 2:10:00 – 18:00 December 3:10:00 – 14:00

GENERAL INFORMATION

SPONSORSHIP

IDW '10 is sponsored by the Institute of Image Information and Television Engineers (ITE) and the Society for Information Display (SID).

CONFERENCE SITE

Fukuoka International Congress Center 2-1, Sekijo-machi, Hakata-ku Fukuoka 812-0032, Japan Phone: +81-92-262-4111 Fax: +81-92-262-4701

ON-SITE SECRETARIAT

Telephone and fax machines for IDW '10 use will be temporarily set up in the secretariat room (Room 405) at the Fukuoka International Congress Center (November 30-December 3). Phone/Fax: +81-92-282-8364

BANQUET

A buffet-style banquet will be held on December 1 from 19:30 to 21:30 at the Crowne Grand Ball Room (2F) in ANA Crowne Plaza Fukuoka. As the number of tickets is limited, you are urged to make an advance reservation through the website.

EVENING GET-TOGETHER WITH WINE

A get-together will be held on November 30 from 18:00 to 20:00 at RACONTER (1F) in the conference site. Wine (Sponsored by Merck Ltd., Japan) will be served to participants with a relaxed atmosphere for informal discussion.

REGISTRATION

Registration is available in advance and also on-site. However, on-site registrants may not be able to obtain books, if there are an unexpectedly large number of on-site registrations. Advance registration is strongly recommended.

Registration Fees

The registration fee for IDW '10 includes admission to the conference and CD-ROM of the proceedings. Additional ¥7,000 will be charged for those who want the proceedings in book format. For users who do not have CD drives on their computers, we will provide the data at the conference site. Detailed information will be announced on the website.

	Paid by Oct. 29	After Oct. 29
Individual Member	¥30,000	¥ 40,000
(ITE/SID/ASO*)		
Non-Member**	¥ 40,000	¥ 50,000
Student***	¥ 8,000	¥ 10,000
Life Member of ITE/SID	¥ 8,000	¥ 10,000
Banquet	¥ 7,000	¥ 10,000

*ASO: Academic Supporting Organizations

(See p. 11 as well as "Supporting Organizations and Sponsors" at the end of each workshop section.)

**Non-Member: If you intend to join either ITE or SID, one year membership fee will be subsidized by IDW '10 committee.

***Photocopy of student ID is required.

Please note that the reduced registration fee must be paid by October 29. The full fee will be charged for payments made later than October 29. Also note that *the number of banquet tickets to register on site is limited.*

For additional sets of the proceedings	(Book and CD-ROM)
At the conference site	¥ 8,000
Air mail after the conference	¥ 15,000
Domestic mail after the conference	¥ 10,000

Additional sets of Book and CD-ROM can be purchased only those who have completed payment by November 19.

Payment

Three ways are provided for registration.

(1) e-Registration

Access the following URL. http://www.idw.ne.jp/regist.html e-Registration will be accepted until November 19, 2010.

(2) Mail or Fax Registration

Complete the registration form (download from the website) and send it to the secretariat together with all necessary payments no later than November 19, 2010.

IDW '10 Secretariat

c/o Bilingual Group Ltd.

3-3-6 Kudan Minami, Chiyoda-ku Tokyo 102-0074, Japan

Phone: +81-3-3263-1345 Fax: +81-3-3263-1264

E-mail: idw@bilingualgroup.co.jp

The registration fee should be remitted by one of the following methods.

- 1. Credit Card
- 2. Bank Transfer to:

Bank: Bank of Tokyo-Mitsubishi UFJ (Swift Code: BOTKJPJT) Branch: Ichigaya Branch (Branch No. 14) Account No.: 1474095 (Ordinary Account) Account: IDW Please attach a copy of the bank receipt with the registration form to avoid any confusion.

All above payments should be made in **JAPANESE YEN**. Also, please note that personal and traveler's checks are not accepted.

(3) On-site Registration

Conference registration desk will be open:

November	30	(Tue.)	17:00 - 20:00	
December	1	(Wed.)	8:00 - 18:00	
December	2	(Thu.)	8:00 - 18:00	
December	3	(Fri.)	8:00 - 13:00	
		antine from .	ملطمينم مرما الأبر	i.

The on-site registration fee will be payable by:

1. Cash (JAPANESE YEN only)

2. Credit Card (VISA or MasterCard only)

Bank transfer, bank check, or personal/traveler's check are not accepted.

Cancellation Policy

Refunds for registration, banquet, additional sets of proceedings etc. will be made upon receipt by IDW '10 secretariat of written cancellation by **October 29**. For cancellations received after October 29 or no-shows, refunds will not be made. However, after IDW '10 closes, a set of the proceedings will be sent to the registrants who have paid the registration fees. If it becomes difficult to hold IDW '10 due to infectious disease and other unavoidable factors, we will substitute the IDW with the mail delivery of the IDW '10 proceedings at a later date to all those who have registered for participation.

INQUIRIES

IDW '10 Secretariat c/o Bilingual Group Ltd. 3-3-6 Kudan Minami, Chiyoda-ku Tokyo 102-0074, Japan Phone:+81-3-3263-1345 Fax: +81-3-3263-1264 E-mail:idw@bilingualgroup.co.jp

ACADEMIC SUPPORTING ORGANIZATIONS (ASO)

The Chemical Society of Japan The Electrochemical Society of Japan (ECSJ) The Illuminating Engineering Institute of Japan The Imaging Society of Japan The Institute of Electrical Engineers of Japan The Institute of Electronics, Information and Communication Engineers (IEICE) The Institute of Image Electronics Engineers of Japan Japan Ergonomics Society (JES) The Japanese Liquid Crystal Society (JLCS) The Japan Society of Applied Physics The Virtual Reality Society of Japan The Society of Polymer Science, Japan

FUNDS

Grant-in-Aid for Scientific Research (KAKENHI: 2264002) from MEXT The Asahi Glass Foundation

For final updated information, please visit our website, http://www.idw.ne.jp/10record.html.



Tuesday, November 30, 2010 18:00 – 20:00 at RACONTER (1F), Fukuoka International Congress Center (Sponsored by Merck Ltd., Japan) See page 9 for details

TRAVEL INFORMATION

ACCOMMODATIONS

JTB Tokyo Metropolitan Corp. will handle arrangements for your hotel reservations.

Hotel reservations can be made at the IDW official website. http://www.idw.ne.jp/accommodation.html

JTB Tokyo Metropolitan Corp. Corporate Sales Office Yokohama

Phone: +81-45-316-4602 Fax: +81-45-316-5701 Office Hours: 9:30-17:30 (Weekdays only) E-mail: jtb_convention@met.jtb.jp

There will be an on-site travel information desk during the conference period to handle arrangements for transportations.

VISAS

Visitors from countries whose citizens must have visas should apply to Japanese consular office or diplomatic mission in their respective country. For further details, please contact your travel agency or the local consular office in your country.

Attention: For some countries' citizens, official documents prepared by the secretariat will be needed. Please ask the secretariat at least two months before the conference.

CLIMATE

The average temperature in Fukuoka during the period is around 12° C in the daytime and 4° C at night.

BANQUET

Wednesday, December 1, 2010 19:30 – 21:30 Crowne Grand Ball Room (2F) ANA Crowne Plaza Fukuoka See page 9 for details

FUKUOKA

Fukuoka City (also known as "Hakata") lies on the northern coast of Kyushu, the southernmost of the four main islands of Japan. The population of the city is approximately 1.4 million people, making it the 7th largest city in Japan.

Being the closest major city in Japan to the Korean Peninsula and China, Fukuoka has from ancient times been a gateway for economic and cultural exchanges with its Asian neighbors. On the basis of these historical and geographical links, the city is working on many levels to strengthen its relationships with the rest of Asia, towards the goal of becoming a "focal point for exchange in Asia".

PLACES OF INTEREST

Dazaifu Tenmangu Shrine

Nishitetsu trains are available from Tenjin to Dazaifu Tenmangu (about 20 minutes by train and then 5 minutes on foot). Here, at the head shrine of all the Tenmangu Shrines in Japan, the god of learning, Michizane Sugawara, is worshipped. The plum tree to the right of the main building as you face it is called Tobiume (the flying plum tree), because it is said that the tree flew here to be with Michizane.

Kyushu National Museum

This museum is located a 5-minute walk from Dazaifu Tenmangu Shrine, and is Japan's newest National Museum after Tokyo, Kyoto, and Nara. Based on the concept of "Understanding Japanese culture from an Asian viewpoint", various valuable exhibits depict Japan's blossoming relationships with other Asian countries over a long time.

Fukuoka City Museum

Covered with half-mirrored windows, this museum stands with the Fukuoka Tower rising behind it (about 15 minutes by bus from Hakata Station). There are 4 different exhibition rooms and a special exhibition room for visiting exhibitions. The Gold Seal, one of Japan's national treasures, is exhibited in the Permanent Exhibition Room.

Uminonakamichi

Uminonakamichi is a peninsula connecting Shikanoshima Island in Higashi Ward to mainland Fukuoka. A large peninsula measuring about 8 km in length and about 2.5 km in width at its widest point, Uminonakamichi is a recreation area with a park in its central to north-western region. The JR Kashii Line and prefectural roads run parallel through Uminonakamichi, providing a popular scenic route. Those who prefer a boat ride can catch a ferry operated by Fukuoka City at the Bayside Place Hakata Futoh.

Yatai (Street Stalls)

"Hakata" is famous for "Hakata Ramen". One of the special features of nighttime Hakata is "yatai", street stalls that appear on the streets in the evening in Nakasu, Tenjin, and other areas. Yatai offer a range of hot tasty foods including Hakata Ramen, and a chance to rub shoulders with the locals.

More information is available at the following websites:

http://www.city.fukuoka.lg.jp/english/index.html

http://www.welcome-fukuoka.or.jp/english/

http://www.city.fukuoka.lg.jp/showcase/english/index.html

Access to Conference Site



Flight information on this page may be changed in October. Please confirm the details with each airline company.

(as of October 31, 2010)

Bus

Nishitetsu customer center Phone: +81-92-303-3333 One Day Pass is available. (¥ 600) For more information, please refer to the following website. http://jik.nnr.co.jp/Tschedule/gb/

Hotel Map



- ANA Crowne Plaza Fukuoka (Banquet Site)
- Hotel Nikko Fukuoka
- **3** Sutton Place Hotel Hakata
- Oliver Nishitetsu Inn Hakata
- 9 Yaoji Hakata Hotel
- Hakata Excel Hotel Tokyu
- IP Hotel Fukuoka
- 8 Best Western Fukuoka Nakasu Inn

IDW Best Paper Award

This award will go to the most outstanding paper selected from those presented at IDW '10. The 2010 award winners will be announced on the IDW website: http://www.idw.ne.jp/award.html

IDW Outstanding Poster Paper Award

This award will go to the most outstanding paper selected from those presented at IDW '10 poster presentation.

The 2010 award winners will be announced on the IDW website: http://www.idw.ne.jp/award.html

EXHIBITION

12:00 – 18:00 Wednesday, Dec. 1, 2010 10:00 – 18:00 Thursday, Dec. 2, 2010 10:00 – 14:00 Friday, Dec. 3, 2010

2F Lobby, 4F Lobby Fukuoka International Congress Center

Free admission with your registration name tag

December 1

Main Hall

Plenary Sessions

Wednesday, December 1

10:20 - 10:30

Opening

Master of Ceremony: N. Ibaraki, Executive Chair, AIST, Japan

Opening Remarks

10:20

K. Betsui, General Chair, Hitachi, Japan R. Hattori, Program Chair, Kyushu Univ., Japan

10:30 - 11:15 Main H						
		Keynote Address				
Co-Chairs:	R. Hatto K. Betsi	ri, Program Chair, Kyushu Univ., Japan ui, General Chair, Hitachi, Japan				
Keynote Ad 10:30	ldress	The Artistic & Scientific World in 8K Super Hi-Vision				

Y. Kawaguchi

Univ. of Tokyo, Japan

The Ultra HDTV system consists of an 8k horizontal spatial resolution and 60 frames per second temporal resolution. This advanced development of 8K Ultra HDTV enable us to verify a wide variety of new possibilities.

1	1:15	5 -	12:0	00								N	lain	Hall
					Inv	ited	Add	res	s					
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Co-Chairs: T. Miyashita, Program Vice-Chair, Tohoku Univ., Japan M. Date, Program Vice-Chair, NTT COMWARE, Japan

Invited Address TAOS-TFTs: History and Perspective 11:15

H. Hosono

Tokyo Inst. of Tech., Japan

Since the first report of a-IGZO-TFT in late 2004, extensive research has been performed toward real application to the backplane of next generation FPDs. This paper reviews the material design concept of transparent amorphous oxide semiconductors (TAOS) and unique features of TAOS-TFTs along with next challenge.

December 1

Workshop on LC Science and Technologies

Wednesday, December 1

13:20 - 16:20

Poster/A.I. Room

Poster LCTp1: LC Materials

LCTp1 - 1 Effects of LC Compositions on Polymer Stabilized Blue Phase LCs

L.-Y. Wang, T.-H. Huang, N. Sugiura, W.-L. Liau, C.-C. Han^{*}, C.-J. Lung^{*}, P.- L. Jung^{*}, H.-C. Lin^{*}

AU Optronics, Taiwan *Nat. Chiao Tung Univ., Taiwan

The compositions of polymer stabilized blue phase liquid crystals (PS-BPLCs) relating to the thermal properties and electro-optical ones which are important for both display performance and productivity were investigated in this paper. By optimizing quantity of chiral-dopants and new monomers, temperature range of the BPLCs could successfully be enlarged.

LCTp1 - 2 Electro-Optic Response in Blue Phase LC

J.-Y. Chou, H.-Y. Chen, S. Chen*

Feng Chia Univ., Taiwan ^{*}Chunghwa Picture Tubes, Taiwan

In PI-less technology, we don't need PI materials and solvent materials that can attain green process. The final results have some advantages, such as high contrast ratio, high brightness, viewing angles. Finally, we have successively developed a new cell process without PI process for VA mode.

LCTp1 - 3 High UV Light Resistance and Low Rotational Viscosity LC

K.-C. Wang, P.-C. Huang, A.-C. Chen, K.-L. Cheng ITRI, Taiwan

We present the novel trifluoro-methyl vinyl (TfV) liquid crystal materials which possess high photostability. Voltage holding ratio (VHR) result is sustained after the irradiation. TfV LCs provide a reliable UV stability compared with F-containing LCs. Plus, mixtures with the TfV LCs exhibit lower rotational viscosity than well-known bis-cyclohexyl diluents.

LCTp1 - 4 Synthesized Novel Dendritic Molecules and Broadening of Temperature Range in Liquid Crystalline Blue Phases

S. Shibayama, H. Higuchi, H. Kikuchi Kyushu Univ., Japan

Liquid Crystalline Blue Phases are promising for applications to tunable photonic liquid crystals because they have three-dimensional photonic bands for visible wavelength. However, narrow temperature range of BPs is a problem to be solved for practical applications. We report the expanded temperature range of BPs with novel dendritic molecules.

LCTp1 - 5 Synthesis and Properties of Novel LCs with Fluorinated Alkenyl Side Chains

T. Sugita, S. Ihara, T. Asai, H. Koh AGC SEIMI Chem., Japan

Novel LCs with fluorinated alkenyl side chain have been prepared by using Tetrafluoroethylene. Some of these LCs show low bulk viscosities and moderate virtual clearing points. It is possible that some of these LCs will be useful LC materials for AM LCDs.

LCTp1 - 6 Direct Observation of Polymer Network Structure on Polymer Stabilized Blue Phase

M. Kwak, H. Kwon, D. Han, J. Jeon, J. Park, S. Choi, Y. Choi, D. Koo LG Display. Korea

The polymer network structure of polymer stabilized blue phase was directly observed with SEM. As a result of analyzing the polymer of defect structure was clearly detected, polymer chain after eliminate liquid crystal, organized network form like form of sponge. The polymer chain was changed according to the temperature condition.

LCTp1 - 7 Influence of Heating Stir Process on Light-Emitting Properties in LC Electrochemiluminescent Cells

M. Tanimoto, T. Horiuchi, M. Honma, T. Nose Akita Pref. Univ., Japan

From the measurement of optical density and photoluminescent intensity in organic fluorescent dye-doped liquid-crystal (LC) cells, heating temperature dependence of both dye concentration and fluorescent quantum yield in sample preparation process have been investigated together with luminance properties of LC electrochemiluminescent cells.

LCTp1 - 8 Difference in the Long-Term Image Degradation of LCD Caused by Two Kinds of Known Impurities Added to the Host Nematic

M. Akimoto^{*}, Y. Higuchi^{*}, M. Inoue^{*,**}, Y. Ueda^{*}, S. Kobayashi^{*}, K. Takatoh^{*} ^{*}Tokyo Univ. of Sci., Yamaguchi, Japan ^{**}Toyo, Japan

We investigate the long-term image degradation of LCDs caused by ionic impurities which is intentionally added to a host nematic LC material. Here we use two kinds of illustrative impurities: 4-(Dimethylamino) pryidine and Stearoyl chloride. It turns out that these impurities lead to different kinds of image degradation of LCDs.

LCTp1 - 9L Alignment of Rod-Disc Molecule by AC Electric Field

S.-E. Kim, J. H. Jung, E. K. Song, K. S. Ha, S. H. Lee, K.-U. Jeong Chonbuk Nat. Univ., Korea

Molecular orientation of chemically linked rod-disc liquid-crystalline in an anti-parallel rubbed LC cell was investigated under vertically applied alternative current electric fields. It was concluded that molecular frustrations under the vertical AC electric field occurred as a result of the competition among rods attached to both sides of the disc.

LCTp1 - 10L Direct Observation of Biaxiality in a Thermotropic Compound Through Measurement of Electro-Optic Characteristics

B. W. Park, D. H. Song, H.-B. Kwon, E.-J. Choi, J. C. Kim, T.-H. Yoon

Pusan Nat. Univ., Korea *Kumoh Nat. Inst. of Tech., Korea

We investigated biaxiality of a thermotropic compound through the measurement of its electro-optic characteristics. We observed the U-shaped behavior in the V-T curve of the compound, which may be attributed to the biaxiality of the compound.

SID 2011

International Symposium, Seminar and Exhibition

May 15-20, 2011

Los Angeles, California, U.S.A.

LCTp1 - 11L All-Optically Controllable Random Laser Based on a Dye-Doped Liquid Crystal Added with a Photoisomerizable Dye

C.-R. Lee, J.-D. Lin, P.-Y. Huang, T.-S. Mo*, S.-Y. Huang**

Nat. Cheng Kung Univ., Taiwan ^{*}Kun Shan Univ. of Tech., Taiwan ^{**}Chung Shan Medical Univ., Taiwan

This study investigates an all-optically controllable random laser in a dye-doped liquid-crystal (DDLC). The all-optical controllability is attributable to isothermal N \leftrightarrow I phase transitions of LCs due to *trans\leftrightarrowcis* isomerizations of azo-dye, which can vary spatial fluctuations of dielectric property of LCs, subsequently change the lasing intensity of the random laser.

LCTp1 - 12L Fundamental Properties of Extremely Thick PDLC by Using Porous PMMA Materials

T. Ito, R. Ito, M. Honma, T. Nose Akita Pref. Univ., Japan

Polymer dispersed liquid crystal (PDLC) is investigated by using nematic liquid crystal and porous PMMA materials to attain millimeterwave (MMW) and/or terahertz-wave (THz) LC control devices. Extremely thick porous PMMA materials are successfully constructed by phase separation in ethanol/water solution and their morphology are observed by SEM.

LCTp1 - 13L Physical Property Improvement of Coatable Polarizer by Photocurable Lyotropic LC Solution

Y.-G. Kim, Y.-J. Bae, K.-U. Jeong, S.-H. Shin^{*}, M.-H. Lee

Chonbuk Nat. Univ., Korea *Korea Inst. of Ind. Tech., Korea

We report new preparation method of coatable polarizer from photocurable lyotropic chromonic liquid crystal solution. Thin film polarizer was prepared by coating a photocurable solution of perylenediimide in the chromonic nematic phase with subsequent photocuring. The new method provided various advantages such as excellent coating characteristics and improved mechanical/chemical stability.

Asia Display 2011

Kunshan, China

LCTp1 - 14L Distributed Feedback Laser with Optoelectronic Tunability in Dye-Doped Cholesteric Liquid Crystal with Coated Photoconductive Layer

C.-R. Lee^{*}, Huang S.-C.^{*}, S.-H. Lin^{*}, Z.-Y. Lin^{*}, S.-Y. Huang^{*****}, T.-S. Mo^{*****} ^{*}Univ. of Electro-Optical Sci. & Eng., Taiwan ^{**}Univ. of Optometry, Taiwan ^{***}Univ. of Ophthalmology, Taiwan ^{****}Univ. of Elect. Eng., Taiwan

This work investigates, for the first time, an optoelectronically-tunable distributed feedback laser that is based on a planar DDCLC cell with a coated photoconductive (PC) layer. The CLC reflection band and the lasing wavelength of the DDCLC can be tuned by optoelectronical effect.

13:20 - 16:20	Poster/A.I. Room

Poster LCTp2: LC Alignment

LCTp2 - 1 Photoalignment Properties of 2- and 3-Thienylacrylates Bearing Laterally Fluorinated Azobenzene Moieties

G. Hegde, D. Chambers-Asman**, A. V. Matharu*,

L. Komitov

Gothenburg Univ., Sweden *Nottingham Trent Univ., UK **Univ. of York, UK

The photoalignment properties of thin films made from several azocontaining thiophene-based acrylate is reported. Inclusion of a lateral fluoro-substituent(s) provides excellent photo alignment ability whereas the non-fluorinated counterpart tends to give unsatisfactory alignment quality. The study showed that 3-substituted thiophenes give better photoalignment quality than their 2-substituted thiophene isomers counterparts.

LCTp2 - 2 Photoalignment Ability of Thin Films of Bishydrazones Derived from 3,4-Dipropyloxythiophene

R. A. Alla, G. Hegde, K. Ravi^{*}, A. V. Adhikari^{*}, K. A. Krishnamurthy^{*}, L. Komitov Gothenburg Univ., Sweden ^{*}Nat. Inst. of Tech.. India

Photoalignment LC promoted by thin films of bishydrazone derived from 3, 4 dipropyloxythiophene is studied. Results show that bishydrazone without methyl group in their structure is promoting planar alignment parallel whereas the ones with methyl group in the structure are promoting planar alignment perpendicular to light polarization direction.

LCTp2 - 3 Investigation of the Photoalignment Effect of 1,3,4-Oxadiazoles Bearing 2-Fluoro-4-Methoxy Phenyl Moiety

R. A. Alla, G. Hegde, A. M. Isloor^{*}, C. B^{**}, P. Shetty^{***},

L. Komitov

Gothenburg Univ., Sweden *Nat. Inst. of Tech., India **Syngene Int., India ***Manipal Univ., India

A new series of 1,3,4-oxadiazole derivatives containing 2-fluoro-4-methoxy moiety were synthesized by refluxing mixture of acid hydrazide 3 with different aromatic carboxylic acid. Photoalignment studies were performed which indicates that the position of fluorine plays vital role in promoting planar alignment either parallel or perpendicular to the light polarization direction.

LCTp2 - 4 Uniformity Enhancement of LC Inorganic Alignment Layer Deposited by the Obliquely Oriented Incidence Direction of Sputtering

J. Kim, G.-J. Lee, K.-J. Yang, H.-K. Lyu, B.-D. Choi Daegu Gyeongbuk Inst. of S&T, Korea

An inorganic LC alignment layer is widely investigated because of thermal and photochemical stability of LC alignment layer. For uniform LC alignment layer, we compared the conventional oblique deposition with 2-step oblique deposition method by sputtering techniques.

LCTp2 - 5 Hysteresis Reduction in EO Characteristics of Photo-Aligned IPS-LCDs with Polymer-Surface-Stabilized Method

Y. Nagatake, Y. limura Tokyo Univ. of A&T, Japan

An In-Plane-Switching (IPS) LCD manufactured using a photoalignment [PA] method appears the hysteresis at EO performance. In this paper, to solve the problem in PA method, we used a polymersurface-stabilized (PSS). We have demonstrated a PA method combined to a PSS method is a useful and attractive LC alignment method.

IDW Best Paper Award

This award will go to the most outstanding paper selected from those presented at IDW '10. The 2010 award winners will be announced on the IDW website: http://www.idw.ne.jp/award.html

LCTp2 - 6 Effect of Photocurable Monomers on Homeotropic LC Alignment Behaviors of LC/Photocurable Monomer System

J. M. Lee, H. Kang^{*}, J.-H. Lee, J. S. Park, J.-C. Lee^{*}, D. Kang Soongsil Univ., Korea ^{*}Seoul Nat. Univ., Korea

We have investigated the effect of photocurable monomers on homeotropic liquid crystal (LC) alignment properties in an LC/ photocurable monomer system through UV irradiation. Different homeotropic LC alignment behaviors and electro-optical performances were observed depending on the type and concentration of photocurable monomers and UV irradiation time.

LCTp2 - 7 LC Alignment on Micrograting Structures Photofabricated from Photo-Polymerizable LCs

A. Tsuno, H. Yoshida, H. Kubo, A. Fujii, M. Ozaki Osaka Univ., Japan

Coexistance of geometric and surface orientation was prepared through the fabrication of micrograting from photo-polymerizable liquid crystals via two-photon excitation direct laser writing. Anchoring energies which were stronger by a factor of 10 were obtained compared to those fabricated from a non-liquid crystalline photopolymer.

LCTp2 - 8 Control of Pretilt Angle and Formation of Bistable Surface by Depositing Alignment Materials by Utilizing an Electro-Spray Deposition Method

Y. Kudoh, Y. Nakanishi, T. Nakano, S. Saito, T. Takahashi Kogakuin Univ., Japan

An infinite number of minute domains which consist of two kinds of alignment materials were formed on substrate surfaces by the ESD method. The amount of spouted solution of alignment material was varied to control the pre-tilt angle or to give bistable characteristic for the nematic LC cell.

LCTp2 - 9L Alignment of Liquid Crystal on Ion Beam Treated ITO Surface Directly without PI Coating

S. Hwang, J. H. Lee, H. K. Shin, T.-H. Yoon, J. C. Kim Pusan Nat. Univ., Korea

We propose a liquid crystal (LC) alignment method that can align LC molecules on ion beam treated indium-tin-oxide (ITO) surface. We found that the exposure energy and time need to be over 200 eV and 10 s, simultaneously, for a high quality homogeneous alignment on the ITO surface.

LCTp2 - 10L Selection of Easy Axis by Liquid Crystal on Rubbed PVCi Surface

R. Yamaguchi Akita Univ., Japan

We reported that LCs with and without polar groups aligned perpendicular and parallel to a rubbing direction on a rubbed PVCi surface, respectively. Easy axis control of the PVCi was realized by mixing LCs and an alignment patterning was successfully demonstrated by exposing with unpolarized UV light.

13:20 - 16:20)					Poster/A.I. Room
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Poster LCTp3: Characterizations

LCTp3 - 1 Mechanism for Lattice-Shaped Mura in TFT-LCD B. C. Woo, K. H. Kim, J. S. Kim, W. H. Kim, S. Y. Han Samsung Elect., Korea

Mechanism for lattice-shaped mura is proposed by characterizing the optical properties of LC showing different transmission. The edge in LC droplet exposed in air evaporated more rapidly. These result in the higher concentration of polar singles in edge of dotted LC droplet, leading to the higher Δn and higher transmittance.

LCTp3 - 2 Characterization of Vertical Alignment Film by X-ray Reflectivity

I. Hirosawa, T. Koganezawa, H. Ishii*

Japan Synchrotron Radiation Res. Inst., Japan *Nissan Chem. Inds., Japan

Existence thin and low density top layer at surface of VA polyimide film, which was considered to be side chains, was detected by X-ray reflectivity. Furthermore, high density layer about 2 nm in thick just below the top layer was found.

LCTp3 - 3 Measurement of Optical Parameters for Birefringent Film Stack

H. T. La, T. Sato

ZEON, Japan

We described a method for measuring the optical parameters of birefringent stacks consisting of two optical films. The method was applied to a stack sample which is consisted of two stretched plastic films as an example.

Wednesday

LCTp3 - 4 Simultaneous Measurement of Elastic Constants and Anchoring Energy of Homeotropic and Homogeneous Nematic LC Cells by a Capacitance Method

K. Iwaya, H. Naito, H. Ichinose^{*}, M. Klasen-Memmer^{**}, K. Tarumi^{**}

Osaka Pref. Univ., Japan *Merck, Japan **Merck KGaA, Germany

We have proposed a method for determining simultaneously elastic constants and anchoring energy of nematic liquid crystal (NLC) cells by measuring capacitance – voltage characteristics. The applicability of thepresent method has been demonstrated in both homeotropic and homogeneous NLC cells.

LCTp3 - 5 Exact Modeling for Nucleation of Defects by Using a Fast Q-Tensor Method

W. S. Kang, S. H. Hur, H. J. Yoon^{*}, G. D. Lee Dong-A Univ. of Elect. Eng., Korea ^{*}Sanayi Sys., Korea

We apply the surface anchoring energy term to the fast Q-tensor method. Also, we investigate the value of the order parameter S around the surface layer and the generation and motion of defects in the pi cell using the fast Q-tensor method with weak anchoring strength.

LCTp3 - 6 Temperature Dependence of Leslie Viscosity Coefficients of Nematic LC with Negative Dielectric Anisotropy Determined from Transient Current Using a Genetic Algorithm

M. Oka, K. Iwaya, Y. Iwata, H. Naito, M. Inoue^{*}, H. Ichinose^{**}, M. Klasen-Memmer^{***}, K. Tarumi^{***}

Osaka Pref. Univ., Japan ^{*}Toyo, Japan ^{**}Merck, Japan ^{**}Merck KGaA, Germany

We have derived the analytical expressions of the transient current in homeotropic nematic liquid crystal cells and have determined the Leslie viscosity coefficients by fitting the analytical expressions to the experimental data using a genetic algorithm. The applicability of the algorithm is demonstrated by determining the Leslie viscosity coefficients at different temperatures.

LCTp3 - 7 Determination of Polar Anchoring Energy Based on SOITE Method by Combining a Voltage Correction

K. Tachibana, K. Goda, Y. Kaneko^{*}, M. Inoue^{*}, M. Kimura, T. Akahane Nagaoka Univ. of Tech., Japan ^{*}Toyo, Japan

We proposed a method for determining the surface polar anchoring energy coefficient of nematic liquid crystal cell based on symmetric oblique incident transmission ellipsometry (SOITE) method in which the applied voltage diminution is compensated. The validity of this technique was confirmed by the numerical calculations.

13:20 - 16:20

Poster/A.I. Room

Poster LCTp4: LCD Modes

LCTp4 - 1 New Pixel Design for PVA Mode LCD Color Shift Improvement

> C.-H. Huang, C.-C. Chen, H.-C. Liang^{*} Chunghwa Picture Tubes, Taiwan ^{*}Chung Yuan Christian Univ., Taiwan

Off-axis image quality of MVA Mode LCD has been improved by new pixel design t. The simulated result shows that gamma shift at large view angle (i.e. 60 deg) of new Pixel design is reduced 40% compared with conventional PVA design, resulting in decreased color shift at off-axis viewing positions.

LCTp4 - 2 Viewing Angle Switching LCDs Using Large Optically Anisotropic Behaviors of Twisted-Nematic LCs

C.-H. Lin, R.-H. Chiang, M.-L. He, C.-W. Chen, C.-T. Kuo Nat. Sun Yat-Sen Univ., Taiwan

This work proposes a viewing angle switching (VAS) panel using twisted-nematic liquid-crystals (TN-LCs). With the proposed panel, a display is only perceived clearly at a downward direction in a narrow viewing angle mode to ensure high privacy protection. Additionally, the proposed VAS panel achieves a high transmittance of 95%.

LCTp4 - 3 Comparison of the Cell Process Margin at Each LC Mode

Y. B. Lee, K. H. Park, S. K. Lee BOE-HF, China

In this paper, we could know the cell process margin at each LC Modes. We compared the T-V characteristics of pre-tilt and cell gap deviation by LC simulator. We confirmed that the FFS mode's cell process margin is wider than other wide viewing angle LC Modes.

LCTp4 - 4 Advanced Twist Nematic LCD

I.-F. Wang, F. W. Kuo, G.-S. Chao, C.-H. Yu Hannstar Display, Taiwan

An new advanced twist nematic (ATN) liquid crystal display mode which perform wide viewing angle and high contrast has been demonstrated. The ATN is unlike traditional TN mode that exhibits normally-white state and low contrast ratio. It exhibits normally-black state and contrast ratio exceeds 2000:1.

LCTp4 - 5 Switching between Bistable States by Applying Vertical and Horizontal Fields in Chiral Tilted-Homeotropic Nematic LC Cell

T. Nakadate, T. Takahashi, S. Saito Kogakuin Univ., Japan

Fundamental properties in the bistable chiral tilted-homeotropic nematic (BCTHN) LC device consisting of a nematic LC with a negative dielectric anisotropy are investigated. The switching between bistable states in the (0.2π) and $(-\pi/2, 3\pi/2)$ types of BCTHN devices by applying a vertical field and a horizontal field is investigated.

LCTp4 - 6 47-in. Full HD Transparent Display without Polarizer Using S-IPS Mode LCD Panel

S. H. Park, E. D. Kim, J. S. Park, J. K. Kang, K. H. Lee, M. C. Jun, I. J. Jung LG Display, Korea

Transparent 47-in. full HD S-IPS mode with backlight system has been developed. This technology is removing polarizer to make transparent display in IPS mode and design polarized light from TBLU. It is possible to reproduce the window displays by turning on TBLU at indoors and turning off TBLU at outdoors.

LCTp4 - 7 Improvement of Correlated Color Temperature Tracking in In-Plane Switching LCD

S.-H. Ji, S. H. Han, J. M. Yoon, I. C. Park, M. C. Jun, I. J. Jung LG Display, Korea

We introduce a method to improve tracking of correlated color temperature (CCT) in the in-plane switching LCD. On the basis of the simulation, we fabricated 17-in. IPS LCD panel to verify the optical characteristic. It exhibits more than 50 percent decrease compared to the conventional IPS LCD in the Δ CCT.

LCTp4 - 8 Reverse Twist Nematic Mode on Stacked Alignment Layer Method

S. I. Jo, S. W. Choi, A. R. Yoon, S. G. Lee, Y.-J. Lee, C.-J. Yu, J.-H. Kim Hanyang Univ., Korea

We propose an inverse twisted nematic mode without chiral dopant. Using a doubly stacked alignment layer, the enhancement of azimuthal anchoring strength is obtained on the vertical alignment layer and gives rise to a stably twisted configuration in the presence of an applied voltage.

LCTp4 - 9 Low Gray Level Color Shift in Twisted Nematic LCD

F. G. Xu, L. B. Mao, Y. W. Chiu, D. C. Chung, T. S. Jen InfoVision OptoElect., China

Twisted Nematic (TN) TFT LCD has color shift issue at oblique viewing angles. Cell retardation and back light were investigated in our experiments, color shift will be decreased with the increasing of retardation, reddish or blueish which came from the influence of backlight spectrum.

LCTp4 - 10 Minimize Gamma Variation in TFT-LCD

F. G. Xu, L. B. Mao, Y. W. Chiu, D. C. Chung, T. S. Jen InfoVision OptoElect., China

The influence of cell parameters and Analog VDD (AVDD) voltage to TFT-LCD's Gamma were investigated. According to the experimental results, pretilt angle and AVDD voltage are key parameters to Gamma, the twist angle and cell gap also have impacts on it. These data are important reference information to process ability control.

LCTp4 - 11 Low-Voltage-Driving LC Lens

M. Ye, B. Wang, M. Uchida, S. Yanase, S. Takahashi, M. Yamaguchi^{*}, S. Sato Akita R&D Ctr., Japan ^{*}Mitsubishi Materials Elect. Chems., Japan

An approximately 1 μ m thickness thin film of insulator is introduced into a liquid crystal lens cell replacing the substrate between the patterned electrode and the liquid crystal layer. The distance between electrodes decreases drastically, and the driving voltages drops from several tens of volts to only several volts.

LCTp4 - 12 Tunable LC Lens Using Stacked Alignment Layers

F. Fan, M.-C. Tseng, A. Murauski, H.-S. Kwok, V. Chigrinov

Hong Kong Univ. of S&T, Hong Kong

A tunable liquid crystal (LC) lens is achieved using stacked alignment layers. The stacked alignment layer consists of photoalignable homogeneous alignment material and rubbed vertical alignment material. By exposing the stacked alignment layer under UV laser, a lens-like phase retardation profile is got due to the variable pretilt angle.

LCTp4 - 13 Four Primary-Color Pixel Design for Wide Color Gamut

Y.-H. Kim, S.-H. Han, S. H. Ji, H. S. Lee, J. M. Yoon, I. C. Park, M. C. Jun, I. J. Jung LG Display, Korea

We developed a multiple primary color LCD's (Red, Green, Blue, Cyan). The Color Gamut was extended 103% of NTSC standard. And, we find the optimum solution of asymmetric 4 Primary-Color structure minimizing luminance decreasing ratio.

LCTp4 - 14L Optical Configuration for a Dual Mode Liquid Crystal Display with Infinite Memory Time and High Contrast Ratio

T. Kim, J. H. Lee, C. G. Jhun^{*}, S.-B. Kwon^{*}, T.-H. Yoon, J. C. Kim Pusan Nat. Univ., Korea ^{*}Hoseo Univ., Korea

We propose an optical configuration for a dual mode liquid crystal display with a d/p ratio of 0.25 for infinite memory time and π -twist state as dark state for high contrast ratio. As a result, we obtained a high contrast ratio of 250:1.

LCTp4 - 15L Optical Design of a Bistable TN Cell

D. H. Song, J. H. Lee, K.-H. Kim, J. C. Kim, T.-H. Yoon Pusan Nat. Univ., Korea

Liquid crystal shutter glasses are used in conjunction with a display screen to create the illusion of a three dimensional image. In this paper, we introduce TN mode fabricated by a dual frequency liquid crystal (DFLC) material with a fast response to remove the flicker.

LCTp4 - 16L Fast Switching of In-Plane Switching Cell with Pixel-Isolating Polymer Walls

J.-W. Kim, D. H. Song, J. C. Kim, T.-H. Yoon Pusan Nat. Univ., Korea

We propose the in-plane switching liquid crystal mode with the pixelisolating polymer wall structure using reactive mesogen. With the multidimensional LC alignment effect, the proposed mode shows faster response time characteristics than the conventional IPS mode without any loss of the transmittance.

LCTp4 - 17L Tunable Fresnel Lens Using Surface Modification of Vertical-Aligned Liquid Crystals

K. Lin, S. Jeng^{*}, T. Chen, S. Hwang Nat. United Univ., Taiwan ^{*}Nat. Chiao Tung Univ., Taiwan

A simple method to make a switchable liquid crystal Fresnel lens with high diffraction efficiency and a low driving voltage was proposed by photo-induced surface modification of vertical alignment layer. Remarkable diffraction efficiency close to the theoretical limit was detected and demonstrated to depend sensitively on the applied voltage.

LCTp4 - 18L Fundamental Performance of Birefringence Imaging System Using a Liquid Crystal Phase Shifter

T. Nose, Y. Aizawa, K. Okano, H. Muraguchi, N. Ozaki, M. Honma, R. Ito

Akita Pref. Univ., Japan

OCB cell is combined with a polarization microscope to construct a birefringence imaging system by introducing the phase shifting interferometry technique. Basic performance of the system is investigated by using a tiny biological sample and quantitative birefringence images are successfully demonstrated.

LCTp4 - 19L Improvement of EO Characteristics for the Reversed-TN LCD by Using Polymer Wall

Y. Ohike, Y. Toko^{*}, S. Saito, T. Takahashi

Graduate School of Kogakuin Univ., Japan *Stanley Elec., Japan

The Reversed-TN LCD has a low threshold voltage and a steep sharpness characteristic is known when the d/P_0 is increased. However, the reversed state is unstable for operating. In this study, polymer walls are formed in the cell to stabilize the reversed state and improvement of sharpness characteristic is attempted.

LCTp4 - 20L Passive Matrix Driving Scheme for Bistable Chiral Splay Nematic Liquid Crystal Display with Cross-Talk-Free

Y. Jin, Z. Hong, J. G. Ying, C. G. Jhun, S. B. Kwon, J. H. Lee^{*}, T. H. Yoon^{*}, J. C. Kim^{*} Hoseo Univ., Korea ^{*}Pusan Nat. Univ., Korea

The BCSN mode is one of promising mode, because it can be operated both as a storage and a monostable device. In this paper, we propose the passive matrix driving scheme for BCSN liquid crystal display. With a dual frequency liquid crystal material, we can suppress the cross-talk effect.

LCTp4 - 21L The Novel Applications and Research of Axial Symmetric Dye-Doped Liquid Crystal Films via Photoalignment Method

S.-W. Ko, A. Fuh, T.-H. Lin^{*} Nat. Cheng Kung Univ., Taiwan ^{*}Nat. Sun Yat-Sen Univ., Taiwan

The research of axially symmetric dye-doped liquid crystal film is demonstrated in paper. Axially symmetric devices were used generally in symmetric optics, such as converting polarized light into axially, azimuthally or vortically light. The novel applications have also been presented in this paper, as polarization-independent liquid crystal lens and tunable donut beam.

LCTp4 - 22L Fast Response Time in Twisted Nematic Mode with a Dual Frequency Liquid Crystal Material for Shutter Glasses

S. H. Han, J. G. Ying, Y. Zhang, Z. Hong, Y. Jin, Y. W. Seo, S. S. Shin, C. B. Moon, C. G. Jhun, M. R. Shin^{*}, J. S. Lim^{*}, J. R. Seo^{*}, B. K. Seo^{*}

Hoseo Univ., Korea *Bokja Girl's High School, Korea

Liquid crystal shutter glasses are used in conjunction with a display screen to create the illusion of a three dimensional image. In this paper, we introduce TN mode fabricated by a dual frequency liquid crystal (DFLC) material with a fast response to remove the flicker.

LCTp4 - 23L Fast Switching of Silica Nanoparticle-Doped Hybrid Aligned Nematic Device

C.-Y. Huang, C.-C. Lai, Y.-J. Huang, J.-H. Chen, H.-C. Song

Nat. Changhua Univ. of Education, Taiwan

We improve the response time of the silica nanoparticle-doped HAN cell. A low-frequency AC pulse-voltage driving scheme accelerates the LC relaxation, decreasing the response time of the cell. In the multistable mode, the obtained response time is ~ 23 ms, which is ~ 4% of our previous result.

13:20 - 16:20	Poster/A.I. Room						
Poster LCTp5: Transflective LCDs							

LCTp5 - 1 Extraordinarily Wide-View and Wide Spectral Bandwidth Transflective LCDs

C.-H. Lin, R.-H. Chiang, M.-L. He, C.-W. Chen Nat. Sun Yat-Sen Univ., Taiwan

This work presents a simple compensation method for widening the viewing angle of transflective liquid-crystal displays (TR-LCDs). Based on the proposed compensation method, the compensated TR-LCDs exhibit a wide spectral bandwidth and a viewing angle of 80° for contrast-ratio (CR) >100:1 and >30:1 in transmissive and reflective modes, respectively.

LCTp5 - 2 A New Double-Cell Gap Transflective OCB-LCD with In-Cell Compensation Film

I. Fukuda, Y. Sakamoto, T. Ishinabe^{*}, T. Uchida^{**}

Kanazawa Inst. of Tech., Japan ^{*}Tohoku Univ., Japan ^{**}Sendai Nat. College of Tech., Japan

A new double-cell-gap transflective OCB-LCD with an in-cell compensation film was designed to improve response time and viewing-angle performance of transflective displays. We verified that wide viewing angle and high luminance could be achieved by optimizing design parameters of the LCD, even if the on voltage is lowered to 3 V.

LCTp5 - 3 Design of Transflective LCD Using a Reflective Polarizer without Sub-pixel Division

H.-J. Jin, K.-H. Kim, J. C. Kim, B.-H. Cheong^{*}, H.-Y. Choi^{*}, S. T. Shin^{*}, T.-H. Yoon Pusan Nat. Univ., Korea

*Samsung Elect., Korea

We propose a LCD mode switchable between reflective and transmissive modes without sub-pixel division. By placing a reflective polarizer between the two LC layers, we can employ the entire pixel area for both reflective and transmissive modes. The proposed structure can have transmittance and reflectance higher than conventional transflective LCDs.

LCTp5 - 4 Transflective LCD Using Two Modes

M. S. Park, B. C. Jang, J. Yi, J. H. Kwon, J. S. Gwag Yeungnam Univ., Korea

We present a transflective liquid crystal display using two modes that are splay state and 180° twisted state obtained from the pi-cell. Here, the splay state operated by horizontal field is used for transmissive part, while the 180° twisted state with vertical field is used for reflective part.

LCTp5 - 5 Single Gap Transflective Vertically Aligned LCD

D. W. Kwon, D. H. Kim, S. H. Lim, S. J. Shin, J. H. Her, Y. J. Lim, S. H. Lee Chonbuk Nat. Univ., Korea

A transflective liquid crystal display associated with surface polymerstabilized vertical alignment mode is proposed. The retardation of liquid crystal layer and its azimuthal tilting direction are determined via polymerization of reactive mesogen. As a result, new device with high performance is achieved without using any compensation film or in-cell retarder.

LCTp5 - 6 Withdrawn

----- Break -----

16:40 - 18:	05	Room 502
	LCT1: Photo Alignment Technolog	у
Chair: Co-Chair:	H. Okada, Univ. of Toyama, Japan I. Hirosawa, Japan Synchrotron Radiation Japan	Res. Inst.,

LCT1 - 1: Invited The UV²A Technology for Large Size LCD-TV 16:40 Panels

K. Miyachi, N. Kimura, Y. Yamada, S. Mizushima Sharp, Japan

We developed the new photo-alignment technology for the large size LCD-TV panel and we successfully applied it to our generation-ten factory. The transmittance, contrast ratio and response time of our panels are drastically improved to evolve the LCD-TVs to the next generation.

LCT1 - 2 Analysis and Implementation of PI Less Technology 17:05 Applied in TFT-LCDs

C. W. Su, J. T. Lien Chunghwa Picture Tubes, Taiwan

In PI-less technology, we don't need PI materials and solvent materials that can attain green process. Besides, we don't need complex fabrication and expensive equipment which can achieve saving process time and cost down. The final results have some advantages, such as high contrast ratio, high brightness, viewing angles. Finally, we have successively developed a new cell process without PI process for VA mode.

LCT1 - 3 Withdrawn

LCT1 - 5L Advanced UV Alignment Technology in IPS-LCD for 17:25 the Improvement of Color and Viewing Angle

H. J. Ahn, J. W. Woo, C. H. Kwak, W.-S. Kim, M.-S. Yang, Y.-K. Hwang, I.-J. Chung LG Display, Korea

The advanced UV alignment technology was developed to overcome the drawbacks of conventional IPS-LCD. The prototype panel by using UV technology shows wider viewing angle and low color shift compared with the rubbing method. It is thought that the symmetrical LC orientation with zero pretilt angle would induce these enhancements.

LCT1 - 4Surface Control with Reactive Mesogen for Fast17:45Switching LCD Modes

Y.-K. Moon, M.-G. Choi, T.-M. Kim, J.-H. Jeong, Y.-J. Lee, C.-J. Yu, J.-H. Kim Hanyang Univ., Korea

We propose an advanced method to improve response time characteristics of the liquid crystal displays (LCDs) through stacking reactive mesogen (RM) on the alignment layer. The RM polymers enhance the surface anchoring strength, and thus the response time of the LCDs was significantly improved, especially in relaxation time.

Author Interviews 18:00 – 19:00
Thursday, December 2

9:00 - 10:25

Room 502

LCT2: High Performance LC Technology

Chair: M. Inoue, Toyo, Japan Co-Chair: K. Miyachi, Sharp, Japan

LCT2 - 1: Invited Analysis of Compare Ion Density with Image 9:00 Sticking Level on Real TFT-LCD Panels

M. Kwak, H. Kwon, D. Han, J. Jeon, J. Park, S. Choi, Y. Choi, D. Koo LG Display, Korea

With the use of Ion Density measuring method, the amount of moving ions within TFT-LCD panel was measured. As a result, the mount of moving ions within the panel affected image sticking, and also the measured amount equalled the image sticking evaluation result.

LCT2 - 2 Effect of Process and Material on TFT-LCD's Image 9:25 Sticking

Z.-F. Su, S.-N. Zhang, L.-B. Mao, Y.-W. Chiu, D.-C. Chung, T.-S. Jen

InfoVision OptoElect., China

Effects of the process parameter and material on the image sticking have been investigated through experiments. The experimental results show that rising PI pre-bake temperature, reducing cell process steps of color filter and shorting the Q-time and the color resist material with lower VHR are useful in image sticking improvement.

LCT2 - 3 Vertical Alignment of LC with Pretilt by an Ordering 9:45 Effect of Alkylsiloxane Self-Assembled Monolayers on an Ion-beam-Irradiated SiO₂ Surface

J.-S. Park, K.-Y. Seok, S.-W. Hwang^{*}, J.-C. Kim^{*}, T.-H. Yoon^{*}, J.-H. Kim^{**}, H.-R. Kim

Kyungpook Nat. Univ., Korea *Pusan Nat. Univ., Korea **Hanyang Univ., Korea

We investigated a vertical alignment (VA) method of liquid crystals (LCs) by using Akylsiloxane self-assembled monolayers (SAM) prepared on an anisotropic surface, which was produced by oblique ion beam irradiation. Depending on the surface anisotropy produced on the underlying SAM layer, the pretilt of LC in VA can be controlled. With our method, multi-domain VA LC configuration can be easily and stably obtained by controlling the ion-beam irradiation conditions.

10:05

LCT2 - 4 Photo Patterned Micro Polarizer

T. Du, L. Yao, F. Fan, V. Chigrinov, H. S. Kwok Hong Kong Univ. of S&T, Hong Kong

In this paper, a photoaligned micro patterned polarizer has been proposed, which is capable of making patterns down to the size of 2 μ m. The patterned polarizer consist of three stacked layers including a conventional linear polarizer, a quarter wave plate and a photo patterned quarter wave plate.

----- Break -----

10:40 - 11:55

Room 502

LCT3: New Functional LCDs

Chair: M. Kwak, LG Display, Korea Co-Chair: K. Ishikawa, Tokyo Inst. of Tech., Japan

LCT3 - 1 Energy Efficient LCDs (e²-LCDs) Using Photonic 10:40 Crystal Structure Based on Cholesteric LC Materials

M. Suzuki, N. Fujiwara

Merck, Japan

Photonic crystals based on cholesteric liquid crystal materials doped with fluorescent dyes have been developed as simultaneous light emitting and reflecting layer. Novel energy efficient LCDs having the photonic crystal layers can utilize not only backlight but also ambient light.

LCT3 - 2 A Novel Structure of Full Color Cholesteric LCD

C.-H. Hsieh, Y.-S. Tsai, Y.-C. Lai, Y.-C. Liao, K.-T. Chen, C.-C. Lai, J.-W. Shiu, G.-W. Wu, S.-Y. Fuh ITRI, Taiwan

We provided a high reflectance and great color performance of the new structure design for full color cholesteric LCD. This new structure can provide the reflectance close to the triplet stacked ChLCD and wider color gamut but only required two ChLC layers and much simpler driving system hardware.

LCT3 - 3The Simulation of Single Layer Ch-LCD Panel11:20Design and Color Adjustment Evaluation

M.-Y. Lu, K.-J. Hu, T.-T. Chang, Y.-Y. Lin, Y.-H. Bai, W.-J. Li

ITRI, Taiwan

The capability of color exhibition and its accuracy on ChLCD are influenced by the spectrum characteristic of material used, circuit driver and manufacturing process advancement. However, it cost a lot on experiment during development stage. Therefore, color simulation can assist to reduce cost and indicate correct direction of research development.

LCT3 - 4L In-Plane Switching of a Bent-Core LC(PAL1) with 11:40 Negative Dielectric Anisotropy in the Homeotropic Cell

Y. Jang, J. K. Vij, C. Tschierske^{*} Trinity College Dublin, Ireland ^{*}Martin Luther-Univ., Germany

Electro-optic behavior of bent-core LC(PAL1) in the nematic phase has been studied under vertical alignment. Optically biaxial nematic phase (N_b) is evidenced by measurement using a photoelastic modulator(PEM) and the material in this phase is switchable through the minor director with an in-plane electric field.

----- Lunch -----

13:20 - 14:40	Room 502
LCT4: High Performance LCDs	

Chair: M. Suzuki, Merck, Japan Co-Chair: H. Wakemoto, Toshiba Mobile Display, Japan

LCT4 - 1 Fast Response TN-LCDs Using Ultra Short Pitch LC 13:20 Materials

K. Takatoh, M. Akimoto, K. Shinohara, Y. Nakamura, S. Kobayashi

Tokyo Univ. of Sci., Yamaguchi, Japan

TN-LCDs with LC materials of the pitch length shorter than the twice of cell width was found to be formed by applying electric field to 270 degree STN-LCD possessing splayed twist molecular arrangement and stabilized by using UV curable monomer. The decay time is improved drastically by using USP TN-LCDs.

LCT4 - 2 Novel Design of Single Cell Gap Wide-View 13:40 Transflective LCD Using Twist Fringe-Field Switch Mode without Retarder

K.-T. Huang, Y.-W. Hung, K. Chen, L.-L. Huang, W. C. Fang HannStar Display, Taiwan

A novel single cell-gap transflective liquid crystal display (LCD) with FFS mode has been proposed. The transmissive region is homogeneous aligned. And reflective region is partial twisted and tilted to reach single gap design. In addition, the VT and VR curve is similar by optima pixel electrode width, space, twist and tilt angle in reflective region.

LCT4 - 3 Withdrawn

LCT4 - 5L Advanced Hybrid FPA Technology for the VA Mode

M. Miyakawa, S. Suwa, T. Isozaki, M. Nakamura, T. Urabe

Sony, Japan

We developed the advanced Hybrid Field induced Photo-reactive alignment (FPA) technology using FPA alignment material and vertical alignment material. This technology could improve the trade-off property and realize the faster falling response as well as the lower black level.

LCT4 - 4Newly Developed Reverse Twisted Nematic LCD14:20Showing Steep Electro-Optical Characteristics

M. Akimoto, N. Motoishi, M. Nishitateno, Y. Toko^{*}, K. Takatoh Tokyo Univ. of Sci., Yamaguchi, Japan

токуо Univ. of Sci., Yamaguchi, Japa *Stanley Elec., Japan

We present a newly developed reverse twisted nematic liquid crystal display (RTN-LCD) endowed with low pretilt angles. We found that the electro-optical characteristics of the present low pretilt angle RTN-LCD is much steep enough to achieve the maximum duty ratio of 1/480 for multiplex drive.

----- Break -----

15:00 - 16:10		Room 502
	LCT5: Emerging LC Application	
Chair: Co-Chair:	K. Takatoh, Tokyo Univ. of Sci., Yamaguchi T. Yamaguchi, Chisso Petrochem., Japan	, Japan

LCT5 - 1 A Full-Resolution and Glasses-Free 3D Display 15:00 Using the OCB-III with a Light Directional Backlight

T. Higano, K. Nakao, Y. Tanaka, H. Takahara, J. Hanari, H. Wakemoto

Toshiba Mobile Display, Japan

We have developed a full-resolution and glasses-free 3D display with no pseudoscopic image in which the OCB-III mode with black insertion and light directional backlight have been applied. The fast response of OCB, black insertion and backlight switching unable us to separate the right/left images clearly and achieve low 3D-crosstalk.

LCT5 - 2Image Quality Simulation of Field Sequential Color15:20Display with Limited LC Response Time

Y.-S. Huang, H.-L. Hou, W.-C. Sun AU Optronics, Taiwan

The image quality of field sequential color (FSC) with limited LC response time were simulated by modifying eye-trace integration of MPRT program; we successfully simulated the color mixing phenomenon in FSC with real LC case, the color shift caused by slow LC response can also been demonstrated.

LCT5 - 3L High-Speed Liquid Crystal Polarization Modulator 15:40 for Time-Multiplexed Stereoscopic 3D Applications

J. Osterman, T. Scheffer^{*} LC-TEC Displays AB, Sweden ^{*}Motif, USA

A high-speed liquid crystal polarization modulator suitable for timemultiplexed stereoscopic 3D applicationsis proposed. By using a double-cell structure together with a novel driving scheme, polarization compensation can be achieved to hide the optical response during the liquid crystal relaxation process, enabling fast powered switching between two polarization output states.

LCT5 - 4LAn Addressing Technique to Drive Blue Phase LCDs15:55T. Ruckmongathan

Raman Res. Inst. Bangalore, India

Bit slice addressing (BSA) is proposed to preserve color purity of images at all angles in fast responding liquid crystal displays with simple data drivers. About 80% reduction in data driver circuit and an average 26.9% reduction in backlight power are achieved with BSA!

Author Interviews 18:00 - 19:00

Friday, December 3

9:00 - 10:20		Room 204
	LCT6: Nanostructured LC	
Chair: Co-Chair:	M. Funahashi, Kagawa Univ., Japan M. Kimura, Nagaoka Univ. of Tech., Japan	

LCT6 - 1 Experiment-Based Proposal of Novel Fast-Switching 9:00 LCDs Using Field-Induced Isotropic-Nematic Transition

M. Kosuge^{*,**}, S. Naemura^{*}, N. Koma^{**}, T. Tsuyuki^{**}, K. Fujimura^{*} ^{*}Tottori Univ., Japan ^{**}Sony Mobile Display, Japan

The electro-optic effect based upon the electric-field-induced isotropicnematic transition was investigated using cells with an appropriate electrodes-configuration and surface treatment. Its exhibits a hysteresis-free large optical-transmittance change with viewing-angleindependent deep-dark-level and the response times are less than 1msec, enabling a novel display featuring fast switching and high image quality.

LCT6 - 2 Electro-Optic Response of Blue Phases

9:20 H. Choi, H. Higuchi, H. Kikuchi Kyushu Univ., Japan

The relation between electro-optic response and chiral pitch was investigated in blue phase I and II, respectively in detail. The result also showed that the hysteresis for the transmittance according to the electric field did not appear before the induced phase transition occurs.

LCT6 - 3 Enhancement of Electro-Optical Performance of 9:40 Narrow-Gap TN-LCDs by Doping Newly Synthesized Nanoparticles

B. Kundu, Y. Shirashi, H. Sawai, K. Takeuchi^{*}, N. Toshima, S. Kobayashi

Tokyo Univ. of Sci., Yamaguchi, Japan ^{*}DIC, Japan

By doping newly synthesized nanoparticles of P γ , β CyD-ZrO₂ into the host media of narrow-gap TN-LCD the reductions of both the threshold voltage by ~30% and the response times by 20 – 50% were obtained at 25°C and 0°C. These effects are analyzed and clarified through a material research on NLCs and computer simulation.

LCT6 - 4 Nanoparticle-Mediated Polyimide for Pretilt Angle 10:00 Control of LC Devices

S.-C. Jeng, S.-J. Hwang^{*}, Y.-M. Shieh^{*}, S.-C. Chen^{*} Nat. Chiao Tung Univ., Taiwan ^{*}Nat. United Univ., Taiwan

The pretilt angles θ_P of LC molecules can be controlled by using conventional polyimide alignment (PI)doped with Polyhedral Oligomeric Silsequioxanes (POSS) nanoparticle. The addition of POSS changes thesurface energy of the PI and generates the variable θ_P over the range of $0^{\circ} < \theta_P < 90^{\circ}$ depending on the POSS concentration.

----- Break -----

10:40 - 11:55

Room 204

LCT7: New LCD Design

Chair: T. Ishinabe, Tohoku Univ., Japan Co-Chair: S. Komura, Hitachi Displays, Japan

LCT7 - 1 New MVA Design to Improve Color Washout for 10:40 Mobile Applications

Y.-P. Kuo, S.-C. F. Jiang, C.-H. Shih, W.-M. Huang AU Optronics, Taiwan

We've designed high performance MVA display utilizing different protrusion ratio in one sub-pixel to improve color washout and GTG response time. We get better washout performance, and the washout value improve ratio is 33% lower than conventional MVA and GTG response time reducing range is 36% lower than conventional MVA.

LCT7 - 2 Transfer 26-in. WXGA LC-TV from TN to Symmetrical 11:00 Viewing-Angle MVA Mode with Only One-Mask Change without ITO Slits and Protrusions

H. L. Ong, J. Chou, X. Y. Wang^{*}, Y. Qiao^{*}, Y. W. Chiu^{*}, D. C. Chung^{*}, T. S. Jen^{*}

Kyoritsu Optronics, Taiwan ^{*}InfoVision OptoElect., China

We successfully transferred a 26-in. WXGA LC TV from the low-end TN to the high-performance AIFF MVA, without protrusions, without ITO slits, and only changed one TN mask. The AIFF MVA process is high-yield and low-cost. The measured transmission of 5.1-5.5% is greater than all published MVA and IPS LC TV.

LCT7 - 3 TFT-LCD with CVA Technologies

H. Zheng, L. Zhou, T.-C. Chung, Y. Qiao, X. Huang, C. Zeng, D. Zhang, C.-T. Liao, Y.-W. Chiu, T.-S. Jen InfoVision OptoElect., China

We developed a series of CVA technology for high performance and low cost LCD TV applications. The CVA shows a high contrast ratio of over 3500:1, the omni viewing angle performance, and comparatively better gamma dispersion characteristics by adopting a low cost design whose CF without the protrusion bump.

LCT7 - 4L Fast LC Devices with Lowest Control Voltage 11:40 A. Andreev, V. Ezhov^{*}, I. Kompanets, A. Sobolev^{**} P.N. Lebedev Physical Inst., Russia ^{*}STEL, Russia ^{**}Megavision, JSC, Russia

Novel FLC cells were developed with the response time of about 30÷ 70 μ s under the electric field 1.0÷2.0 V/µm for 1.0 μ m layer thickness (reflectance mode) and 1.3 μ m (transparent mode). Stereo glasses with shutters modulating the light with the frequency 200 Hz at ±1.5 V and 1000 Hz at ±3.0 V were manufactured.

Author Interviews 16:20 – 17:20

Supporting Organization: The Japanese Liquid Crystal Society (JLCS)

SID 2011

International Symposium, Seminar and Exhibition May 15-20, 2011

Los Angeles, California, U.S.A.

IDW Tutorial in Japanese

Tuesday, November 30, 2010 Room 412 Fukuoka International Congress Center

Detailed information is announced at http://www.sidchapters.org/japan/

IDW '11

The 18th International Display Workshops

December 7-9, 2011

Nagoya Congress Center Nagoya, Japan

http://www.idw.ne.jp

Workshop on Active Matrix Displays

Wednesday, December 1

15:00 - 16:25

Room 501

AMD1: AM-LCD

Chair: H. J. Kim, Yonsei Univ., Korea Co-Chair: M. Hiramatsu, Toshiba Mobile Display, Japan

AMD1 - 1: *Invited* Characteristics, Their Applications and 15:00 Trends of LED Backlights

K. Otoi, T. Shinomiya, T. Masuda, H. Murakami, H. Ichioka, K. Fujiwara, K. Hashimoto, T. Murai Sharp, Japan

LED backlights are becoming major backlight modules of displays instead of CCFL backlights. We summarize characteristics of LED backlights from the viewpoints of LED packages, optical designs, control systems and evaluations with their applications. Then we refer to the trends of LED backlights discussing merits and demerits of those characteristics.

AMD1 - 2 Modeling and Measurement of Ultra-Low Leakage 15:25 Current of a-IGZO TFTs and New Driving Method of LCDs

H. Godo, A. Miyanaga, K. Kusunoki, K. Toyotaka, T. Nishi, K. Moriya, S. Fukai, Y. Kubota, K. Wakimoto, J. Koyama, S. Yamazaki, Y. Oikawa, K. Okazaki^{*}, M. Sakakura^{*}

Semiconductor Energy Lab., Japan *Advanced Film Device, Japan

We showed that an a-IGZO TFT has ultra-low leakage current by measurement. We realized new driving method by taking advantage of ultra-low leakage current of an a-IGZO TFT. As a result, the power consumption in displaying images at 1/180 fps is approximately 1/10000 of that at 60 fps.

AMD1 - 3 Advanced Pixel Potential Shift Driving for Flicker 15:45 Reduction

M. Yoshiga, T. Inada, M. Shibazaki, S. Kawata, Y. Matsui, H. Watsuda, K. Hashimoto, C. W. Lin^{*}, K. Sano^{*}, D. L. Ting^{*}

TPO Displays Japan, Japan *Chimei Innolux, Taiwan

We've successfully developed Advanced Pixel Potential Shift (APPS) driving for flicker reduction to compensate photo leak voltage loss through TFT. Furthermore with backlight luminance sensor it is possible to increase aperture ratio by reducing storage capacitance size. Thus backlight power reduction is also feasible with newly developed APPS driving.

AMD1 - 4 Novel Data Line Sharing Method in AMLCDs for High Resolution Displays W. S. Choi, Y. H. Jang, K.-S. Park, Y. G. Chang, S. C. Choi, T. W. Moon, J. Y. Seo, H. N. Cho, N. W. Cho, S. B. Ryu, J. Y. Yang, C.-D. Kim, Y. K. Hwang, I.-J. Chung LG Display, Korea

A novel data line sharing method, suitable for high resolution and fast frequency display, has been developed, which has a symmetrical pixel structure. Moreover, we have successfully fabricated the 17.1-in. AMLCD WXGA panel with the new method and the a-Si TFT based circuit integration technology of LG Display's own.

----- Break -----

 16:40 - 17:40
 Room 501

 AMD2: System on Panel & Sensing Device

Chair: A. Heya, Univ. of Hyogo, Japan Co-Chair: M. Inoue, Chimei Innolux, Japan

- AMD2 1 Withdrawn
- AMD2 4LDynamic Self-Refreshing Memory-in-Pixel Circuit16:40for Ultra Low Power 302ppi LTPS TFT-LCD

K. Yamashita, M. Shibazaki, H.-Y. Liang^{*}, Y. Matsui, S. Kawata, C.-J. Chang^{*}, M. Yoshiga, N. Sumi, T.-Y. Cheng^{*}, T.-W. Kuo^{*}, E.-L. Deng^{*}, W.-J. Lin^{*}

TPO Displays Japan, Japan ^{*}Chimei-Innolux, Taiwan

An ultra low power dynamic Self-Refreshing-Pixel Memory In Pixel (SRP-MIP) circuit with 302 ppi is integrated into a 2.65-in. VGA (480RGBx640) transflective LTPS TFT-LCD by using new VA mode. The power consumption in MIP mode is 200 μ W, while keeping the transmissive aperture ratio of 20%.

AMD2 - 2A Novel Pixel Design of 4-in. QHD TFT-LCD with New17:00Reliable Integrated a-Si Scan Driver (RASD)

H. R. Han, W. C. Wang, M. C. Yu, W. C. Tsai, T. H. Lin, C. H. Huang, H. Y. Chang, M. H. Tsai, F. C. Wu, W. T. Liao

Wintek, Taiwan

A novel 4-in. QHD a-Si TFT-LCD with reliable integrated a-Si scan driver (RASD) has been developed. This new circuit is able to resist the Vth shift of a-Si TFT after a long-term operation. Furthermore, by introducing fast-switching liquid crystal with protrusion free pixel design, fast response display can also be achieved.

AMD

AMD2 - 3The Polarity Bias Control of Indium Zinc Oxide Thin17:20Film Transistor for Gas Sensor Application

L.-F. Teng, P.-T. Liu, Y.-T. Chou, Y.-S. Fan Nat. Chiao Tung Univ., Taiwan

An obvious V_{th} shift was observed after gate-bias stress and recovered. This metastability was attributed to the interaction between the exposed a-IZO backchannel and oxygen/moisture from the atmosphere, regardless of the polarity of stress voltage. This water/moisture sensitivity characteristic can be used for gas sensor application.

Author Interviews

18:00 - 19:00

Thursday, December 2

9:00 - 10:20 Room 5		1
	AMD3: Si TFT	
Chair: Co-Chair:	M. Yoshiga, TPO Displays Japan, Japan S. Horita, JAIST, Japan	
AMD3 - 1 9:00	Advanced 405 nm Laser Diodes Crystallization of a-Si Film for the Fabrication of Microcrystalline-Si TFTs	

K. Morimoto, N. Suzuki, M. Yuri, K. Yamanaka, J. Milliez^{*}, X. Liu^{*}

Panasonic, Japan ^{*}Panasonic, USA

We have proposed a novel crystallization method of a-Si using 405 nm laser diodes and applied it to the fabrication of bottom gate microcrystalline-Si TFTs for the first time. High performance TFTs were successfully demonstrated and the advantage of a 405 nm wavelength was also verified with heat flow simulation.

AMD3 - 2 9:20 Fabrication of 15-in. HD WXGA AMOLED Panel with Micro-Crystalline Silicon TFTs by the Indirect Thermal Crystallization (ITC) Method

K.-T. Kim, J. H. Bae, S. Lee, B. G. Choi, H. K. Lee, S. K. Kim, K.-S. Park, C.-D. Kim, Y. K. Hwang, I.-J. Chung LG Display, Korea

15-in. HD WXGA AMOLED panel has been fabricated with microcrystalline silicon TFTs adopting indirect thermal crystallization (ITC) method. We developed a-Si TFT based bottom gate process of 7masks, which is suitable for a large sized panel. ITC-TFT showed high mobility and reliable electrical characteristics in a full range of the panel.

AMD3 - 3 A High Resolution Polymorphous 3ATI AMOLED 9:40 Display Based on a Low Mask Count Top Gate Process

M. Herrmann, P. Schalberger, H. Baur, N. Fruehauf Univ. of Stuttgart, Germany

We processed a grayscale-compliant 3ATI type display with high resolution driven by an integrated gate driver based on our new polymorphous silicon top gate process. Due to the selective deposition of n-doped silicon onto metal D/S contacts a lower mask count compared to well established bottom gate processes was achieved.

AMD3 - 4 Drain Bias Effect on Characteristics of Leakage 10:00 Current for Various Back-Surface State Density

C.-S. Wei

AU Optronics, Taiwan

Device leakage current for drain bias effect has been investigated. Furthermore, the back-surface state density is a key parameter for lower the reverse sub-threshold leakage current under smaller drain operation. Display application for high drain operation was also introduced when device off-state driving region was different.

AMD

----- Break -----

10:40 - 12:	:10 Room 204	
FLX5/AMD4: Flexible Active-Matrix Devices		
Chair: Co-Chair:	K. Tsukagoshi, NIMS-MANA, Japan T. Shiro, Teijin, Japan	
FLX5/ AMD4 - 1: 10:40	Invited Application of Organic Thin-Film Transistors for Circuits on Flexible Foils P. Heremans ^{*,**} , K. Myny ^{*,**} , H. Marien ^{**} , E. V. Veenendaal ^{***} , S. Steudel [*] , J. Genoe [*] , M. Steyaert ^{**} , G. H. Gelinck ^{*****} [*] imec, Belgium ^{**} Katholieke Univ. Leuven, Belgium ^{**} Katholieke Univ. Leuven, Belgium ^{**} Polymer Vision, the Netherlands ^{****} Holst Ctr. TNO, the Netherlands	

We present the state of the art of digital and analog circuits (in particular code generators for RFID tags, amplifiers, AC-DC and DC-DC converters) using organic TFTs on plastic foil, and discuss some design considerations needed to overcome today's technology limitations.

FLX5/ Invited A Rollable OTFT-OLED Display AMD4 - 2: I. Yagi, M. Katsuhara, A. Yumoto, N. Kobayashi, M. Noda, 11:05 I. Yasuda, S. Ushikura, G. Yukawa, N. Hirai, K. Nomoto, T. Urabe Sony, Japan

A rollable OLED display, which can be rolled-up in a radius of 4 mm, is driven by a newly-developed OTFT backplane. The backplane equips with an integrated gate driver circuit and it is constructed of OTFTs using a self-developed organic semiconductor, a PXX derivative.

 FLX5/
 The High Stability and Uniformity a-IGZO Thin Film

 AMD4 - 3
 Transistors Array for AM-OLED Application

 11:30
 J.-Y. Yan, H.-C. Yao, Y.-P. Chen, C.-Y. Hung, Y.-Y. Wu, K.-Y. Ho, H.-C. Cheng

 ITRI, Taiwan

The high stability and uniformity amorphous $InGaZnO_4$ TFTs were fabricated on plastic substrate. We optimize the process and abandon the ES layer to reduce photomask and processing time. The mobility, SS and Vth of a-IGZO TFTs is 7.33 cm²/Vs, 0.42 V/dec and 0.79 V. The lifetime of AMOLED is exceeding 10 years.

FLX5/
AMD4 - 4
11:50Full Color AM-LCDs on Flexible Glass Substrates
S. Hoehla, S. Garner^{*}, M. Hohmann, O. Kuhls, X. Li^{*},
A. Schindler, N. Fruehauf
Univ. of Stuttgart, Germany
*Corning, USA

We have realized a full color 4-in. quarter-VGA amorphous Silicon AM-LCD on 75 μ m flexible glass substrates. With this work we demonstrate that the incorporated ultra-thin glass substrates have suitable properties to be compatible with a standard color AM-LCD process and achieve active matrix backplanes with reliable performance.

----- Lunch -----

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13:20 - 16:20

Poster/A.I. Room

Poster AMDp: Active-Matrix Devices

AMDp - 1 New Compensation Method for Image Distortion by the Ripple of Common Electrode in TFT-LCDs

K. H. Kim, W. K. Moon, M. S. Kim, J. H. Park, J. K. Song*

Samsung Elect., Korea *Sungkyunkwan Univ., Korea

The ripple of common electrode by internal capacitive coupling in TFT-LCDs makes a falling-off in image quality like horizontal crosstalk and greenish phenomenon. To improve these defects, some compensation methods have been used since long ago, but not perfect. This paper proposes more advanced methods to maximize the improvement effect.

AMDp - 2 Withdrawn

AMDp - 3 A Novel Depletion Mode IGZO TFT Gate Driver Embedded with a Level Shifter

B. Kim^{*,**}, S. B. Ryu^{*}, S. C. Choi^{**}, S.-H. Choi^{**}, Y. H. Jang^{**}, K.-S. Park^{**}, C.-D. Kim^{**}, Y.-K. Hwang^{**}, I.-J. Chung^{**}, M.-K. Han^{*} ^{*}Seoul Nat. Univ., Korea ^{**}LG Display, Korea

We propose and design a new gate driver embedded with a level shifter employing depletion mode In-Ga-Zn-O thin film transistors. The SPICE simulation results exhibit that the gate driver successfully generates an output-pulse without any distortion. The proposed circuit would be an important building block for an oxide TFT display.

AMDp - 4 Stabilization for Integrated Gate Driver Circuit with High Temperature Operation in Large-Sized Panel

C.-D. Tu, C.-E. Wu, C.-L. Lin Nat. Cheng Kung Univ., Taiwan

A new gate driver circuit using 11 TFTs, one capacitor and 4 signals is proposed. Based on the measurement of a-Si:H TFT, the threshold voltage shift can be reduced by adjusting the duty ratio. The simulation result shows the proposed circuit can implement over than 24 hours at high temperature.

AMDp - 5 A Voltage Regulator Using Chopper Comparators for LTPS-TFT

T. Mizuno, M. Yoshida Tokai Univ., Japan

In this paper, a voltage regulator using chopper comparators for LTPS-TFT (Low Temperature Poly Silicon-Thin Film Transistor) is proposed. The proposed circuit can reduce the maximum deviation rate of the output voltage (V_{OUT}) for the device mismatch. In addition, the power efficiency of the proposed circuit is 58%.

AMDp - 6 A Novel a-Si TFT Gate Driver with Simplified Logic Circuit for Three Level Driving Application

J. Lu, Y. Qiao, C.-T. Liao, T.-C. Chung, T.-S. Jen InfoVision OptoElect., China

A novel circuit with a simple four-TFT- three-clock structure which was implemented to GIA for reducing the cost of TFT-LCD was proposed. It could output the three- level waveform. By implementation of this 3-level gate driving scheme, both low cost and high aperture ratio could be achieved simultaneously.

AMDp - 7 An Active-Matrix Backplane Design Using Shadow-Masking Techniques to Create Economically Attractive Devices with Integrated Drivers

C. E. Harrigal, W. Little Advantech US, USA

Through shadow-masking techniques, we have economically produced active-matrix backplanes with integrated driving circuitry. The TFT's have speeds and currents necessary to drive E-Paper and OLED frontplanes. Additionally, they have leakage currents low enough to have power consumption advantages.

AMDp - 8 Integrated Potentiostat Using Thin-Film Transistors with Electrochemical Cell

Y. Imuro^{*}, K. Bundo^{**}, Y. Sagawa^{**}, K. Setsu^{*}, M. Kimura^{*,***,****}

^{*}Ryukoku Univ., Japan ^{**}Nara Inst. of S&T, Japan ^{***}Joint Res. Ctr. for S&T, Japan ^{****}Innovative Materials & Processing Res. Ctr., Japan

We developed an integrated potentiostat using TFTs with an electrochemical cell. Poly-Si TFTs and three electrodes are fabricated on a glass wafer. Cyclic voltammetry for enzyme and redox reactions is executed, and a glucose concentration of 0.4 mM can be detected, which is sufficient sensitivity for some medical applications.

AMDp - 9 Embedded Touch Sensing Circuit Using the Body Capacitance for AMOLED Displays

Y.-J. Park, S.-J. Seok, S.-H. Park, O. Kim POSTECH, Korea

The embedded touch sensing circuit is proposed and simulated for AMOLED display. Unlike LCD which has a variable capacitor, there is no a variable capacitor in OLED structure so that we artificially make the variable capacitor in the sensing pixel to detect the touch using the concept of body capacitance.

AMDp - 10 Peculiar Charge Pumping Characteristics and Exploration of MOS Interfaces in Large-Grain LTPS TFTs

T. Kato, G. Kawachi^{*}, T. Tsuchiya Shimane Univ., Japan ^{*}ALTEDEC, Japan

The charge-pumping characteristics in LTPS-TFT were investigated to understand the electronic-properties near the MOS interface. It was found from the investigation that there are some scattered dense regions of interface traps, which are considered to correspond to joining points of the grain boundaries.

AMDp - 11 Polycrystalline Silicon Thin Film Transistors with Simultaneous Realization of Threshold Voltage Adjustment and Nickel Drive-in

W. Zhou, S. Zhao, R. Chen, M. Wong, H.-S. Kwok Hong Kong Univ. of S&T, Hong Kong

A new fabrication process of metal induced crystallization polycrystalline silicon (poly-Si) Thin Film Transistors (TFTs) is proposed. Threshold voltage adjustment and nickel drive-in is simultaneous realized by boron implantation after nickel sputtering. Threshold voltage of TFTs is greatly reduced, while the current on/off ratio, mobility and sub-threshold slope are maintained.

AMDp - 12 Characteristics of Thin Film Transistors Fabricated by Solid Phase Crystallization and High Speed Lateral Crystallization Induced by Micro-Thermal-Plasma-Jet Irradiation

> S. Hayashi, S. Higashi, H. Murakami, S. Miyazaki^{*} Hiroshima Univ., Japan ^{*}Nagoya Univ., Japan

Thin Film Transistors (TFTs) were fabricated by Solid Phase Crystallization (SPC) and High Speed Lateral Crystallization (HSLC) Si films fabricated by Micro-Thermal-Plasma-Jet irradiation with different plasma-substrate gap. Characteristic variation of SPC-TFT was suppressed to less than 1%, while HSLC-TFT achieved a very high field effect mobility of 260 cm²/Vs.

AMDp - 13 Crystallization of Sputtered Si Films by Blue Laser Diode Annealing (BLDA) for Photo-Sensor Application

J. D. D. Mugiraneza, K. Shirai, T. Suzuki, T. Okada, T. Noguchi, H. Matsushima^{*}, T. Hashimoto^{*}, Y. Ogino^{*}, E. Sahota^{*}

Univ. of the Ryukyus, Japan *Hitachi Computer Peripherals, Japan

Results of various spectroscopic methods showed the thick sputtered-Si films entirely crystallized with preferred orientation as (111) after BLDA. Superficial layer turns into lateral grains while underlying layer grows into columnar grains. Photo-electrical characteristics show BLDA is promising for fabrication of advanced poly-Si photo-sensor and for thin film photovoltaic cells.

AMDp - 14 Microwave Remote H⁺ Plasma Passivation for Self-Release Nickel Induced Crystallization (SR-NIC) Polycrystalline Silicon Thin-Film Transistors (TFTs)

S. Zhao, W. Zhou, R. Chen, Z. Meng, M. Wong, H. S. Kwok

Hong Kong Univ. of S&T, Hong Kong

In this study, microwave remote H⁺ plasma treatment was applied to self-release nickel induced crystallization (SR-NIC) polycrystalline silicon thin-film transistors (poly-Si TFT). By applying microwave remote plasma treatment, intra-grain and grain boundary trap states in the poly-Si film can be passivated. So, performance of p-channel TFT can be improved significantly.

AMDp - 15 Withdrawn

AMDp - 16 Dependence of Poly-Crystallization on Scanning Velocity of Blue-Multi-Laser-Diode Annealling (BLDA)

K. Shirai, J. D. D. Mugiraneza, T. Suzuki, T. Okada, T. Noguchi, H. Matsushima^{*}, T. Hashimoto^{*}, Y. Ogino^{*}, E. Sahota^{*}

Univ. of the Ryukyus, Japan ^{*}Hitachi Computer Peripherals, Japan

Undoped amorphous Si (a-Si) thin films prepared by radio frequency (RF) sputtering were poly-crystallized by changing the scanning velocity of BLDA. Arbitrary grain size structure and high crystallinity of grains can be realized for the sputtered a-Si film by controlling the scanning velocity of BLDA.

AMDp - 17 Influence of Grain Size on Gate Voltage Swing and Threshold Voltage of Poly-Si Thin Film Transistors

F. Oshiro, K. Shirai, T. Noguchi, T. Ohachi^{*}, H. M. Koo^{**}, H. S. Choi^{**}

Univ. of the Ryukyus, Japan ^{*}Doshisha Univ., Japan ^{**}LG Display, Korea

A model of the gate voltage swing considering interface trap, bulk trap and grain size is proposed. The threshold voltage can be given to estimate I_d - V_g characteristics by grain size and Si thickness. The proposed model successfully explains a behavior of practical TFT in weak and strong inverted region.

AMDp - 18 Crystallization Mechanism of a-Ge and a-Si Films by SR Soft X-Ray Irradiation

Y. Nonomura, S. Amano, A. Heya, N. Isoda, S. Miyamoto, K. Kanda, N. Matsuo, T. Mochizuki, T. Sadoh^{*}, M. Miyao^{*} Univ. of Hyogo, Japan

*Kyusyu Univ., Japan

We investigatedlow-temperaturecrystallization of a-Ge, a-Si and a-SiGe films by the SR soft X-ray irradiation at storage ring current of 25-220 mA and dose quantity of 50 mA · h. The relationship between electron excitation-atom movement process, thermal process and the storage ring current are investigated.

AMDp - 19 Plasma Annealing of ZnO:Al Capping Layer for Thin-Film Transistors

N. Ohta, Y. Imamura, S. Sato, D. Ohba, H. Shimizu^{*}, H. Shirai

Saitama Univ., Japan ^{*}Saitama Ind. Tech. Ctr., Japan

The rapid thermal annealing of a-Si/SiO₂/ZnO:Al(AZO) heterostructure was studied using the rf thermal plasma jet of argon. The crystallization of Si and AZO layers was enhanced without creating intermixing layer at theSi/SiO₂/AZO interfaces by adjusting the plasma conditions. These findings are effective to improve the TFT performance.

AMDp - 20 Effect of Back-Channel Treatment on the Photo-Leakage Current of a-Si TFTs

C.-Y. Yang, C. Y. Lin, S.-C. Huang, C.-Y. Huang, H.-L. Chen

AU Optronics, Taiwan

Different treatments onto the back-channel region of a-Si TFTs are performed, including different plasma treatments. By comparing namely the "beta" parameter, it is discovered that beta is the smallest under H_2 treatment and the largest as no treatment is performed, which just corresponds to the photo-leakage behaviors under these treatments.

AMD

AMDp - 21 Systematic Measurement of Negative Gate Bias Instability and Application for Power Consumption Display

C.-S. Wei, S.-W. Huang, P. M. Chen, J.-S. Chen, C. T. Peng, W.-M. Huang AU Optronics, Taiwan

Negative bias stress with variously gate bias driving board have several reliability results when gate bias duty ratio and wait time as the next gate bias driving was applied. Results show that permanent degradation and instantly recovery was observed when gate bias driving mode was different.

AMDp - 22 Influence of Silicon Nitride and Amorphous Silicon on the Stability of Amorphous Silicon Thin-Film Transistors

C.-Y. Hou, S.-H. Lin, J.-K. Chang, H.-L. Chen, C.-H. Chen AU Optronics, Taiwan

A systematic study of amorphous silicon (a-Si) TFTs fabrication process with high stability for driver circuit application has been investigated. Using the bias temperature stress measurement, it is discovered that the threshold voltage shift is more dominated by the quality of the active layer than the dielectric layer.

AMDp - 23 Determining Factor of the Preferential Crystal Orientation of the Growth of Microcrystalline Silicon Films by rf PE-CVD of a SiH₂Cl₂ and H₂ Mixture for Silicon Thin-Film Transistors

D. Ohba, Z. Tang, H. Shirai Saitama Univ., Japan

The factor determining the preferential crystal orientation in the growth of microcrystalline silicon films was studied by the rf PE-CVD of a SiH_2CI_2 and H_2 mixture. The sticking process of deposition precursors and/or reconstruction of Si clusters within the subsurface region determines the growth of the preferential (220) crystal orientation.

AMDp - 24 Highly Stabile Amorphous Indium-Gallium-Zinc Oxide TFT with Photosensitivity Organic Passivation Layer for AM-OLED Display

> L. C. Lee, H. C. Ting, F. W. Chang, T. H. Shih, C. W. Chou, H. H. Lu, C. Y. Chen, Y. H. Lin AU Optronics, Taiwan

A method to improve the amorphous IGZO TFTs environment stability is demonstrated in this study. An organic passivation layer without acryl element has high anti-water absorption ability. [1, 2] The TFTs were effective fabricated with good performance by using conventional process.

AMDp - 25 Three TFT Pixel Circuit with Highly Stable OLED Current for AMOLED

K.-W. Chou, C.-C. Hung, F.-C. Chang, C.-L. Lin Nat. Cheng Kung Univ., Taiwan

This work proposes a novel voltage-programming pixel circuit for AMOLED using a-Si:H technology. The proposed 3T1C circuit can stabilize the output current regardless of V_{TH} shift and OLED degradation. Experimental results indicate that the OLED current degradation is less than 3% over more than 16 h of operation.

AMDp - 26 Frequency Characteristics of Solution-Processed Organic Field-Effect Transistors with Self-Aligned Electrodes

T. Nagase^{*,**}, H. Hatta^{*}, Y. Miyagawa^{*}, T. Kobayashi^{*,**}, S. Murakami^{***}, M. Watanabe^{****}, K. Matsukawa^{****}, H. Naito^{*,**}

*Osaka Pref. Univ., Japan **The Res. Inst. for Molecular Elect. Devices, Japan ***Tech. Res. Inst. of Osaka Pref., Japan ****Osaka Municipal Tech. Res. Inst., Japan

We have fabricated the solution-based organic FETs with polymer gate insulators using a self-aligned method and investigated their frequency characteristics. The fabricated organic FETs exhibit electrically stable operation and have extremely low parasitic capacitance. Impedance spectroscopy of organic FETs with self-aligned electrodes reveals frequency-dependent channel formation process in FET structure.

AMDp - 27 Polymer Thin-Film Transistors with a Solution-Processed Passivation Layer

F.-C. Wu, Y.-T. Chen, Y.-W. Jang, H.-L. Cheng Nat. Cheng Kung Univ., Taiwan

Poly(3-hexylthiophene)-based (P3HT) thin-film transistors (TFTs) made from different solvents were fabricated. After covering the P3HT active layers with a solution-processed passivation layer, the mobility of P3HT TFTs was enhanced. We suggest that some vacancies in the P3HT active layers should be filled with solvent molecules to promote carrier transport.

AMDp - 28 Synergistic Effect of Light Illumination and Bias-Stress on Threshold Voltage Shift of Ink-Jet Printed TIPS-Pentacene Thin-Film Transistor

T. H. Hwang, S. H. Lee, S. H. Kim, M. H. Choi, J. Jang Kyung Hee Univ., Korea

We have studied the electrical stability of the ink-jet printed TIPSpentacene TFT with Ag source/drain electrodes. We have measured the gate bias-stress effect in dark, and the gate bias effect under light illumination. The results are discussed with the carrier trappings at the interface and in the bulk.

AMD

AMDp - 29 Anomalous Photocurrent Characteristic at Negative Gate Bias

T. Inoue, M. Tsubuku, M. Takahashi, A. Miyanaga, S. Yamazaki

Semiconductor Energy Lab., Japan

We conducted light irradiation to IGZO TFT at negative bias applied to its gate and found anomalous photocurrent characteristics. On calculation model, we well reproduced this phenomenon by assuming relaxation time with different length for holes and electrons. This analytical technique will be effective in discussing levels in the bandgap.

AMDp - 30 Effects of Additive Elements on TFT Characteristics in Amorphous IGZO Films under Light Illumination Stress

S. Morita, S. Yasuno, A. Miki, T. Kugimiya Kobe Steel, Japan

We have studied effects of additive elements on light-induced threshold voltage (V_{th}) shift in amorphous IGZO TFTs. By addition of Hf or Si, V_{th} shift due to light illumination, negative-bias and thermal stress was successfully suppressed. The suppression could originate from a decrease in hole trap at the gate-IGZO interface.

AMDp - 31 Direct Correlation of Photo Conductivity Decay with Transistor Performance in Amorphous Oxide Semiconductor Films Evaluated by Microwave Photo Conductivity Decay Method

S. Yasuno, S. Morita, A. Miki, T. Kugimiya, F. Ojima*

Kobe Steel, Japan ^{*}Kobelco Res. Inst., Japan

The microwave photoconductivity decay method was applied to evaluate film quality of IGZO, an amorphous oxide semiconductor. The peak reflectivity was correlated with transistor performance. Also, μ -PCD mappings over the films were undertaken. The μ -PCD method was useful to predict device performance of AOS TFTs fabricated under various process conditions.

AMDp - 32 Study on Oxygen-Dependent Instability of Amorphous In-Ga-Zn-O TFT and Completely Stable Device under Both Positive and Negative Bias Stresses

W.-T. Chen, H.-W. Zan, S.-Y. Lo, S.-C. Kao, C.-C. Tsai, J.-H. Lin^{*}, C.-H. Fang^{*}, C.-C. Lee^{*}

Nat. Chiao Tung Univ., Taiwan ^{*}AU Optronics, Taiwan

An experiment is conducted to verify the origin of stress-induced instability in an amorphous indium-gallium-zinc-oxide (a-IGZO) thinfilm transistor. It is found that the oxygen ratio in an IGZO layer strongly influences the device stability under bias stress. For realizing an adequately stable device, post-annealing and passivation are performed in order.

AMDp - 33 Effect of Active Layer Thickness on the Indium-Gallium-Zinc-Oxide TFTs

S.-J. Kim^{*}, S.-Y. Lee^{*}, J.-Y. Kwon^{*}, W.-G. Lee^{**}, K.-S. Yoon^{**}, Y.-W. Lee^{*,**}, M.-K. Han^{*}

*Seoul Nat. Univ., Korea

IGZO TFTs with various active-layer thicknesses were investigated. V_{TH} of TFT with 400 Å activelayer was -0.6 V at R.T. and shifted 0.83 V at 230°C while that of TFT with 700 Å active-layer was -1.2 V and shifted 2.3 V. We have investigated the effect of active-layer thickness on the IGZO TFTs.

AMDp - 34 Channel Dimension and Hysteresis Behavior on ALD-Prepared Transparent ZnO Thin Film Transistor

W.-S. Choi, Y.-J. Kwack, J.-S. Lee, E.-S. Chun Hoseo Univ., Korea

Different thickness of active layer in ZnO bottom-contact thin-film transistors (TFTs) were fabricated by using injector type atomic layer deposition (ALD). The properties of the ZnO TFT were influenced by the active thickness and width-to-length (W/L) ratio of device. The hybrid gate dielectrics were examined to investigate hysteresis behaviors.

AMDp - 35 Shadowmask-Controlled Circuit Fabrication - an Obsolete Technology Resurrected

T. P. Brody, C. E. Harrigal, W. Little Advantech US, USA

Advantech has revived the shadowmask process of manufacturing TFT circuits, which promises low cost, in-line system fabrication of active matrix backplanes and other circuits. We discuss the philosophy and justification of the revived process and report on initial results of color AMOLED and e-paper backplanes.

AMD

AMDp - 36L Evaluation of Hall Effect in Micro Poly-Si Hall Devices to Analyze Electron Transport in Poly-Si Films

H. Hashimoto^{*}, Y. Yamaguchi^{*}, M. Hirako^{*}, T. Yamaoka^{*}, M. Kimura^{*,******}

*Ryukoku Univ., Japan **Joint Res. Ctr. for S&T, Japan ***Innovative Materials & Processing Res. Ctr., Japan

Hall effect in micro poly-Si Hall devices is evaluated to analyze electron transport in poly-Si films. The Hall voltage has offset voltage even when magnetic field is zero. The polarity is reversed when control current is reversed. The offset voltage is caused by zigzag paths of the electron transport.

AMDp - 37L Dependence of Trap Density in SPC Poly-Si TFT on Temperature and Time of Post Annealing

M. Kimura

Ryukoku Univ., Japan

Dependence of trap densities in SPC poly-Si TFTs on post annealing temperature and time is evaluated using low-f C-V characteristics and extraction algorithm. The trap densities can be reduced by increasing the temperature and time, which is brought by the extinction of crystal defects. The activation energy is roughly 2 eV.

AMDp - 38L High-Performance Amorphous InGaZnO Thin-Film Transistors with High-k Sm₂O₃ Gate Dielectrics

F.-H. Chen, Y.-H. Shao, W.-C. Li, T.-M. Pan

Chang Gung Univ., Taiwan

In this paper, we developed high-k Sm₂O₃ indium-gallium-zinc oxide thin-film transistor (IGZO TFTs) with and without RTA treatment. The high-k Sm₂O₃ oxide TFT device annealed at 400°C exhibited better electrical characteristics in terms of a large effective carrier mobility, high-driving current, low-threshold voltage, and high I_{ON}/I_{OFF} current ratio.

AMDp - 39L High-performance LTPS TFT for High-k Tb_2O_3 with CF_4 Plasma Treatment

F.-H. Chen, Z.-H. Li, Y.-H. Shao, W.-C. Li, T.-M. Pan Chang Gung Univ., Taiwan

The high-k Tb₂O₃ poly-Si TFT device using a 20 W plasma power treatment exhibited good electrical performances, including a high effective carrier mobility, a low-threshold voltage, a small subthreshold slope, and a high I_{ON}/I_{OFF} current ratio. It also enhanced electrical reliabilities including hot carrier and positive bias temperature instability.

AMDp - 40L Performance Enhancement of Organic Thin-Film Transistors Using Bathophenanthroline:Cs Electron Injection Layer

J. Kim, H. Son, J. Yang, M. Yi Pusan Univ. of Elec. Eng., Korea

We fabricated organic thin film transistor (OTFT) with Bphen:Cs electron injection layer between organic semiconductor(C_{60}) and metal electrode to improve the electrical performances. Mobility and on-current of the device with Bphen:Cs electron injection layer were increased more than twice compared with the normal device without the injection layer.

AMDp - 41L Predicting Realistic Reliability Using DC Bias Stress

Y.-J. Hsu, M.-H. Lee, J.-T. Peng, W.-M. Huang AU Optronics. Taiwan

A new method was proposed for predicting reliability of TFT during realistic panel operations. Based on traditional bias-temperature stress data, more accurate predictions regarding threshold voltage shift can be obtained and used in real panel operations.

AMDp - 42L Bias Dependent of Threshold Voltage Shift of a-Si:H TFT with DC and AC Stress on the Gate Electrode

S. W. Jeong, D. Y. Park, H. Choi, K. H. Moon, Y. S. Choi, D. H. Koo

LG Display, Korea

We have investigated the threshold voltage shift(ΔV th) of a-Si:H TFTs induced by Bias-Temperature-Stress(BTS) conditions. Our Research showed that, the ΔV th has bias-dependence due to the various DC(direct current) BTS. Also, instead of DC BTS, AC(alternating current) BTS was applied to extrapolate the ΔV th induced by reliability evaluation.

AMDp - 43L Width Dependent Degradation of Amorphous Si:H Thin Film Transistors Due to Self-Heating Effect

D. Y. Park, D. H. Nam, S. W. Jeong, H. Choi, K. H. Hoon, Y. S. Choi

LG Display, Korea

In this paper, we have investigated the channel width effect on the stability of a-Si:H TFTs. Results of this paper show that the electrical stress causes positive V_{τ} shift and subthreshold slop degradation. As the channel width gets wider, the degradation derived under stress is more increased.

AMD

Thursday

AMDp - 44L Gate-Drain-Bias Stress Study of Amorphous In-Ga-Zn-O TFTs

C.-Y. Wu, Y.-C. Kao, C.-Y. Huang, C.-N. Lin, C. H. Chen AU Optronics, Taiwan

The stability of amorphous indium gallium zinc oxide (α -IGZO) TFTs under different gate and drain bias stress is discussed in this paper. The stress effect of different channel-width testkey is also shown in this article.

AMDp - 45L Self-Assembled Monolayer Gate Dielectric for Low Voltage Driving Pentacene Thin-Film Transistors

D. Lee, J. H. Lee, S. W. Kim, J.-S. Kim^{*}, D. Y. Jeon KAIST, Korea ^{*}Imperial College London, UK

In this study, pentacene thin-film transistors were fabricated with n-octadecylphosphonic acid as self-assembled monolayer gate dielectric on a plastic substrate. Also we fabricated pentacene TFTs with SiO₂ dielectric on a Si wafer for comparison. The range of V_G was remarkably decreased from -40 V to -3 V comparing to SiO₂ dielectric devices.

AMDp - 46L Lateral Large-Grained Low-Temperature Poly-Si₁. "Ge" TFTs on Glass Substrate

Y. Okabe, K. Kondo, K. Hirose^{*}, J. Suzuki^{*}, K. Kitahara^{*}, A. Hara

Tohoku Gakuin Univ., Japan ^{*}Shimane Univ., Japan

We fabricated lateral large-grained poly-Si_{0.95}Ge_{0.05} TFTs on glass substrates at a low process temperature of 550°C and obtained a field-effect mobility of 130 cm²/Vs. This value is larger than those of previously reported researches. We realized the fabrication of high-performance TFTs with reduced thermal damage to glass substrates.

AMDp - 47L Solution Process for Metal Oxide Thin Film Transistors under 350°C Post-Annealing

W. H. Jeong, J. H. Bae, K. M. Kim, D. L. Kim, Y. S. Kim, S. J. Kim, H. J. Kim, M.-K. Ryu^{*}, K.-B. Park^{*}, J.-B. Seon^{*}, S.-Y. Lee^{*}

Yonsei Univ., Korea ^{*}Samsung Advanced Inst. of Tech., Korea

We have investigated solution process for metal oxide thin film transistors under post-annealing temperature of 350°C. Process engineering which includes materials, precursors, and gate insulators acts important roles under 350°C post-annealing process for large-area deposition.

16:40 - 18:05

Room 501

AMD5/OLED6: AM-OLED

Chair: D. Pribat, SungKyunKwan Univ., Korea Co-Chair: Y. Fujisaki, NHK, Japan

AMD5/InvitedProcess Development of Amorphous Indium-OLED6 - 1:Gallium-Zinc-Oxide Thin-Film Transistors for Large16:40Size AMOLED Applications

H.-C. Ting, H.-H. Lu, T.-H. Shih, L.-C. Lee, C.-W. Chou, L.-P. Shin, S.-S. Wang, T.-C. Wan, C.-Y. Chen, Y.-H. Lin AU Optronics, Taiwan

In this paper, we will show how to approach a-IGZO TFTs AMOLED in Gen 6 Fab currently. We evaluated the TFTs structure from bottom gate coplanar to BCE type with Mo/AI/Ti as S/D electrode. Using photosensitive organic passivation layer and TiO_x coating to improved the device performance and stability.

AMD5/ High Mobility Oxide Semiconductor TFT for Circuit OLED6 - 2 Integration of AM-OLED

E. Fukumoto, T. Arai, N. Morosawa, K. Tokunaga, Y. Terai, T. Fujimori, T. Sasaoka

Sony, Japan

We have developed a high mobility and high reliability oxide semiconductor TFT which used ITZO as a channel material. Its mobility and Δ Vth after 20,000sec of BTS test were 30.9 cm²/Vs and 0.1 V. We have achieved a stable enhancement type TFT, which realizes circuit integration for AM-OLED.

AMD5/ A New Simple Pixel Circuit Compensating the OLED6 - 3 Threshold Voltage for AMOLED Displays

17:25 Y.-I. Hwang, Y.-S. Park, K.-N. Kim, B.-H. Kim, B. H. Berkeley, S.-S. Kim, B.-D. Choi^{*} Samsung Mobile Display, Korea

^{*}Sungkyunkwan Univ., Korea

We propose new simple pixel compensation circuits with three or four thin film transistors (TFTs) and one capacitor. In addition to compensating the deviation of the threshold voltage of the driving TFTs, we can compensate IR-drops and reduce the number of components in compensation circuits with these novel circuits.

AMD

December 2/3

AMD5/ OLED6 - 4 17:45 4.1-in. Full Color AMOLED Driving by Top Gate Nanocrystalline Silicon Thin Film Transistor Array K.-Y. Ho, H.-C. Lin, H.-S. Dai, P.-F. Lee, C.-C. Hsu, S.-Y. Peng, C.-W. Lin, C.-H. Cheng, B.-C. Kung, W.-Y. Chao, J.-Y. Yan, H.-C. Cheng

ITRI, Taiwan

High performance nanocrystalline silicon thin film transistors are achieved with top gate staggered structure. The nc-Si is directly deposited by 13.56 MHz plasma enhanced chemical vapor deposition (PECVD) at 200°C. Good device perf ormance, uniformity, and reliability make it possible to be integrated into active matrix organic light emitting diode (AMOLED) applications.

Author Interviews 18:00 – 19:00

Friday, December 3

9:00 - 10:1	10 Room 501	
	AMD6: Organic & Carbon TFT	
Chair: Co-Chair:	P. Heremans, imec, Belgium K. Nomoto, Sony, Japan	
AMD6 - 1: 9:00	Invited Organic Single Crystals with Band-Like Transport in Field-Effect Transistors	
	K. Tsukagoshi ^{*, **} , C. Liu [*] , T. Minari ^{*, **}	
	*NIMS-MANA, Japan **CREST-JST, Japan	

We report organic single crystals transistor formed by solution process. A self-organized phase separations to form an amorphous semiconductor film on insulator-polymer by spin-coating the mixture of the semiconductor molecule and insulator-polymer realized the band-like transport with high mobility up to 9.1 cm²/Vs after annealing in solvent vapor.

AMD6 - 2: Invited Field Effect Transistors Based on Organic 9:25 Semiconductors and Graphene

K. Tanigaki, S. Ikeda, X. Fan, R. Nouchi, Y. Wang, N. Mitoma Tohoku Univ., Japan

Organic semiconductors and graphene are described as new field effect transistors (FETs). Graphene shows high mobility as well as long spin coherent length, because of the mass-less Dirac states and the small spin-orbit coupling, relevant in spintronics. Ambipolar carrier injection can be realized in organic semiconductors useful for future optoelectronics.

AMD6 - 3 A Spin Coating Process for High Mobility of Organic 9:50 Transistor

P.-Y. Lo, J.-M. Ding, C.-W. Liu, C.-C. Chou, J.-P. Hu ITRI, Taiwan

We reach device mobility of 2 cm²/V-s in this study. The high mobility OTFT is integrated into a VGA display panel of OTFT-EPD with the Sipix electrophoretic medium for further demonstration.

----- Break -----

10:40 - 12:00	Room 501

AMD7: Oxide TFT (1)

Chair: K. Tanigaki, Tohoku Univ., Japan Co-Chair: K. Azuma, Shimadzu, Japan

AMD7 - 1: *Invited* Characteristic of the Hysteresis on ZnOTFT 10:40 with SiO₂ Gate Oxide

Z. Ye, M. Wong

Hong Kong Univ. of S&T, Hong Kong

Hysteresis in the current-voltage characteristic is observed in a ZnO TFT with silicon dioxide as the gate dielectric; and presently attributed to delay flipping of electric dipoles located at the interface between the dielectric and the channel. Potential application to the realization of an electronic memory element is also reported.

AMD7 - 2 Improvements in the Characteristics of Solution 11:05 Processed Zinc-Tin Oxide Thin-Film Transistors by Adding H₂O in the ZTO Solution

Y.-U. Lee, J.-S. Lee, Y.-J. Kim, S.-H. Cho, B. Kim, Y.-H. Kim^{*}, M.-K. Han Seoul Nat. Univ., Korea ^{*}KETI, Korea

We fabricated solution-processed ZTO TFTs with various ZTO solutions in order to investigate the effect of H_2O on the electrical properties of TFTs. In the case of the ZTO TFT fabricated with H_2O added ZTO solution, the mobility and subthreshold slope were better than those of conventional ZTO TFTs.

AMD

AMD7 - 3 A Novel Method of Low Contact Resistance 11:25 Treatment in Solution Metal Oxide TFT Fabrication

K.-H. Su, C.-C. Yu, Y.-C. Lai, C.-Y. Chien, L.-Y. Lin, J. P. Tseng, F.-W. Chang AU Optronics, Taiwan

In our research, IZO (In_2O_3 -ZnO) prepared by sol-gel method was applied to thin film transistor (TFT) fabrication as semiconductor layer. To protect channel region in a vacuum system and improve the contact interface between metal oxide semiconductor and S/D metal simultaneously, we introduced a half-tone method to IZO TFT device.

AMD7 - 4L High Stability of Inkjet Printed Indium Zinc Oxide 11:45 Thin Film Transistors

K.-B. Park, M.-K. Ryu, J.-B. Seon, K.-H. Lee, S.-Y. Lee, W. H. Jeong^{*}, J. H. Bae^{*}, H. J. Kim^{*}

Samsung Advanced Inst. of Tech., Korea *Yonsei Univ., Korea

We report the fabrication of Indium zinc oxide transistors using inkjet printing. The compositions of dropped IZO films have high stoichiometric characteristics. The IZO field effect transistors were fabricated showing a field-effect mobility of 0.2 cm²/Vs. An electrically and thermally biased stability showed a threshold voltage deviation of 0.66 V for 3 hours.

----- Lunch -----

13:20 - 14:40

Room 501

AMD8: Oxide TFT (2)

Chair: H.-H. Hsieh, AU Optronics, Taiwan Co-Chair: H. Hamada, Sanyo Elec., Japan

AMD8 - 1: Invited Impact of Density of States Near Valence 13:20 Band on Photo-Stability in InGaZnO TFTs

J.-W. Park, W.-G. Lee, G.-S. Youn, D.-H. Lee, S.-H. Cho

Samsung Elect., Korea

From the photo-stability test for InGaZnO TFTs under gate bias, the relationship between threshold voltage shift and DOS near VBM was analyzed. The threshold voltage shift after 3 hours of gate bias stress with illumination decreases to less than 3.5 V due to the reduction of DOS near VBM.

AMD8 - 2 Photo-Current Response and Negative Bias 13:45 Stability Under Light Irradiation in IGZO-TFT

M. Tsubuku, T. Inoue, M. Takahashi, S. Yoshitomi, H. Kanemura, K. Akimoto, A. Miyanaga, S. Yamazaki Semiconductor Energy Lab., Japan

Photo-current response and negative bias stability under light irradiation become issues in using In-Ga-Zn-O thin film for TFT. We report the improved photo-characteristics seen by comparing three TFTs. A sample with good characteristics has small and fast photo-response, and it is expected traps within a band gap would become few.

AMD8 - 3 Transportation Model Establishment of InGaZnO for 14:05 Thin Film Transistor Device Application

L.-F. Teng, P.-T. Liu, Y.-T. Chou, Y.-S. Fan Nat. Chiao Tung Univ., Taiwan

The transportation model of on electrical metastability of a-InGaZnO TFT is established. The generation of oxygen vacancies by the annealing in a vacuum led to an increased I_{off} and large V_{th} shifts, while N₂ and O₂ ambience effectively improve the device performance. A physical mechanism is also reasonably proposed.

AMD

AMD8 - 4L Influence of TFT Structure & Process Condition on 14:25 the Extent of IGZO Stability & Mobility

Y.-C. Kao, C.-N. Lin, K.-Y. Tu, F. Wu, D. Tu, C. Shieh, C. Wu, R. Lin, P. Lu, H.-M. Sung, W.-C. Tsai, C.-H. Chen AU Optronics, Taiwan

IGZO TFT with different structures and process conditions were studied. Structure of BCE type has higher mobility (10 cm²/Vs). The stability & IV uniformity of IGZO TFT is improved by surface modification of IGZO film. The T65/240Hz LCD display driven by IGZO TFT is also fabricated.

----- Break -----

15:00 - 16:05

Room 501

AMD9: Nanodevice & Oxide TFT

Chair: J.-W. Park, Samsung Elect., Korea Co-Chair: H. Kumomi, Canon, Japan

AMD9 - 1: *Invited* Thin Film Transistors with Semiconductor 15:00 Nanowires

D. Pribat

Sungkyunkwan Univ., Korea

Semiconductor nanowires are new nanomaterials, studied for thin film transistors and electronics applications. Although these nanomaterials are usually synthesised at moderate to high temperatures, they can be transferred to any kind of substrate after growth, paving the way for the fabrication of displays and large area electronics systems on plastic.

AMD9 - 2 Amorphous In-Ga-Zn-Oxide TFTs with High Stability 15:25 Against Bias Temperature Stress

N. Saito, T. Ueda, S. Nakano, Y. Hara, K. Miura, H. Yamaguchi, I. Amemiya, A. Ishida^{*}, Y. Matsuura^{*}, A. Sasaki^{*}, J. Tonotani, M. Ikagawa

Toshiba, Japan ^{*}Toshiba Mobile Display, Japan

Detailed investigations of amorphous In-Ga-Zn-Oxide (a-IGZO) TFT revealed that the degradation under bias-temperature stress (BTS) originated from hydrogen-diffusion phenomena. By optimizing the initial a-IGZO film and the intermediate annealing, and lowering hydrogen concentration in insulators, BTS stability was improved. A 3.0-in. OLED panel showed excellent luminance uniformity.

AMD9 - 3 The Instability of a-IGZO TFT Caused by the Drain 15:45 Induced Barrier Lowering (DIBL) and Parasitical TFT

M.-C. Hung, C.-H. Tu, W.-T. Lin, J.-J. Chang, P.-L. Chen AU Optronics, Taiwan

The instability of a-IGZO TFT--including oxygen and water and photosensitivity effect--has been studied widely, but no definitive mechanism was given so far. In this work, the instability caused by the drain induced barrier lowering (DIBL) as well as parasitical TFT was studied and a proposed model was provided.

Author Interviews 16:20 – 17:20

Supporting Organization:

Thin Film Materials & Devices Meeting

16.40 10.00

Doom 400

Workshop on FPD Manufacturing, Materials and Components

Wednesday, December 1

10.40 - 10.00 NOUII 40		
FMC1: Optical Films		
Chair: Co-Chair:	Y. limura, Tokyo Univ. of A&T, Japan M. Miyatake, Nitto Denko, Japan	
FMC1 - 1: 16:40	Invited Vacuum Particle Beam Methods for Alignment of Reactive Mesogens	
	O. Yaroshchuk, R. Kravchuk, E. Telesh [*] , A. Khokhlov ^{**} , O. Parri ^{***}	
	NAS of Ukraine, Ukraine [*] Belorussian State Univ. of Informatics & Elect., Belarus ^{**} Izovac, Belarus	
	Merck Chems., UK	

The vacuum particle beam processes of liquid crystal alignment are successfully extended to reactive mesogens (RMs). In this series, etching process is preferable for planar/tilted alignment, while deposition processes for homeotropic alignment. Combining these processes various laminated and patterned structures are realized showing attractive solutions for optical and electronic films.

FMC1 - 2 Negative Dispersion Retarder for 3D TV Applications

A. Geivandov, A. Lazarev, P. Lazarev^{*}, S. Palto^{*,**}

Crysoptix, Japan ^{*}Kontrakt, Russia ^{**}Inst. of Crystallography RAS, Russia

Crysoptix has developed lyotropic liquid crystal (LLC) materials for manufacturing coatable LCD retarders. LLC coated on plastic substrates produces a negative dispersion TBF[™] retarder that provides an efficient optical compensation of LCD and can be used for 3D LCD applications: circular polarizers for screens and goggles; patterned retarders for stereoscopic imaging.

FMC1 - 3 Low-Reflective Wire-Grid Polarizers Exhibiting High 17:20 Performance in Visible Region

A. Takada, T. Yamada, N. Hanashima, K. Sasaki, E. Takahashi, M. Suzuki^{*} Sony Chem. & Info. Device, Japan ^{*}Kyoto Univ., Japan

We have developed low reflective wire-grid polarizers in visible region. The structure consists of absorptive layer/gap layer on wire-grid. Both the high transmittance and low reflectance in the desired wavelength range have been achieved by the selection of absorptive material and the optimization of the thickness of each layer.

FMC1 - 4Adhesive Design of Transparent PSA Sheets for17:40Multi-Function Mobile-Use Display

H. Fumoto, H. Kishioka Nitto Denko, Japan

LUCIACS series is transparent PSA sheets. It is suitable for laminating of Multi-Function Mobile-Use display such as touch panels. The new adhesive could be designed without acid components and it is optimum for the capacitive type touch panel.

Author Interviews 18:00 – 19:00

Thursday, December 2

9:00 -12:00	Poster/A.I. Room
Poster FMCp: FPD Manufactur	ing, Materials & Components

FMCp - 1Light Guide with Reverse-Cone Textures for9:00Sheetless Backlight

C. G. Son, S. K. Hwang, J. S. Gwag, J. H. Yi, J. H. Kwon, G. Park^{*}, W. T. Moon^{**}, S. H. Kim^{**}, B. K. Kim^{**}, S.-H. Kang^{*}

Yeungnam Univ., Korea *Sunlin Univ., Korea **LG Display, Korea

A lightguide panel with reverse-cone array textures on the top surface is designed and fabricated to develop a sheetless edge-lit backlight. The optimum structure of reverse-cone texture was obtained by simulation and a lightguide without any prism sheet was fabricated by attaching the reverse-cone textures by using UV resin.

FMCp - 2 Brightness Enhancement in LCDs Using the High Color Temperature (HCT) of Panel

H. J. Wang, Y. J. Kim, S. W. Lee, I. C. Park, M. C. Jun, I. J. Jung LG Display, Korea

Brightness improvement of LCD was achieved nearly 6% by means of high color temperature (HCT) of panel and lamp tuning. A new high transmittance property of blue resin was designed to achieve HCT of panel. For the compensation of panel color temperature down, high luminance lamp was used.

FMCp - 3 One Dimensional Coupler Lens for LED Collimation

W.-H. Yang, H.-H. Lin, C.-J. Hsu, Y.-N. Pao ITRI, Taiwan

We have developed a one dimensional coupler lens for LCD Backlight. At the optimum curvature and size, the light out through the lens has a high-collimating emitting property, in which the simulation FWHM is smaller than 1.8°. The FWHM of the prototype is collimated to 5.07°.

FMCp - 4 Design of LED Illumination Devices Based on Reflectors

B.-W. Lee, J. H. Lee, J.-H. Ko, J. Wang^{*}, H. Kim^{*} Hallym Univ., Korea [°]GLS, Korea

LED illumination devices based on reflectors were designed to realize specific illuminating distributions and compared to those based on lenses. Both reflector-based and lens-based LED lighting devices showed the targeted distributions satisfactorily. However, reflector-based devices exhibited higher optical efficiencies compared to lens-based devices due to reduced light losses.

FMCp - 5 Withdrawn

FMCp - 6 7-in. Field Emission Backlight Unit Assembled for LCD Panel with TiO₂ Coated Spacer

M.-T. Chian, W.-C. Shih^{*}, J.-M. Jeng^{*}, Y.-L. Lee^{*}, P.-T. Tai^{*}, C.-H. Cheng^{*}, J. Lo^{*}

Chunghwa Picture Tubes, Taiwan ^{*}*Tatung Univ., Taiwan*

The field emission backlight unit for LCD panel was fabricated in this work. In order to avoid the space charge on the spacer, the spacer is coated with TiO_2 which acts as the charge-leakage layer. By introducing the TiO_2 coated spacers, the assembly of the FEBLU becomes very easy.

FMCp - 7 Withdrawn

FMC

FMCp - 8 Properties of Transparent Conducting IZTO Electrode Deposited at Room Temperature

Y. D. Ko, J. Y. Kim, H. C. Joung, D. J. Son^{*}, D. G. Jung^{*}, B. H. Choi^{**}, Y. S. Kim^{***}

Samsung Mobile Display, Korea ^{*}Sungkyunkwan Univ., Korea ^{**}Korea Inst. of Ceramic Eng. & Tech., Korea ^{***}Seoul Nat. Univ. of Tech., Korea

IZTO films have been deposited by pulsed DC magnetron sputtering onto glass substrate to investigate the effect of oxygen partial pressure. The structural, electrical, optical properties were analyzed. In addition, the grown IZTO films were used in fabrication of organic-emitting diodes (OLEDs) as anode to study the device performances.

FMCp - 9 Electrical Property Improvements by Inserting Buffer Layer for Impurity-Doped ZnO Transparent Electrodes Prepared by Magnetron Sputtering Depositions

J. Nomoto, T. Hirano, T. Miyata, T. Minami Kanazawa Inst. of Tech., Japan

Improvements of obtainable resistivity in AI- or Ga-doped ZnO (AZO or GZO) thin films prepared by magnetron sputtering depositions were successfully achieved by inserting a very thin buffer layer. A resistivity of approximately $3 \times 10^{-4} \Omega$ cm was obtained in 150-nm-thick-GZO and -AZO thin films prepared on glass substrates at 200°C.

FMCp - 10 Effects of Superimposing RF Power on the Preparation of Impurity-Doped ZnO Transparent Electrodes by DC Magnetron Sputtering

J. Nomoto, T. Hirano, T. Miyata, T. Minami Kanazawa Inst. of Tech., Japan

The effects of superimposing RF power on the preparation of transparent conducting impurity-doped ZnO films by d.c. magnetron sputtering depositions were investigated for transparent electrodes used in FPDs. Superimposing appropriate RF power produced a decrease in both deposition damage and obtainable resistivity as well as an increase of deposition rate.

FMCp - 11 Improving S/D Resistance in Zinc Tin Oxide TFT with Atmospheric Plasma Surface Treatment

S. J. Oh^{*,**}, Y. H. Kim^{*}, J. W. Kang^{**}, M. S. Oh^{*} ^{*}KETI, Korea ^{**}Dankook Univ., Korea

Atmospheric plasma treatment of zinc tin oxide (ZTO) surfaces has been studied and demonstrate to be efficient method in improving the performance of TFT characteristics. Our result suggest that atmospheric plasma treatment is a cheaper, more convenient, and more efficient method than low-pressure plasma treatment for improving device performance.

FMCp - 12 Optimisation of a Mass Analyzed Multiple Beamline for the Ion Implantation of Very Large FPD Substrates

D. Aitken Superion, UK

Beam extraction from a large area source with an array of parallel long double extraction slots is optimized using magnetic fields to minimize plasma losses between these double slots. This paper also introduces a variable geometry analyzing magnet giving control of resolving power and the transmitted ion mass range.

FMCp - 13 Development of Dose Distribution Control as a Countermeasure against Pressure Variations Resulted from Photoresist Outgassing

T. Matsumoto, K. Imai, M. Konushi, K. Orihira, Y. Nakazawa, M. Onoda, K. Nakao, Y. Inouchi, J. Tatemichi, M. Konishi, M. Naito

Nissin Ion Equipment, Japan

An accurate dose distribution control system was developed for an ion implanter for LTPS-TFT to improve dose uniformity under photoresist outgassing. Excellent uniformity was exhibited even in a case of a gas pressure increase of one order of magnitude. The system does not have a negative impact on the throughput.

FMCp - 14 Organic Light-Emitting Diodes Fabrication by Electrospray Deposition Process

W. T. Hwang, N. H. Kim, H. Y. Chae Sungkyunkwan Univ., Korea

We have demonstrated organic light emitting diodes (OLED) fabrication with electrospray deposition (ESD) as a solution process alternative. OLED fabricated with ESD shows good performance in terms of surface smoothness and brightness. Current efficiency (cd/A) of device which is fabricated by ESD shows better performance than that of spincoated device.

FMCp - 15 Optimum Design of Single-Slit Mask Applied for High Performance TFT-LCDs

S.-J. Choi, Y.-S. Im, G.-B. Hui, F. Zhang, K.-Y. Kim^{*}, W.-S. Yoon^{*}, J.-S. Xue, J.-Y. Lee

BOE Tech. Res. Inst., China *Beijing BOE Display Tech., China

Optimum single slit mask design applied by gray-tone photolithography had been established by simulation and experiments. We found out that transmittance of single slit was influenced by TFT channel length, size and shape. We obtained optimum design factor of single slit and achieved a fine channel to improve TFT characteristics.
FMCp - 16 Analysis and Fabrication of PSS Technology Applied in TFT-LCD Displays

C. W. Su, A. Mochizuki^{*}, J. T. Lien Chunghwa Picture Tubes, Taiwan ^{*}Nano Loa, Japan

We have succeeded to achieve 1.7 μ m cell gap thickness and good liquid crystal alignment. In finally results, the response time (rising time and falling time) is less 1 ms. However, PSS technology is compatibility in an LC panel mfg with conventional mfg lines. Besides, we also have succeeded to develop 15.4-in. PSS-LCD.

FMCp - 17 New Structure of Transflective LCD without HMDS

Y. Wu, J. Ma, S. Huo, X. Luo, Z. Xia, Z. Ling Shanghai Tianma Micro-Elect., China

An approach of coating organic material onto the silicon nitride insulate layer without HMDS process is invented, eliminating the peeling off phenomenon originated from the etching undercut. The panel process is simplified, and a fully function sample is fabricated.

FMCp - 18 Transparent Conductive Film Incorporating Silver Halide Photographic Technologies

T. Kuriki, A. Ichiki, K. Yokota FUJIFILM, Japan

Fujifilm has developed "EXCLEAR", a new transparent conductive film based on silver-halide photography technologies, offering advanced transmittance, advanced flexural performance and wider sheet resistance ranging from ultra-low (0.2 ohm/sq) to high (several thousand ohm/sq) with the combination with inorganic / organic transparent conductive materials.

FMCp - 19 Wettability Improvement by Silica Nanoparticle for TIPS-Pentacene

K. Matsukawa, S. Yamazaki^{*, **}, S. Tokai^{*}, M. Yoshikawa^{**}, T. Nagase^{**}, T. Kobayashi^{**}, Y. Michiwaki^{***}, S. Watase, M. Watanabe, H. Naito^{**}

Osaka Municipal Tech. Res. Inst., Japan ^{*}Citizen Holdings, Japan ^{**}Osaka Pref. Univ., Japan ^{***}Fuso Chem., Japan

It is essential to control the wettability of soluble organic semiconductors on gate dielectrics for organic field-effect transistors using solution processes. We found that the addition of a small amount of silica nanoparticles (SNPs) drastically improves the wettability of soluble organic semiconductor of 6,13-bis(triisopropy lsilylethynyl)pentaceneonto the hydrophobic gate dielectric of poly (methylsilsesquioxane).

FMCp - 20 Photo-Patternable Silicon-Organic Hybrid Glass with Silsesquioxane Derivatives

T. Fuke, D. Yokoyama, Y. Tashiro, T. Sekito, T. Nonaka AZ Elect. Materials, Japan

We succeeded in development of photo-patternable Silicon-Organic Hybrid Glass with siloxane derivatives comprised of silsesquioxane incorporated with silica unit. The cured film has high optical transparency, thermal stability and chemical durability together with excellent photolithographic property. Here we demonstrate successful usage of photo-patternable silicon-organic hybrid glass materials and lithography patterning.

FMCp - 21 Interface Engineering with a Hole-Transporting SAM for Organic Electronics

C.-L. Lin, W.-S. Hsieh, S.-M. Chang Nat. Taipei Univ. of Tech., Taiwan

A series of organic compounds based on triphenylamine were designed with two substitute groups and a carboxyl group, which was connected to TiO_2 surface by self-assembled monolayers (SAMs). The modified TiO_2 was applied in organic electronics and measured the optical properties to confirm the characteristic of light-harvesting.

FMCp - 22 Evaluation of TIMs on Thermal Dissipation Performance for Power LEDs

P. F. Ji, B. H. Kim, W. K. Hong, C. H. Moon Hoseo Univ., Korea

This experiment evaluates the function of TIMs in thermal management by comparing the effects of TIMs and ceramic substrates on thermal dissipation performance for high power LEDs. It was demonstrated that ceramic substrate gave a bigger change than TIMs in thermal dissipation characteristic.

FMCp - 23 Properties of Transparent Conductive Ga-doped ZnO Films in Bending

K. Nagamoto, Y. Matsubayashi, T. Kondo, Y. Sato^{*}, H. Makino^{*}, N. Yamamoto^{*}, T. Yamamoto^{*}

LINTEC, Japan *Kochi Univ. of Tech., Japan

Transparent conducting polycrystalline Ga-doped ZnO (GZO) films were deposited on polyester substrates by ion-plating deposition with direct current arc-discharge at process temperature of less than 100°C. We evaluated the mechanical bending properties of GZO films and obtained the relationship between bending properties of GZO films and process temperature.

FMCp - 24 Passivation Effect of F+Y Monolayer on Yttria-Stabilized Zirconia (YSZ) Layers of LTPS

S. Horita JAIST, Japan

Crystallized Si films are obtained on glass substrates covered with poly-YSZ layers at temperature lower than without YSZ by over 100°C. From XPS analysis, we proposed F+Y monolayer formation on the chemically cleaned YSZ layer, which supports Si crystallization. Crystallization model with it can explain the results quantitatively.

FMCp - 25 Atmospheric Plasma and Process for Liquid Crystal Alignment

O. Yaroshchuk, R. Kravchuk, S. Pogulyai, V. Tsiolko NAS of Ukraine, Ukraine

The method of liquid crystal alignment is developed based on combination of atmospheric plasma and rubbing processes. In this tandem, rubbing insures uniformity, while plasma process provides tuning of anchoring parameters. High-quality alignment is realized with a pretilt angle controlled in the range 0° - 90° . The samples demonstrate excellent electro-optic performance.

FMCp - 26 Effective Method for Electrode Pattern Positioning in Touch Screen Panel

S.-J. Seok, Y.-J. Park, S.-H. Park, O. Kim Pohang Univ. of S&T, Korea

We propose the effective way of internal electrode pattern positioning in projected capacitive touch screen panel. By changing the way of alignment, the distance, and height between two electrodes, we estimate capacitance values and the change of each value using a simulator. Finally we present a proper example of placement.

FMCp - 27L Enlargement of Polycrystalline Si Grain on Polycarbonate Substrate Prepared by Conventional Laser Annealing

N. Kawamoto, T. Imamura^{*}, Y. Tomizawa^{*}, K. Tadatomo

Yamaguchi Univ., Japan *Teijin, Japan

In this paper, we discuss the crystal growth mechanism of polycrystalline Si grain by conventional laser annealing on polycarbonate substrate. We show the polycrystalline Si grain of diameter with over 150 nm by conventional laser annealing on polycarbonate substrate.

FMCp - 28L Display Performance of PSVA-LCD Using Reactive Mesogen Monomer Induced Alkyl Spacer

R. Kawakami, S. Niiyama, Y. Nakagawa^{*}, Y. Soda^{*} Asahi Glass, Japan ^{*}Optrex, Japan

We proposed a novel UV curable reactive mesogen (RM) monomer for Polymer-Stabilized Vertical Alignment (PSVA) LCD. The experimental results reveal that the PSVA by the novel RM monomer realizes less image sticking and better response time. In addition, the novel monomer needs less UV irradiation energy to be cured.

FMCp - 29L Dye Absorption Properties of the TiO₂ Electrodes Coated with Al₂O₃ for a Dye Sensitized Solar Cell(DSSC)

S.-C. Choi, H.-S. Lee, S.-H. Sohn Kyungpook Nat. Univ., Korea

The surface of TiO₂ electrode in the DSSC was coated with Al₂O₃ nanoparticles by a sol-gel method. Because Al₂O₃-coated TiO₂ (pH9.48) is more basic than bare TiO₂(pH3.9), the higher basicity of Al₂O₃-coated TiO₂ surface favors dye attachment through its carboxylic acid groups. Thus dye absorption of Al₂O₃-coated TiO₂ is enhanced.

FMCp - 30L Surface Modification of the TiO₂ Electrode for Dye Sensitized Solar Cells (DSSCs)

H.-S. Lee, S.-C. Choi, S.-H. Sohn Kyungpook Nat. Univ., Korea

The surface of TiO₂ electrode, photo-anode in DSSCs, was coated with SiO₂, Al₂O₃ nanoparticles in simple surface treatment way, a kind of the modified sol-gel method. It is found that the surface coating of TiO₂ electrode with nanoparticles is dependent on the concentrations of precursors and pH of TiO₂ suspensions.

FMCp - 31L The Investigation on the Relation between CD Bias and SD Layer Area on the Glass Substrate

Z. Weifeng, X. Jianshe, L. Xiang, H. Guanbao, Z. Feng BOE Tech. Group, China

The relation between CD bias and SD layer area on the glass substrate has been investigated. It is found GTM and HTM's situation is different. HTM CD Bias has an increasing trend while SD layer area increases. But GTM CD bias doesn't change. The difference is caused by transmittance difference.

FMCp - 32L Spin-Coatable Gate Dielectric for Organic Thin Film Transistor

Y. Isogai, T. Katoh, K. Sugitani, T. Hirano, M. Tada, Y. Fujisaki^{*}, Y. Nakajima^{*}, T. Yamamoto^{*}, T. Suzuki ZEON, Japan ^{*}Japan Broadcasting, Japan

We have developed spin-coatable gate dielectric for flexible organic thin film transistor. It is applicable to P-type and N-type organic semiconductor with stable TFT characteristics. Under long term bias stress to gate, little hysterisis and threshold shift was detected. It can meet the cost reduction of manufacturing flexible displays.

FMCp - 33L Quasi-Single-Crystal Si Thin Film for System on Panel Using SiGe Precursor and Laser Lateral Crystallization

A. Hara, K. Hirose^{*}, J. Suzuki^{*}, K. Kondo, K. Kitahara^{*} Tohoku Gakuin Univ., Japan ^{*}Shimane Univ., Japan

We have fabricated a quasi-single-crystal (QSC) Si thin film on glass substrate with a SiGe film as a precursor using cw laser lateral crystallization. The fabricated QSC Si film is poly-Si; however, most of the grains, which have large and ribbon-like shape, have {111} surface orientation and <011> growth direction.

FMCp - 34L Low-Hydrogen-Content Transparent SiNx Film Prepared at Low-Temperature by Surface-Wave-Plasma CVD

S. Ueno, M. Yomogida^{*}, M. Suzuki, Y. Konishi, K. Azuma

Shimadzu, Japan ^{*}Shimadzu Emit, Japan

We have succeeded in obtaining transparent SiN_x films with a water vapor transmission rate (WVTR) of less than $1x10^{-6}$ g/m²/d. We developed a surface-wave-plasma CVD system and found that the WVTR of the SiN_x film could be controlled by changing the distance between the plasma and the substrate.

FMCp - 35L Highly Foldable Polarizer Film for Anti-Reflection of OLED Display

H. S. Shim, H.-J. Kwon, S. Kim, Y. T, Chun, I. S. Kee, S. Y. Lee, S. O. Hwang^{*}, Y. W. Kim^{*}, H.-R. Chung^{*},

C. S. Lee*

Samsung Elect., Korea ^{*}Cheil Inds., Korea

Development and evaluation of highly foldable polarization film for antireflection of AMOLED display is described. This film can be folded up to 100,000 times at about 1.6 mm radius while maintaining the 90% transparency and anti-reflectivity as the conventional one.

FMCp - 36L Improvement of Light Extraction Efficiency in Mercury-Free Flat Fluorescent Lamp(MFFL) using Sub-Wavelength Structures

B. J. Oh, J. C. Jung, I. W. Seo, O. Kwon, K.-W. Whang Seoul Nat. Univ., Korea

Sub-wavelength structures and formed on the surface of mercury-free flat fluorescent lamp(MFFL) front glass plate using CF₄ and O₂ plasma etching. Transmittance and light extraction efficiency of MFFL improved through the sub-wavelength structures formed on the glass surface which effectively has gradient refractive index change.

FMCp - 37L An Edge-Lit Backlight Unit with a Newly Designed Asymmetric Pyramid Sheet

M. Lee, S.-T. Hur^{*}, S.-W. Choi^{*} Vinnosys, Korea ^{*}Kyung Hee Univ., Korea

An edge-lit backlight unit (BLU) for small size liquid crystal display (LCD) was suggested. In this BLU, a newly designed single pyramid sheet replaced the two orthogonally placed prism sheets used for collimating.

FMCp - 38L Effect of CuO Nanoparticles Mixed in PEDOT:PSS Buffer Layer on Organic Solar Cells

Sang Hoon Oh, Jung Joohye, Hyun Jae Kim Yonsei Univ., Korea

In this research, the effect of poly(3,4-ethylendioxythiophene):

poly(styrenesulfonate) (PEDOT:PSS) buffer layer with CuO nanoparticles on organic solar cell was investigated. CuO nanoparticles mixed in PEDOT:PSS film can improve short circuit current density due to their low resistivity. This method can contribute to get high efficiency organic solar cells.

----- Lunch -----

15:00 - 16:00

Room 204

FLX7/FMC6: Materials & Components for Flexible Displays

Chair:	T. Tomono, Toppan Printing, Japan
Co-Chair:	T. Ogura, Nippon Steel, Japan
FLX7/ FMC6 - 1 15:00	Transparent High Barrier Coating on Flexible Film Substrate by Roll to Roll PECVD System H. Tamagaki, T. Okimoto, T. Segawa Kobe Steel, Japan

A new Roll to Roll PECVD System, which generates plasma between a pair of rollers, is developed for the deposition of SiOx transparent high barrier coating on film. At SiOx deposition, the deposition rate of 900 nm-m/min and barrier performance (WVTR) below 5x10⁻⁴ g/m²day is demonstrated.

FLX7/Robust Folding Structure for a Foldable DisplayFMC6 - 2H.-J. Kwon, H. S. Shim, S. K. Kim, Y. T. Chun, I. S. Kee,
S. Y. Lee

Samsung Advanced Inst. of Tech., Korea

Design and analysis of folding structure applied hyperelastic material for foldable display are described. This structure allows to realize extendable and foldable large display using conventional glass panels. From Finite Element Method (FEM) analysis and mechanical and optical experimental results, we can confirm the design of more stable folding structure.

 FLX7/
 Direct Connection of LSI Chips to Polyethylene

 FMC6 - 3
 Naphthalate Using Au Cone Bump

 15:40
 T. Shuta, N. Watanaba, A. Wada, T. Higashimashi^{*}

T. Shuto, N. Watanabe, A. Ikeda, T. Higashimachi^{*}, T. Asano Kyushu Univ., Japan

^{*}Sojo Univ., Japan

We show that the direct connection of LSI chip to PEN (polyethylene naphthalate) film can be realized by using Au cone bump for flexible display. More than 10,000 connections at 20 μ m pitch with low resistance can be realized at 150 °C.

----- Break -----

Author Interviews 18:00 - 19:00

Friday, December 3

9:00 - 10:20 Room 409

FMC2: Manufacturing Technologies (1)

Chair: F. Pieralisi, Appl. Materials, Germany Co-Chair: K. Miyazawa, Chisso, Japan

FMC2 - 1 Split Sputter Mode - A Novel Deposition Method for 9:00 TFT Metallizations

F. Pieralisi, M. Hanika, E. Scheer, M. Bender Appl. Materials, Germany

The novel Split Sputter Mode (SSM) method, based on the superposition of two complementary film distributions, provides highly uniform and homogeneous metallization layers. An analytical model is presented and the critical deposition parameters are evaluated. Finally, the effectiveness of the SSM technique is demonstrated through aluminium-coated large area substrates.

FMC2 - 2Development of Sputtering Process for IGZO TFT on9:20Large Substrate

T. Yukawa, T. Kurata, M. Arai, J. Kiyota, S. Sato, K. Takahashi, S. Ishibashi, K. Saito ULVAC, Japan

In recent years, In-Ga-Zn-O (IGZO) has been drawing attention as high mobility material for panel performance improvement. In this report, we discuss uniformity of IGZO deposited by vertical type AC Magnetron Sputtering Equipment that is most widely used in the panel production line of more than Gen. 6 size.

FMC2 - 3 Microstructure Analysis and Electrical Properties of 9:40 Cu-Mn Electrode for Back-Channel Etching a-IGZO TFT

P. Yun, J. Koike Tohoku Univ., Japan

Cu-Mn alloy was investigated as an electrode on a-IGZO film because of its good adhesion, a diffusion barrier and a wet etching selectivity of about 10:1 with IGZO film. Contact property showed non-linear behavior with Al and Cu, while Ohmic contact was obtained with Cu-Mn and Ti after annealing.

FMC

FMC2 - 4Role of Oxygen Atoms in the Growth of Magnetron10:00Sputter-Deposited ZnO Films

A. Morita, I. Watanabe, H. Shirai Saitama Univ., Japan

Among various deposition methods of ZnO films, a magnetron sputtering has been most widely used for fabricating ZnO films in large area at low cost. However, the role of oxygen atoms in the growth is still controversial. We demonstrate the role of oxygen atoms in the growth of ZnO films.

----- Break -----

10:40 - 12:00			Room 409

FMC3: Manufacturing Technologies (2)

Chair: K. Miyazawa, Chisso, Japan Co-Chair: T. Takeda, Nagase ChemteX, Japan

FMC3 - 1 Electroless Cu Metallization for FPD Manufacturing

B. Beck, B. Dosse, F. Brüning, J. Etzkorn Atotech Deutschland, Germany

The feasibility of using wet chemical copper deposition for Thin Film Transistor gate metallization was demonstrated. Environmentally friendly processes were then developed that produced adherent copper deposits on smooth molybdenum layers. The samples were characterized by means of Interference Microscopy, 4-Point Probe Measurement, FIB/SEM and Tape Test.

FMC3 - 2 Enhancement of Scribing Stability for Laminated 11:00 TFT-LCD

C.-H. Tseng, Y.-C. Liu, M.-S. Chen, T. Huang AU Optronics, Taiwan

Reducing the thickness of LCD panels enhance the aesthetic and ease use of portable devices. Laminated cells have a potential issue of unstable control during scribing process. In this study, we illustrated a new design which enhances the supportability and offers a reliable status during scribing for laminated cells.

FMC3 - 3Novel Structure of Acoustic Inkjet Method for11:20Dispensing Large Phosphor Particles

Y. Nomura, Y. Hosono, K. Higuchi, S. Enomoto, I. Amemiya Toshiba, Japan

A novel acoustic inkjet method with a conveyed film has been investigated for stable ink supply and droplet ejection of ink containing large-phosphor-particles. High accuracy of ejected droplet volumes (5%) was proved in the case with water used as ink. Moreover, droplets containing 20-micrometer-phosphors were ejected by the novel method.

FMC3 - 4Layout and Process Optimization Using Proximity11:40Exposure Lithography Simulation

B. Meliorisz, U. Hofmann, N. Unal, J. Sachen GenISys, Germany

This paper presents the benefits of using optical proximity lithography simulation for process and OPC development, layout optimization and verification. The simulation provides accurate optical, image formation and resist processing results. We show several examples that demonstrate how simulation can contribute to improving lithography processes when using proximity printing exposure.

----- Lunch -----

Room 409

FMC4: Materials (1)

Chair: Z. Liang, Corning Display Tech., USA Co-Chair: R. Yamaguchi, Akita Univ. Japan

FMC4 - 1: Invited Post-Modern FPD Manufacturing -13:20 Environmentally Sustainable Facility Construction and Operation, and Lessons from Adjacent Industries

D. Carkner, M. O'Halloran, T. Johnson, A. Maule CH2M HILL, USA

A review of techniques for improved efficiency, environmental responsibility, and cost performance in FPD manufacturing, informed by examples of successful methods used in adjacent industries, such as semiconductors, solar PV, and data centers. Practical examples of energy, water, and materials savings achieved together with cost and schedule reductions are provided.

FMC4 - 2: *Invited* Tunable Microwrinkles for Display Device 13:40 Elements

T. Ohzono, H. Monobe, Y. Shimizu AIST, Japan

Microwrinkles on a surface-modified soft elastomer form under lateral compression through surface Euler's buckling. The wavy microstructures are reversibly altered by adding strain. We briefly review the transformation of microwrinkles and the preliminary applications: liquid crystal alignment, liquid micromanipulation and microswitch array, which are applicable to the display device elements.

FMC4 - 3LCD Performance and Evaluation on Substrate14:00Surface

Z. Liang, R. Greene, R. Schweiger, R. White, X. Zhang^{*} Corning, USA ^{*}Dalian Maritime Univ., China

TN mode LC cells with 4 μ m cell gap were fabricated using glass samples with variety of SDs. The threshold cell gap variation for JND=1 is about 0.15 μ m which is in good agreement with human eye direct inspection. JND reading is a good predictor to evaluate spots mura.

FMC4 - 4Ultra Fine Pitch Anisotropic Conductive Film with14:20Fixed Array of Conductive Particles

R.-C. Liang, Y. Morita, S. Tseng, S. Rokutanda, J. Chung, J. McNamara, Z.-A. G. Wu, Trillion Science, USA

Ultra fine pitch Anisotropic Conductive Adhesive Film with fixed array of conductive particles has been developed and manufactured. This novel ACF has demonstrated superb performance at less than 10 μ m pitch in LCD driver IC bonding. Conductive particles are arranged in array pattern providing uniform contact resistance with reliable performance.

----- Break -----

15:00 - 16:20

Room 409

FMC5: Materials (2)

Chair: D. L. Schulz, North Dakota State Univ., USA Co-Chair: T. Nonaka, AZ Elec. Mat., Japan

FMC5 - 1: Invited Development of Low Temperature Solution-15:00 Processed Metal-Oxide TFT Materials

J. Steiger, R. Anselmann, H. Thiem, A. Hoppe, D.-V. Pham, A. Merkulov Evonik Degussa, Germany

We will present recent developments at Evonik in regard to material synthesis and solution based processing techniques of metal oxides for the use in TFT applications. Mobilities of higher than 10 cm²/Vs in bottom-gate devices at a processing temperature of 350°C will be demonstrated.

FMC5 - 2: *Invited* Electrospun a-Si using Liquid Silane/Polymer 15:20 Inks

D. L. Schulz, J. M. Hoey, J. Smith, J. Lavaasen, C. Braun, X. Dai, K. Anderson, A. Elangovan, X. Wu, S. Payne, K. Pokhodnya, I. Akhatov, L. Pederson, P. Boudjouk North Dakota State Univ., USA

Amorphous silicon nanowires (a-SiNWs) were prepared electrospinning cvclohexasilane bv $(Si_{6}H_{12})$ admixed with polymethylmethacrylate (PMMA) in toluene. Raman spectroscopy characterization of these wires (d~50-2000 nm) shows 350 °C treatment yields a-SiNWs. Porous a-SiNWs are obtained using a volatile polymer.

FMC5 - 3 Characterization of New Silsesquioxane and 15:40 Silsesquiazane Polymers

Y. Tashiro, T. Fuke, T. Sekito, D. Yokoyama, T. Nonaka AZ Elect. Materials, Japan

We succeeded in development of new silsesquioxanes and silsesquiazanes by new synthesis method. New Silsesquioxanes (SQ) are low temperature curable and provide superb pencil hardness and high optical transparency. And new silsesquiazanes (SQAZ) provide high refractive index and high optical transparent film. Here we demonstrate properties as new coating material.

FMC5 - 4Intrinsically Conductive Polymer Dispersions and16:00Inks for Transparent Electrode

T. Isaji, M. Abe

Nissan Chem. Inds., Japan

Organic solvent dispersions and inks of intrinsically conductive polymer (polyaniline based) with high conductivity have the possibility to be used for transparent electrode.

Author Interviews 16:20 – 17:20

Supporting Organizations:

The Japan Society for Printing Science and Technology Japan Society of Colour Material The Technical Association of Photopolymers, Japan Society of Photographic Science and Technology of Japan The Society of Radtech, Japan The Japanese Research Association of Organic Electronics Materials

Japan Electronics Packaging and Circuits Association

Workshop on Plasma Displays

Thursday, December 2

13:20 - 14:40

Room 501

PDP1: Panel Configuration

Chair: L. F. Weber, Consultant, USA Co-Chair: R. Murai, Panasonic, Japan

PDP1 - 1: Invited Technology for 3D PDPs at LG Electronics

S.-H. Moon, D.-H. Kim, J.-H. Lee, J.-M. Ra, M.-J. Jeon, K.-R. Choi

LG Elect., Korea

Recently, the market of 3D TVs has become larger. LGE has developed 3D PDP TV and released these models at July. Also, LGE has successfully developed a prototype 3D Multi-vision display of 180-in. screen which consists of 9 sub-modules of 60" PDP TV.

PDP1 - 2 50-in. Full HD Shadow Mask PDP

13:40 Z. Fan^{*,**}, X. Zhang^{*,**}, Z. Wu^{*,**}, Y. Tu^{*}, L. L. Yang^{*}, B. P. Wang^{*,**}, Q. Zhang^{*} ^{*}Southeast Univ., China ^{**}Nanjing Huaxian High Tech., China

The research of discharge performance of SMPDP with 0.19 μ m×RGB ×0.57 μ m pitch, rectangular cell and Delta arrangement is done on experimental platform. It proves high-resolution can be realized through optimization of cell structure and parameter, without affecting the performance. The 50-in. FHD SMPDP is developed.

PDP1 - 3 Study on the Discharge Characteristics of a 14:00 Diagonal Discharge AC PDP with Facing Electrodes

D.-H. Kim, J. Heo, J.-W. Ok, Y.-G. Kim, D.-H. Kim, H. J. Lee, H.-J. Lee, C.-H. Park

Pusan Nat. Univ., Korea

In order to improve electro-optical characteristics, the new facing discharge structure has been investigated. The proposed structure, which has a diagonal discharge path, make it possible to gain a low power consumption, a high luminance and a high luminous efficacy compared with those of conventional coplanar structure.

PDP1 - 4 Comparative Study on Discharge Characteristics of 14:20 FHD and Quad-FHD PDPs

Y.-S. Choi, J.-B. Lee, S.-Y. Cho, S.-B. Shim, C.-H. Park, D.-H. Kim, H. J. Lee, H.-J. Lee Pusan Nat. Univ., Korea

We have investigated the luminous efficacy of various cell resolution. The luminance and luminous efficacy decreased as the resolution increased from FHD to QFHD, because of higher plasma loss. Absolute efficacy of delta cell array QFHD PDP reaches about1.03 lm/W.

----- Break -----

15:00 - 16:20

Room 501

PDP2: Picture Quality

Chair: H. Tolner, Southeast Univ., China Co-Chair: M. Uchidoi, Panasonic, Japan

PDP2 - 1: Invited Advances in Moving Picture Quality of 15:00 Recent PDPs

I. Kawahara^{*,**}

*Panasonic Plasma Display, Japan **APDC., Japan

Image quality of PDP has been greatly improved in recent years, including native contrast and moving picture performance. Especially, moving picture resolution, through elaborate signal processing and fast phosphors developed for 3D plasma shows stunning superiority also in 2D mode over other devices. Comparison between latest models is also covered.

PDP2 - 2Skin Color Enhancement Based on Preferred Skin15:20Color in PDPs

J. Jiang, Z.-H. Liang, X.-N. Zhang, C.-L. Liu Xi'an Jiaotong Univ., China

A skin detection method and the preferred skin color region are obtained via psychological experiment. Then the skin color is enhanced according to the distance between it and preferred skin color. The experiment results show that the enhanced skin colors are more natural and agree with human vision and psychology.

PDP

PDP2 - 3Two-Stage Dither Combined with Minor Pixel15:40Separation for Gray Scale Enhancement

J.-F. Huang, Y.-G. Wang, X.-N. Zhang, Z.-H. Liang Xi'an Jiaotong Univ., China

Order dither combined with minor pixel separation (MPS) can improve the gray levels in the dark area. Random dither combined with MPS can bring back gray-level lost in the middle and high gray ranges. The experiment results show that the gray scale can be expressed smoothly without structural pattern noise.

PDP2 - 4L High Luminance Twin-path Discharge Cell with 16:00 Auxiliary Pulses for Ultra-High-Resolution PDP

Y. Hirano, K. Ishii, T. Usui, Y. Murakami NHK, Japan

We have proposed a new electrode structure that uses twin-path discharges for ultra-high-resolution PDP. When auxiliary pulses are applied to the address electrodes during the sustaining discharge period, the luminance is improved less than 60% and the luminous efficiency is also improved by 10% by using 3-D fluid simulation.

----- Break -----

17:00 - 18:00 Room 204 PDP5: Late News Session (Protective Layer)

Chair: K. C. Choi, KAIST, Korea

Co-Chair: S. Mikoshiba, APDC., Japan

PDP5 - 1L: Invited Display and Lifetime Characteristics of AC 17:00 PDPs with SrO-MgO Double Protecting Layer

K.-W. Whang, H.-W. Cheong, J.-C. Jung, T.-H. Lee, O. Kwon

Seoul Nat. Univ., Korea

We have reduced the long aging time of AC PDP with SrO-MgO double protecting layer by introducing a special process to the front dielectric layer and achieved high luminous efficacy. It is essential to study the address discharge and lifetime characteristic of AC PDP with SrO-MgO double protecting layer.

PDP5 - 2L An AC PDP with an Air-Stable CaMgO Protective 17:20 Layer

Y. Motoyama, D. Kato, M. Seki NHK, Japan

We have successfully reproduced video images on a PDP that was airsealed at 450°C and had a Ca_{0.36}Mg_{0.64}O protective layer. The sustain pulse was obtained at 135 V, which was lower than the 170 V required when the conventional MgO protective layer is used.

PDP5 - 3LInverse Relationship between Exo-Electron Currents17:40and Statistical Delay of AC PDPs

Y. Kuang, K.-H. Choi^{*}, Y.-S. Kim Hongik Univ., Korea ^{*}Southeast Univ., China

A relationship between exo-electron current and statistical relationship was examined on AC PDP test panels with or without MgO nanocrystals sprayed on MgO layer. The results indicated that the statistical delay is inversely proportional to exo-electron currents, but its proportional constant varies significantly, depending on the presence of MgO nano-crystals.

Author Interviews 18:00 - 19:00

Friday, December 3

9:00 - 12:00	Poster/A.I. Room
	Poster PDPp: Plasma Displays

PDPp - 1 Characterization of Protective Layer Materials for

PDPs by the EUPS Observation

T. Nakayama^{*}, M. Terauchi^{*,**}, K. Yoshino^{*,**}, T. Tsujita^{*,**}, M. Nishitani^{*,**}, T. Ishituka^{***}, T. Tomie^{***}, Y. Morita^{*,**}

*Panasonic, Japan **Osaka Univ., Japan ***AIST, Japan

We applied EUPS (EUV photoelectron spectroscopy) to the characterization of protective layer materials. EUPS has a higher sensitivity than XPS to detect the outermost surface conditions. We found that hydroxide and carbon absorption on CaO progressed deeper from the surface and that they are more stable than on MgO.

PDPp - 2 Electron Energy Band Structure of Sprayed Functional Layer on MgO Measued by Secondary Electron Emission Using γ-FIB System

> J. H. Choi, C. G. Son, Y. J. Hong, K. A. Lee, H. S. Uhm, E. H. Choi

Kwangwoon Univ., Korea

We have studied the electron energy band structure of MgO single crystal based on the Auger neutralization theory using by gamma-focused ion beam (γ -FIB) system. We measured secondary electron emission characteristics of MgO single crystals which have different crystal orientation. We measured the energy band structure f_e(α) function in valence band from secondary electron emission characteristics with He ion source (24.58 eV) in the three kinds of MgO single crystal with respective (100), (111), (111) orientations.

PDPp - 3 Electro-Optical Characteristics of Degraded Functional Layer in AC PDPs

K. A. Lee, C. G. Son, J. H. Choi, Y. J. Hong, E. H. Choi Kwangwoon Univ., Korea

We have studied electro-optical characteristics of different kinds of the MgO layer during the continuous discharge in AC-PDP. For observation of each degraded MgO layer characteristics, we measured the surface morphology, cathodoluminescence (CL) spectrum and the discharge characteristics after 500 hours discharge.

PDPp - 4 Adaptive Unsymmetrical Dither Region to Improve Dynamic False Contour of PDPs

Y.-G. Wang, J.-F. Huang, Z.-H. Liang, X.-N. Zhang Xi'an Jiaotong Univ., China

Dynamic false contour (DFC) can be improved with less gray scales in PDPs, the others gray scales are realized by dither. Adaptive unsymmetrical dither region is computed and changed according to the DFC. So the dither region can be kept the minimum and PSNR is better than other methods.

PDPp - 5 Study of Jitter Characteristics Depending on Wall Charge Status on an Emissive Layer

S. J. Lee, S. M. Kim, J. Kang Dankook Univ., Korea

We investigated the jitter characteristics depending on wall charge amount and polarity on different emissive layers, such as MgO and CEL MgO. The accumulation of negative wall charges on pulse-applied electrode and negative applied voltage were important to decrease the operation voltage and time delay.

PDPp - 6 Electro-Optical and Exoemission Properties of Fe-Doped MgO for AC PDPs

S. Y. Cho, J. W. Ok, C. H. Park, D. H. Kim, H. J. Lee, H. J. Lee Pusan Nat. Univ., Korea

In this paper, to improve the electro-optical characteristic in AC-PDP, we suggest the new analysis system to measurement exo-electron emission directly method and examine a relationship between the exoelectron emission (EEE) and SEE coefficient of Fe-doping MgO films or between characteristics of electro-optical properties of test panel.

PDPp - 7 Improvement of Luminous Efficiency Using New Reflective Layer in AC PDPs

T.-J. Kweon, J.-C. Ahn, E.-Y. Jung, B.-J. Kim, S.-J. Cho, H.-S. Jung, Y.-J. Park Samsung SDI, Korea

In this paper, new reflective layer between barrier rib and phosphor was adopted to increase luminance. New reflective layer has the characteristics which high reflectance and low permittivity. By using this material, the luminous efficiency was improved by about 22%.

PDPp - 8 Effect of the Cell Structure on the Luminous Efficiency of PDPs

H. K. Kwon, M. S. Lee, C. H. Moon Hoseo Univ., Korea

To investigate the possibility of increasing the luminous efficiency of the PDP, ITO electrode structure and barrier rib structure were changed. Conclusively, 4.23 Im/W of luminous efficiency was obtained in a proposed structure under 220 V with Ne-20% Xe, 400 torr gas mixture.

PDPp - 9 Effect of Deuterium on the Xe Excitation Efficiency in PDP

A. Khorami, S. Ghanbari^{*} IRIB Univ., Iran ^{*}Univ. of Essex. UK

Different gas compositions affect the efficiency of ultraviolet light. In this paper, in order to improve luminous efficiency of plasma display panels, a small quantity of Deuterium is added to Ne-Xe gas mixture. Furthermore, the performance of the SrCaO protective layer is shown to be significant in enhancing cell efficiency.

PDPp - 10 Improvement of Luminous Efficiency via Nanoparticle Phosphors in PDP

A. Khorami, S. Ghanbari^{*}, M. Mofidi^{**}

IRIB Univ., Iran *Univ. of Essex, UK **Univ. of Azad, Iran

The luminous efficiency of plasma display panels can be enhanced through the type of phosphor and nano sized phosphor. The photoluminescence characteristics of PbS nanoparticle phosphors is simulated in order to exhibit the advantages of more excitons and higher band gap, and results show a 14% improvement on cell efficiency.

PDPp - 11L Addressing Delay Time vs. Initial Number of Electrons in AC-PDP

T. Sakai, K. Tachibana^{*} Display Res. Labs., Japan ^{*}Ehime Univ., Japan

We analyzed the addressing delay T vs. initial number of electrons n_0 with a cell using Ne and MgO. A variation ΔT / T is mainly caused by γ action. If $n_0 \geq$ 16, T and ΔT is very small and a miss addressing rate \leq 10⁻¹⁰. This condition is possible by a field emission.

PDPp - 12L Negative Sustain Waveform for Reducing Temporal Image Sticking in AC Plasma Display Panel

S.-Y. Kim, C.-S. Park, H.-S. Tae Kyungpook Nat. Univ., Korea

The temporal image sticking characteristics produced by a negative sustain waveform were examined in comparison with those produced by a positive sustain waveform. It was observed that the temporal image sticking when applying the negative sustain waveform was reduced in comparison with the positive sustain waveform.

PDPp - 13L Effects of Overlap Sustain Waveform on Panel-Aging and Temporal Image Sticking Characteristics in AC Plasma Display Panel

C.-S. Park, S.-Y. Kim, H.-S. Tae Kyungpook Nat. Univ., Korea

The panel-aging and the temporal image sticking characteristics were investigated with the non-overlap and overlap sustain waveforms in the 7-in. test panel. It is concluded that the overlap sustain waveform can induce the stable discharge very quickly and reduce the problem of temporal image sticking in plasma displays.

PDPp - 14L A Study on the Optical Properties of PDP Cells Using 3D Optical Code

H. Park, J. Kang Dankook Univ., Korea

The optical properties of PDP were analyzed with 3D optical code. The reference model shows 16.6% and 10.2% higher reflectance than the test 1 and 2 models respectively. The calculated reflective properties are compared to the measured data. The relative difference is less than 4.9%.

Friday

PDPp - 15L Discharge Cell Designs for Large-Sized Transparent AC PDPs

H.-N. Choi, Y.-S. Kim Hongik Univ., Korea

A new design of transparent AC PDP for large area information displays was attempted in this study. The discharge cells with large fraction of non-discharge area was designed and its potential as the transparent display was examined. The results indicated that it can achieve optical transmittance while displaying images as well as while not-displaying images.

----- Lunch -----

13:00 - 14:40

Room 412

PDP3: High Efficiency

Chair: Y.-S. Kim, Hongik Univ., Korea Co-Chair: Y. Murakami, NHK, Japan

PDP3 - 5L: *Invited* Application of Localized Surface Plasmon 13:00 Phenomena to an AC Plasma Display Panel

K. C. Choi, S. M. Lee, W. H. Kim KAIST, Korea

Gold and silver metal nanoparticles are applied to phosphor and protective layer in an ACPDP in order to induce localized surface plasmon phenomena. The localized surface plasmon resonance induces a very strong localized electric field. It is believed that the strong localized field affects the display characteristics of the ACPDP.

PDP3 - 1: Invited PDP Research and Development in China 13:20 Q. Yan

Shichuan COC Display Devices, China

Low cost, high luminous efficiency PDP, low power consumption, high image quality are key factors to have a sustainable PDP business in China. Newly established PDP consortium in China is working closely with PDP manufacture to solve those challenges. The future direction of PDP development will be discussed.

PDP3 - 2 Withdrawn

PDP3 - 6L Improvement of Excitation Efficiency by a Localized 13:40 High Capacitance Region in Micro-Discharge Cell and Its Mechanism

M. Konishi, M. Miura, M. Murata, R. Murai, M. Kitagawa Panasonic, Japan

We performed an experimental and simulation study on the relation between the distribution of capacitance in micro discharge cell and excitation efficiency for AC PDP. Introduction of localized high capacitance region in front dielectric layer near barrier rib is found to be effective for the improvement of the excitation efficiency.

PDP3 - 3 Efficacy Improvement of PDP Discharge Using 14:00 Energy Stored in Panel Capacitance

Y. Tanaka, T. Shiga Univ. of Electro-Commun., Japan

Sustain voltage waveform using high impedance is introduced to improve the luminous efficacy of PDPs. When the discharge is ignited, the panel capacitance voltage drops during the high impedance period, resulting in low and narrow discharge current. Efficacy increases by 60% and luminance is almost identical to the conventional technique.

PDP3 - 4 Development of Degradation Resistant Red, Green 14:20 and Blue Silica Encapsulated Phosphors for PDPs

R. S. Yadav, A. F. Khan, A. Yadav, H. Chander, V. Shanker, S. Chawla Nat. Physical Lab., India

PDPs performance is greatly dependent on phosphors. Towards this goal, highly efficient phosphors $Y_4Al_2O_9$:Eu³⁺ (Red), BaMgAl₁₀O₁₇:Eu²⁺(Blue) and YBO₃:Tb³⁺ (green) have been developed. Degradation resistance, enhancement in luminescence intensity by 30-35% and uniform particle size distribution (1-2 μ m) could be achieved by encapsulating the phosphor grains by a thin silica layer.

----- Break -----

15:00 - 16:20

Room 412

PDP4: Protective Layer

Chair: Q. Yan, Shichuan COC Display Devices, China Co-Chair: H. Kajiyama, Hiroshima Univ., Japan, Korea

PDP4 - 1: *Invited* Investigation of Panel Design Parameters for 15:00 Low Power Consumption PDPs

H.-B. Park, J.-H. Kim, W.-S. Yoon, Y.-S. Seo, S.-B. Song, W.-J. Chung, E.-G. Heo, Y.-J. Park, C.-I. Chung Samsung SDI, Korea

To reduce the power consumption of PDP, a panel should be carefully designed for high luminous efficiency and low reactive power consumption. Effects of barrier rib structure, dielectric layer property, and gas mixture on efficacy and especially on reactive power are investigated.

PDP4 - 2 Discharge Characteristics of SrCaO-PDP with 15:20 MgO:α Powder Manufactured by Using All-in-Vacuum Process

T. Yano^{*,**}, K. Uchida^{*}, K. Suesada^{**}, S. Miyamoto^{**}, T. Shinoda^{**}, H. Kajiyama^{**}

^{*}ULVAC, Japan ^{**}Hiroshima Univ., Japan

The SrCaO-PDP with MgO: α powder are manufactured by using the all-in-vacuum process. By coating MgO: α powder on SrCaO protective layer surface in vacuum, it is possible to keep low discharge voltage of SrCaO protective layer and to shorten the discharge time lag within about 1 μ s.

PDP4 - 3Discharge Diagnosis of High-γ PDPs with Various Xe15:40Contents

D. Zhu^{*,**}, T. Izumi^{***}, T. Akiyama^{***}, K. Suesada^{*}, S. Miyamoto^{*}, X. Zhang^{**}, H. Kajiyama^{*}

*Hiroshima Univ., Japan **Southeast Univ., China ***APDC, Japan

The 4-in. test plasma display panels which have high γ protective layer SrCaO have been investigated by experiments. The xenon content in the discharge gas ranges from 4% to 80%, respectively. The panel parameters that have been measured include firing voltage, luminance, efficacy, infra-red emission, etc.

PDP4 - 4Analysis of Discharge Characteristics for High16:00Luminous Efficacy with High γ Protective Layer

T. Izumi, T. Akiyama, S. Uchida^{*}, M. Kitagawa APDC, Japan ^{*}Tokyo Metropolitan Univ., Japan

VUV production efficiencies were simulated by a one-dimensional fluid discharge model. By examining the electron and ion densities, it has been revealed that an increase in the electron heating efficiency originated from the high γ characteristics played a major contribution to the improvement of the VUV production efficiency.

PDP

Author Interviews 16:20 – 17:20

Sponsor:

Plasma Display Technical Meeting

IDW Outstanding Poster Paper Award

This award will go to the most outstanding paper selected from those presented at IDW '10 poster presentation. The 2010 award winners will be announced on the

I he 2010 award winners will be announced on the IDW website: http://www.idw.ne.jp/award.html

BANQUET

Wednesday, December 1, 2010 19:30 – 21:30 Crowne Grand Ball Room (2F) ANA Crowne Plaza Fukuoka See page 9 for details

EXHIBITION

12:00 – 18:00 Wednesday, Dec. 1, 2010 10:00 – 18:00 Thursday, Dec. 2, 2010 10:00 – 14:00 Friday, Dec. 3, 2010

2F Lobby, 4F Lobby Fukuoka International Congress Center

Free admission with your registration name tag

December 1

Workshop on EL Displays and Phosphors

Wednesday, December 1

15:00 -16	:40	Room 413
	PH1: Phosphors in General	
Ohaim	T. M. Chan, Nat. Chain Tunn Liniu, Taiwan	

Chair: T. -M. Chen, Nat. Chaio Tung Univ., Taiwan Co-Chair: S. Okamoto, NHK, Japan

PH1 - 1: Invited The Luminescence of Divalent Europium 15:00 (Eu²⁺) for Display Applications

A. M. Srivastava GE Global Res., USA

The Eu²⁺ luminescence finds use in several lighting and display devices. This paper explores several aspects of Eu²⁺ luminescence and point to the need of fundamental studies that are needed to resolve interpretations of the experimental data. Such investigations can lead to the development of commercially important phosphors.

PH1 - 2: Invited R&D for Reducing Tb and Eu Usage in 15:30 Phosphors for Fluorescent Lamp for Sustainable Development

T. Akai AIST, Japan

The future, there may be an imbalanced supply and demand of Tb and Eu, which are used in fluorescent lamps. An outline of an R&D project to reduce the usage of Tb and Eu is presented with a review of their demand and supply.

PH1 - 3 A Computational Chemistry Study on Relationship 16:00 between Crystal Structure and Emission Property of Eu²⁺-Doped Phosphors

- H. Onuma, I. Yamashita, R. Nagumo, R. Miura, A. Suzuki, H. Tsuboi, N. Hatakeyama, A. Endou, H. Tekaba, M. Kuba, A. Miuranata
- H. Takaba, M. Kubo, A. Miyamoto

Tohoku Univ., Japan

In this paper, we reported a computational study on emission property of Eu²⁺-doped phosphors. Multi-regression analyses were carried out and prediction equations for emission/excitation wavelength of Eu²⁺-doped phosphors were obtained. We found that Ca/Sr/Ba and Si/O/S atoms around Eu atoms make emission/excitation wavelength long and short, respectively.

Wed./Thu.

PH1 - 4 The Improvement in Photoluminescence Property of 16:20 CaYAIO₄:Eu³⁺ Phosphor by the Post-Annealing Process

M. Bartic, H. Kominami, Y. Nakanishi, K. Hara Shizuoka Univ., Japan

This paper describes the synthesis and characterization of the novel CaYAlO₄:Eu³⁺ phosphor, which emits red photoluminescence (PL) with the main emission peak located at 611.5 nm under a VUV irradiation at room temperature. The experimental data showed that the post-annealing process has improved significantly the PL property of this phosphor.

----- Break -----

Author Interviews

18:00 - 19:00

Thursday, December 2

9:00 - 10):10	Room 413
	PH2: Phosphors for LEDs	
Chair:	A. M. Srivastava, GE Global Res., USA	

Co-Chair: S. Oshio, Panasonic, Japan

PH2 - 1: Invited Synthesis and Luminescence Properties of 9:00 Lanthanide Ion-Doped Nitride Phosphors

K. Machida

Osaka Univ., Japan

Novel techniques were applied to synthesize nitride phosphors for white LED illumination. Without using alkaline earth metal nitrides, $M_2Si_5N_8$:Eu²⁺ (M=Ca, Sr, and Ba) are produced by nitriding the corresponding oxides with carbonaceous reductants. Meanwhile, direct nitriding of the component metals or hydrides such as M, Si, and/or Al are effective to produce $Ba_2Si_5N_8$:Eu²⁺ and CaAlSiN₃:Eu²⁺ as high-quality phosphors.

PH2 - 2Eu2*-Doped AIN-SiC Solid Solutions: Synthesis,9:30Cathodoluminescence and Potential Applications

R.-J. Xie, N. Hirosaki, B. Dierre, T. Takeda, T. Sekiguchi NIMS, Japan

Eu²⁺-doped AIN-SiC phosphors were prepared by firing the powder mixture at 2050°C for 2 h under 1 MPa N₂. A solid solution between AIN and SiC was formed, promoting the solution of Eu²⁺ in AIN. The phosphors showed intense blue emissions under electron beam excitation, indicative of potential phosphors for FEDs.

Thursday

PH2 - 3 A New Synthesis Route for Nitride Phosphors: 9:50 Sr₂Si₅N₀:Eu²⁺ Orange Red-Emitting Phosphors Synthesized at Relatively Low Temperature for LED Application

A. Kirakosyan, D. Y. Jeon KAIST, Korea

 ${\rm Eu}^{2*}$ activated ${\rm Sr_2Si_5N_8}$ nitridosilicate phosphors was prepared by a new synthesis method allowed to synthesize it at relatively low temperature and atmospheric pressure of nitrogen. The method has several advantages compared to commonly used processes and shows high reaction yield. The phosphor synthesized might be used in WLED application.

----- Break -----

13:20 - 16:20

Poster/A.I. Room

Poster PHp: Phosphors

$\begin{array}{lll} PHp - 1 & Structural and Luminescent Properties of Y_{6+x/3} \\ Si_{11-y}Al_yN_{20+x-y}O_{1-x+y} {\bf :} Ce^{3+} \ Phosphors \end{array}$

W. B. Park, S. P. Singh, K.-S. Sohn Sunchon Nat. Univ., Korea

A two-step high throughput screening was implemented in YN-AIN-SiN_{4/3} ternary system based on random choices. We pinpointed a host structure $Y_{6+x/3}Si_{11-y}Al_yN_{20+x-y}O_{1-x+y}$ (x= 0~3, y=0~3), the refined structure of which was the trigonal (P31c) with lattice parameters a = b = 9.81513 Å, c = 10.6305 Å, $\alpha = \beta = 90^{\circ}$, $\gamma = 120^{\circ}$.

PHp - 2 Luminescence Properties of Eu²⁺-doped β-SiAION Phosphors Synthesized by Spark Plasma Sintering

S.-W. Choi, S.-H. Hong Seoul Nat. Univ., Korea

Eu_xSi_{e-z}Al_zO_zN_{e-z} phosphors were successfully prepared by spark plasma sintering (SPS). The obtained β -SiAlON:Eu²⁺ phosphor was excited over a broad spectral range in a UV-visible region, and showed a green emission band centered at 535 nm. The Eu²⁺-doped β -SiAlON phosphor showed superior thermal stability (25°C-200°C) compared to commercial green phosphor.

PHp - 3 Luminescence Properties of Ca₂Si₅N₈:Eu²⁺ Synthesized by Spark Plasma Sintering

Y.-S. Kim, S.-W. Choi, S.-H. Hong Seoul Nat. Univ., Korea

 ${\sf Eu}^{2*}\text{-doped }{\sf Ca}_2{\sf Si}_5{\sf N}_8$ phosphors were synthesized by Spark Plasma Sintering. The emission spectra of ${\sf Ca}_2{\sf Si}_5{\sf N}_8{:}{\sf Eu}^{2*}$ exhibited a single broad band centered at 600 nm under the excitation of 460nm. The influence of the synthesis temperature and the doping concentration on the crystalline phase and luminescence properties had been characterized.

PHp - 4 Photoluminescence Behavior of MgAISiN₃:Eu²⁺ Phosphors

B. Y. Han, K.-S. Sohn Sunchon Nat. Univ., Korea

The effect of Eu^{2+} concentration in MgAlSiN₃: Eu^{2+} Phosphors is studied. MgAlSiN₃: Eu^{2+} Phosphors with low Eu^{2+} concentration emits red light and is suitable for white light emitting diodes, however, higher Eu^{2+} concentration emit deep red light around 710 nm is useful for energy down converting material for use in crystalline Silicon cells.

PHp - 5 The Effect of AI Inclusion on the Photoluminescence of $LaSi_{3}N_{5}$:Ce³⁺ Phosphors

J. W. Park, S. P. Singh, K.-S. Sohn Sunchon Nat. Univ., Korea

Blue emitting LaSi₃N₅:Ce³⁺ phosphor has been modified by Al substitution to enhance the color rendering index of white light emitting diodes (WLED) by shifting the excitation band towards desirable wavelength region. The crystal structure remains unaltered with Al substitution and orthorhombic structure in the P2₁2₁2₁ space group is maintained.

PHp - 6 Photoluminescence Properties of CaTiO₃:Bi

T. Kyomen, K. Hirozumi, M. Hanaya Gunma Univ., Japan

CaTiO₃:Bi phosphor showed yellowish white photoluminescence by irradiation of light in the wavelength range of 400-300 nm. It was suggested that the photoluminescence is occurred by not only s-p transition excitation of Bi³⁺ but also band-gap excitation of CaTiO₃ and successive energy transfer to Bi³⁺.

PHp - 7 Growth of Silicate Phosphors from the Vapor Phase

T. Ishigaki, K. Toda, T. Sakamoto, K. Umeatsu, M. Sato Niigata Univ., Japan

Well-crystalline $Ba_2SiO_4:Eu^{2+}$ powders were grown on a substrate by new vapor phase reaction between mixed powder and SiO gas. The emission intensity of the $Ba_2SiO_4:Eu^{2+}$ phosphor synthesized by new vapor phase technique is about 2.6 times higher than that of a conventional solid state reaction sample.

PHp - 8 Study on Intermediate State of YAG:Ce Prepared by Coprecipitation Method

T. Murakawa^{*}, H. Okura^{*,**}, T. Honma^{***}, Y. Miyamoto^{*}, K. Ohmi^{*} ^{*}Tottori Univ., Japan ^{**}Merck, Japan ^{***}Japan Synchrotron Radiation Res. Inst., Japan

Intermediate states of $Y_3AI_5O_{12}$:Ce prepared by liquid phase reaction has been studied. Relationships between precursors, intermediate products and completed phosphors are systematically investigated by analyzing the valence and local structure around Ce. It has been found that most of Ce is segregated as amorphous tetravalent cerium oxide by oxidized fire.

PHp - 9 Optical Properties of Sr_{1.9}Ba_{0.1}SiO₄ : Eu²⁺Thin Film Phosphors According to Thickness

J. H. Moon, K. N. Lee, Y. R. Do Kookmin Univ., Korea

This study investigates yellow emitting Eu²⁺ doped Sr_{1.9}Ba_{0.1}SiO₄ Thin Film Phosphors (TFPs). Sr_{1.9}Ba_{0.1}SiO₄:Eu²⁺ TFPs were deposited on a 2x2 cm² quartz substrate using electron beam evaporation. The brightness and luminescence efficiency of the thin films improved as the deposition temperature and thickness of the Sr_{1.9}Ba_{0.1}SiO₄:Eu²⁺ TFPs were increased.

PHp - 10 Structural and Cathodoluminescent Properties of ZnAl₂O₄ Phosphor for UV Emission

T. Iguchi, H. Kominami, Y. Nakanishi, K. Hara, A. Ohnishi^{*}, M. Kitaura^{*} Shizuoka Univ., Japan

*Yamagata Univ., Japan

 $ZnAl_2O_4$ which shows UV emission under the EB excitation has been investigated for the UV emitting devices. The luminescent properties were drastically changed by the synthesis temperature and Zn/Al ratio. From PLE and CL measurement, it is thought that the UV emission is caused from oxygen vacancy.

PHp - 11 Valence Estimation of Eu Luminescent Centers of BAM Phosphors by Conversion Electron Yield and Fluorescence Yield XAFS Measurements

T. Honma, T. Kunimoto^{*}, T. Koshiba^{**}, Y. Yamashita^{**}, K. Ohmi^{**}

Japan Synchrotron Radiation Res. Inst., Japan ^{*}Tokushima Bunri Univ., Japan ^{**}Tottori Univ., Japan

Conversion electron yield (CEY)- and X-ray fluorescence yield (XFY)-XAFS measurements have been performed for Eu luminescent centers in BAM phosphors baked in various conditions. The valence states of Eu ions near the surface and the internal bulk of BAM crystal are evaluated from Eu-L₃ edge CEY- and XFY-XANES spectra, respectively.

PHp - 12 Synthesis and Characterization of Lithium Aluminate Red Phosphor

K. Inoue, T. Sago, Y. Amano^{*}, Y. Iwamoto^{*} Mie Ind. Res. Inst., Japan ^{*}Nagoya Inst. of Tech., Japan

The sol-gel-derived lithium aluminate composition with Li:Al=1:1 yielded α -LiAlO₂ at 600°C. Then α/γ phase transformation at 800 to 1200°C, and subsequent decomposition lead to the formation of LiAl₅O₈ above 1200°C. At 1600°C, the red emission band is observed with the maximum around 685 nm.

PHp - 13 Synthesis of Ce³⁺-Tb³⁺ Co-activated Phosphate Phosphor in Air Condition

N. Sato, K. Uematsu, T. Ishigaki, K. Toda, M. Sato Niigata Univ., Japan

 β -SrP₂O₆:Ce³⁺, Tb³⁺ phosphor was synthesized by solid state reaction in air condition. Ce and Tb could be easily reduced without reduction gases. The phosphor emit strong green light under UV excitation. Therefore, β -SrP₂O₆:Ce³⁺, Tb³⁺ can be expected as a green phosphor for the CCFL backlight.

PHp - 14 Synthesis of Eu³⁺ Doped Novel Borotungstate and Borosilicate Phosphors for White LEDs

M. Inoue, S. Seki, K. Uematsu, T. Ishigaki, K. Toda, M. Sato

Niigata Univ., Japan

 $Eu_{3}BWO_{9}$ and $Gd_{3}BSi_{2}O_{10}{:}Eu^{3+}$ as novel red emission phosphors were prepared by solid-state reaction. These phosphors have the main excitation band located at 395 nm, and dominated emission peak at 588 nm and 614 nm. $Eu_{3}BWO_{9}$ and $Gd_{3}BSi_{2}O_{10}{:}Eu^{3+}$ were suitable for the tri-color phosphors based white LED.

PHp - 15 Effect of Organic Dye in Inorganic-Organic Hybrid Electroluminescence Devices

Y. Noguchi, Y. Hoshino, T. Tamura, T. Uchida, T. Satoh Tokyo Polytechnic Univ., Japan

By using organic dyes to dope the phosphor layers of powder EL devices, high luminosity and uniform luminescence can be realized. In hybrid EL device, the excitation energy of the phosphor is transferred to the organic dyes. The introduction of the organic dye results in increased luminosity and uniform brightness.

PHp - 16 Current-Voltage Characteristics of Top-Emission Printed EL Devices Using Solution-Processed ZnO Nanocrystals

H. Kawasaki, K. Itatani, T. Toyama, H. Okamoto Osaka Univ., Japan

Current–voltage (J–V) measurements were performed on the topemission EL devices with a printed emission layer involving solutionprocessed ZnO nanocrystals. The temperature dependence of J–V characteristics suggested the deposition method and the deposition conditions of top anodes play a crucial role in determining UV emission intensity.

PHp - 17 Inorganic Electoluminescent Devices with Carbon Nano Tube

K.-M. Yu^{*}, H.-S. Song^{*}, H.-K. Yi^{*}, H.-S. Choi^{*}, H.-R. Oh^{*}, H.-J. Moon^{**}, D.-S. Moon^{***}, B. S. Bae^{***}

^{*}Univ. of New IT Eng., Korea ^{**}Univ. of Semiconductor, Korea ^{***}CCO Display Tech., Korea

The EL devices were investigated with CNT. We investigated EL with a phosphor paste mixed with CNT by impeller and ball mill. The luminance of EL devices depends on how to mix the CNT. We investigated EL devices according to amount of CNT, and the position of the CNT layer.

PHp - 18 Preparation of Rare-Earth Doped SrGa₂S₄ Thin Film Phosphors by Two Electron Beams Evaporation and 355 nm Laser-Annealing

- T. Yamasaki, T. Seino^{*}, H. Kominami, Y. Nakanishi,
- Y. Hatanaka^{**}, K. Hara

Shizuoka Univ., Japan ^{*}Japan Steel Works, Japan ^{**}Aichi Univ. of Tech., Japan

The crystallization mechanism of SrGa₂S₄:Eu²⁺ thin-film phosphors by 355nm laser-annealing was examined. From simulation of thermal distribution by laser irradiation on SrS and Ga₂S₃ films, the laser energy was mainly absorbed by Ga₂S₃ and heated. It was expected that laser energy absorption in Ga₂S₃ contributed to formation of SrGa₂S₄ greatly.

PHp - 19 Thin-Film Electroluminescent Devices Fabricated Using La₂O₃-Based Multi-Component Oxide Phosphors

J. Ishino, Y. Nishi, T. Miyata, T. Minami Kanazawa Inst. of Tech., Japan

Multicolor PL and EL emissions were observed from newly developed La_2O_3 -based oxide phosphors using $BaLa_2O_4$, $CaLa_2O_4$ or $SrLa_2O_4$ as the host material. The use of Bi-activated oxide phosphors co-doped with Eu made it possible to control the EL and PL emission color over a wide range.

PHp - 20 EL and PL Characteristics in Various Bi-Activated Vanadate-Based Phosphor Thin Films

J. Ishino, T. Miyata, T. Minami Kanazawa Inst. of Tech., Japan

Multicolor PL and EL emissions were obtained in Bi-activated YVO_4 and $GdVO_4$ as well as YVO_4 :Bi,Eu, $GdVO_4$:Bi,Eu and $LaVO_4$:Bi,Eu phosphor thin films. Color changes from green to red in PL and EL emissions were obtained. A maximum luminance of 24 cd/m² was obtained in a red-emitting $GdVO_4$:Bi, Eu TFEL device.

PHp - 21 Influence of Organic Solvent on Optical Degradation Characteristics of Sol-Gel Glass Coated Eu-Complex

T. Fukuda, S. Akiyama , S. Kato , Z. Honda , N. Kamata, N. Kijima*

Saitama Univ., Japan *Mitsubishi Chem. Group, Sci. Tech. Res. Ctr., Japan

We investigated the influence of organic solvent on the optical degradation of Eu-complex encapsulated by sol-gel derived glass networks. The most important finding is that the dielectric constant of the organic solvent affects the optical degradation characteristics of the encapsulated sample and PL quantum efficiency of the sol-gel starting solution.

PHp - 22 Improved Stability of Glass-Coated Eu-Complex Using Solvothermal Synthesis

S. Kato, S. Akiyama, T. Fukuda, Z. Honda, N. Kamata, N. Kijima^{*}

Saitama Univ., Japan ^{*}Mitsubishi Chem. Group, Sci. Tech. Res. Ctr., Japan

We achieved an improved optical degradation characteristic of Eucomplex encapsulated by the silica glass network via a solvothermal synthesis. By optimizing the concentration of the organic solvent, a maximum half brightness time of more than 360 min was achieved, and it was 5.4-times longer than that of the reference sample.

PHp - 23 Fabrication of a Transparent Thin Film Using Y₃Al₅O₁₂:Ce³⁺ Nanophosphor with a Poly (methyl methacrylate) Matrix

B. K. Park, J. H. Oh, Y. R. Do Kookmin Univ., Korea

 $Y_3AI_5O_{12}:Ce^{3+}$ (YAG:Ce³⁺) nanophosphor was synthesized by a glycothermal method, where a reaction between aluminum isopropoxide and acetates of yttrium and cerium(III) was induced in 1,4-butylene glycol in an autoclave. A PMMA matrix transparent thin film dispersed YAG:Ce³⁺ nanophosphor was fabricated on glass substrates by a spincoating method.

PHp - 24 Enhanced Photoluminescence of Transparent Polymer Films Dispersed Fluorescent Dye with Light-Recycling Filters

H. K. Park, J. R. Oh, Y. R. Do Kookmin Univ., Korea

We exploit the effects of light-recycling filters (LRFs) to enhance the photoluminescence of transparent polymer films incorporating dispersed fluorescent dye. Fluorescent dye (Lumogen yellow) was dispersed in a transparent polymer consisting of polymethyl methacrylate (PMMA) and toluene. Transparent films were spin-coated on glass substrates with and without LRFs, respectively.

PHp - 25 Preparation of Perovskite-Type Alkaline-Earth Stannates Thin Films Using a Unilamellar Nanosheets Seed Layer

H. Takashima, K. Ueda^{*}, K. Ikegami

AIST, Japan ^{*}KIT, Japan

We have obtained green photoluminescence in rare-earth-doped perovskite-type alkaline-earth stannate thin films. On a glass substrate with a seed layer prepared by the Langmuir-Blodgett method, uniaxially oriented thin films of [$(Ca_{0.97}Mg_{0.03})_{0.98}Tb_{0.02}]SnO_3$ with sharp and intense emission and transmittance > 75% have been successfully obtained.

PHp - 26 A Novel Synthesis of Spherical Silica Phosphors

W. Pan, N. Wang, Y. Wu, G. Li, J. Li, G. Ning, Z. Mu^{*}, Y. Lin^{*}

Dalian Univ. of Tech., China *Liaoning Zhongda Superconducting Material, China

The novelty of the current work lies in the simple synthesis of a class of silica phosphors produced upon calcination of hybrid-functionalized silica spheres which to the best of our knowledge are the first known the role of en on the morphology and luminescence properties of the resultant silica spheres.

PHp - 27 High Throughput Synthesis "Melt-Synthesis Technique" for Photoluminescence Materials Using by Arc Imaging Furnace

T. Ishigaki, K. Uematsu, K. Toda, M. Sato, M. Yoshimura^{*} Niigata Univ., Japan ^{*}Tokyo Inst. of Tech., Japan

To synthesize photoluminescence materials, we applied a novel "meltsynthesis technique". Rapid synthesis methods to develop those double oxides have been strongly anticipated. During melt synthesis, the mixture of oxides or their precursors is melted rapidly (1–60 s) in an arc-imaging furnace using strong light radiation.

PHp - 28L Computational Screening of Host Crystal for Phosphors: Correlation of Eu²⁺ Emission Wavelength with Stoichiometry

H. Onuma, D. Yoshihara, I. Yamashita, R. Nagumo, R. Miura, A. Suzuki, H. Tsuboi, N. Hatakeyama, A. Endou, H. Takaba, M. Kubo, A. Miyamoto

Tohoku Univ., Japan

We reported a decision tree analysis to explore a host material of Eu^{2+} doped phosphors focusing on their emission wavelength. The emission wavelengths of investigated phosphors correlated well with a simple function of their stoichiometry. Our proposed rule would be useful for a first screening of host materials for Eu^{2+} -doped phosphors.

PHp - 29L Crystallographic and Luminescent Characteristics of CuAlS₂:Mn Phosphor Thin Films Prepared by Multi Source Deposition Using Al₂S₃:Mn and Cu Evaporation Sources

T. Koshiba, Y. Miyamoto, K. Ohmi Tottori Univ., Japan

CuAlS₂:Mn phosphor thin films have been prepared by multisource deposition method using Al₂S₃:Mn and Cu as electron-beam evaporation sources. The prepared films are crystallized as CuAlS₂ by annealing at 650°C, and are singly oriented to the <112> axis. The films show an efficient reddish-orange photoluminescence under UV light irradiation.

PHp - 30L Eu, Mn Coactivated Calcium Silicate Phosphors for Near-UV Excitation Synthesized by Microreaction Method

H. Okura^{*,**}, T. Murakawa^{**}, Y. Miyamoto^{**}, K. Ohmi^{**} ^{*}Merck, Japan ^{**}Tottori Univ., Japan

Novel orange phosphors $(Ca_{1,x,y},Eu_x,Mn_y)SiO_3(SiO_2)_n$ have been developed by combinatorial synthesis, which is an effective method for searching for new phosphors. Synthesized phosphors have acicular particles and show an orange luminescence with a peak wavelength at 600 nm under near-UV excitation. The phosphors are suitable for high-color rendering white LEDs.

$\label{eq:PHp-31L} \begin{array}{c} \mbox{Surface Modification of the LED phosphor by} \\ \mbox{Al}_2O_3\mbox{-coating and NaOH Treatment} \end{array}$

J. H. Seo, S. H. Sohn Kyungpook Nat. Univ., Korea

The surface of Eu doped silicate phosphor was coated with Al_2O_3 nanoparticles in a simple surface treatment way, a kind of the modified sol-gel method. Surface modification was caused by NaOH-treatment. It was found that the surface coating and the NaOH-treatment do not affect to the luminance intensity of the phosphors.

PHp - 32L The Nitridation of Europium Doped Strontium Silicate Phosphors

S. J. Lee, J. S. Lee, W. H. Jung^{*}, K. Lee, Y. J. Kim Kyonggi Univ., Korea ^{*}Cerakor, Korea

 Eu^{2*} doped Sr_2SiO_4 powders were nitrided and then the structural and optical properties were investigated. The nitridation was performed by firing the mixture of $SrCO_3\text{-}Si_3N_4\text{-}Eu_2O_3$ under N_2 atmosphere. The emission wavelength ranged from green to red under 466 nm excitation, depending on the firing parameters.

PHp - 33L Broad Band-SrSi₂O₂N₂: Eu²⁺ Phosphor for Solid-State Lighting and Photovoltaic Cell

Y.-C. Fang*, S.-Y. Chu*,**

Nat. Cheng Kung Univ., Taiwan

 $SrSi_2O_2N_2;\ Eu^{2*}$ green phosphors are prepared using a solid-state reaction. The luminescence properties are investigated using PLE/PL spectra, and this concentration quenching mechanism may be exchange interaction. Results show that $SrSi_2O_2N_2;\ Eu^{2*}$ phosphors with a broad excitation band have potential for use in solid-state lighting and solar cells.

----- Break -----

16:40 - 17:50

Room 502

PH3: Emissive Displays and Phosphors

Chair:	D. Jeon, KAIST, Korea
Co-Chair:	K. Wani, Tazmo, Japan

PH3 - 1: *Invited* Challenges to Full-Color Quantum Dot 16:40 Display

B. L. Choi, T.-H. Kim, K.-S. Cho, E. K. Lee, S. J. Lee, J. Chae^{*}, J. W. Kim, D. H. Kim, S. Y. Lee, Y. Kuk^{*}, J. M. Kim Samsung Elect., Korea *Seoul Nat. Univ., Korea

Colloidal quantum-dot (QD) display has recently received considerable attention due to their many strengths of QD property. In this talk, the status of QD-EL and the embodiment of full-color QD display with a noble, scalable approach for fine patterning of QD will be presented.

PH3 - 2 Optical Simulation of Light Conversion Process in 17:10 Emissive LCDs Consisting of Phosphor Layers and Near-UV LEDs

T. Yata^{*,**}, Y. Miyamoto^{*}, K. Ohmi^{*} ^{*}Tottori Univ., Japan ^{**}Sony Mobile Display, Japan

A light conversion process in emissive LCDs consisting of phosphor layers and near-UV light has been simulated using a Monte Calro ray tracing method. It enables to optimize parameters of phosphor layer by only using measured luminescent and optical characteristics of phosphors and optical filters.

PH3 - 3 Effect of Annealing on the Structural and 17:30 Photoluminescence Properties of ZnO/Zn_{0.9}Mg_{0.1}O Heterostructures Heterostructures

C. Li, D. Wang, T. Kawaharamura, T. Matsuda, T. Hiramatsu, H. Furuta, M. Furuta, T. Hirao Kochi Univ. of Tech., Japan

 $ZnO/Zn_{0.9}Mg_{0.1}O$ thin films were prepared by radio frequency magnetron sputtering. Thermal-annealing was carried out in different ambient gases at a low temperature of 430°C. Bamboo-like nano-rods were only formed after annealing in a reducing gas, accompanying with an enhancement in both visible and UV region emissions.

Author Interviews 18:00 - 19:00

Supporting Organizations:

The 125th Research Committee on Mutual Conversion between Light and Electricity, Japan Society for Promotion of Science Phosphor Research Society, The Electrochemical Society of Japan

IDW '11

The 18th International Display Workshops

December 7-9, 2011

Nagoya Congress Center Nagoya, Japan

http://www.idw.ne.jp

IDW Best Paper Award

This award will go to the most outstanding paper selected from those presented at IDW '10. The 2010 award winners will be announced on the IDW website: http://www.idw.ne.jp/award.html

PH

IDW Outstanding Poster Paper Award

This award will go to the most outstanding paper selected from those presented at IDW '10 poster presentation.

The 2010 award winners will be announced on the IDW website: http://www.idw.ne.jp/award.html
Workshop on Field Emission Display and CRT

Friday, December 3

9:00 - 9:10

Room 402

Opening

Opening Remarks 9:00

M. Takai, Osaka Univ., Japan

9:10 - 10:0	0 Room 402	2
FED1: FEDs & BLUs		
Chair: Co-Chair:	H. Mimura, Shizuoka Univ., Japan H. Shimawaki, Hachinohe Inst. of Tech., Japan	
FED1 - 1: 9:10	Invited Development of Carbon Nanotube Backlight for LC Television; Reliability of Printed Carbon Nanotube Field Emitters	
	Y. C. Kim, I. H. Kim, J. N. Hur, J. W. Bae, S. H. Park, H. J. Kim, I. T. Han, J. M. Kim, Y. H. Kim	
	Samsung Advanced Inst. of Tech., Korea	
LCD TV lit b	y CNT BLU has been developed. We present developme	nt

LCD TV lit by CNT BLU has been developed. We present development and optimization on the CNT paste for the application in BLU. Emission current density ~ 1 mA/cm² under DC bias was stably obtained through the CNT paste with high concentration of CNTs up to 10 wt%.

FED1 - 2 High Speed Lightening of CNT Field Emission 9:40 Backlight for LCD by Enhanced Turn-off Current Driving Method

J.-W. Jeong^{*}, J.-W. Kim^{*,**}, J.-T. Kang^{*,***}, Y.-H. Song^{*,**} ^{*}Elect. & Telecommun. Res. Inst., Korea ^{**}Univ. of Sci. & Tech., Korea ^{***}Kyungpook Nat. Univ., Korea

The advanced current driving method was adopted for a high speed operation of CNT field emission backlight. The enhanced turn-off method shortens the response time of field emission switching in the FE-BLU, under 1ms, which is applicable to an impulsive or a colorsequential BLU for premium LCD.

FED1 - 3 Withdrawn

----- Break -----

10:40 - 12:10

Room 402

FED2: Field Emitters (1)

Chair:	Y. Gotoh , Kyoto Univ., Japan
Co-Chair:	F. Wakaya, Osaka Univ., Japan

FED2 - 1: Invited Field Emission Characteristics of Carbon 10:40 Nanotube Emitters Fabricated by a Filtration-Transfer Method

> D. H. Shin, Y. Song, Y. Sun, J. Y. Lee, J. H. Shin, C. J. Lee Korea Univ., Korea

We demonstrated CNT field emitters made by a filtration-transfer method. They showed low turn-on and threshold electric fields and very stable emission stability for long operation time at the acceleration condition. The new fabrication method can promise high-performance CNT emitters with organic binder free at room temperature.

FED2 - 2 Robust Carbon Nanotube Cathode with Various CNT 11:10 Diameters and Post Treatments

M. Takai, T. Takikawa, H. Oki, K. Murakami, S. Abo, F. Wakaya

Osaka Univ., Japan

Carbon nanotube (CNT) cathodes with high emission current and long lifetime have been realized using various surface treatments and pulsed aging, resulting in the field emission lifetimes exceeded 100 hours in dc operation, corresponding to 100,000 hours at a duty ratio of 1/1000.

FED2 - 3 Performance of Hafnium Nitride Field Emitter Array 11:30 in Tough Circumstance

W. Ohue, K. Ikeda, K. Endo, Y. Gotoh, H. Tsuji Kyoto Univ., Japan

Gated Hafnium Nitride field emitter arrays (HfN-FEAs) which posses approximately 10,000 emission tips were fabricated, and their performance was evaluated both at room temperature and at 200°C. HfN-FEAs could be operated even at 200°C.

FED2 - 4 Enhanced Electron Emission from nc-Si MOS 11:50 Cathode by Laser Irradiation

H. Shimawaki, Y. Neo^{*}, H. Mimura^{*}, F. Wakaya^{**}, M. Takai^{**}

Hachinohe Inst. of Tech., Japan ^{*}Shizuoka Univ., Japan ^{**}Osaka Univ., Japan

Enhancement of electron emission by laser irradiation of a metaloxide-semiconductor (MOS)-type cathode based on nanocrystalline silicon has been studied. The emission current was enhanced under irradiation and quickly responded to on-off of the laser. In addition, the threshold voltage for the electron emission became lower than that without irradiation.

----- Lunch -----

13:20 - 14:40

Room 402

FED3: Field Emitters (2)

Chair: M. Takai, Osaka Univ., Japan Co-Chair: Y. Neo, Shizuoka Univ., Japan

FED3 - 1 FEA Technologies for Display and Imaging Sensor 13:20 Application

> M. Nagao, T. Yoshida, T. Shimizu, S. Kanemaru, Y. Neo^{*}, H. Mimura^{*}

AIST, Japan *Shizuoka Univ., Japan

Several FEA technologies for display and imaging device application that we have developed will be overviewed. A vertical-thin-film FEA for material saving fabrication, an integration of FEAs on TFT substrate for precise emission control, a volcano-structured multi-gate FEA for beam focusing, and HfC coating for lifetime improvement will be presented.

FED3 - 2 Observation of Field Emission Current Fluctuation 13:40 with In Situ Analyzer of Field Emission Devices

Y. Gotoh, M. Kawasaki, H. Tsuji Kyoto Univ., Japan

Current fluctuation of field emission current was observed with in situ analyzer of field emitters. Current-voltage characteristics obtained by superimposing ac voltage, we obtained Seppen-Katamuki plots of the emitter. Detailed analysis revealed that the change in emission current could be detected by the present method.

FED3 - 3 Enhancement of Electron Field Emission from 14:00 Titanium-Oxide Nanostructure by Ultraviolet Light Irradiation

F. Wakaya, T. Tatsumi, K. Murakami, S. Abo, T. Takimoto^{*}, Y. Takaoka^{*}, M. Takai

Osaka Univ., Japan ^{*}Ishihara Sangyo Kaisha, Japan

Effect of ultraviolet light irradiation on electron field emission from titanium-oxide nanostructure is investigated. The field-emission current was increased by the irradiation. The enhancement in the field-emission current by UV light with a wavelength λ = 365 nm is larger than that with λ = 405 nm.

FED3 - 4 A New Method for Improving the Surface 14:20 Conduction Electron Emission

X. Siliang, L. Lu, Z. Lingguo, W. Shengli Xi'an Jiaotong Univ., China

Surface-conduction electron emitters (SCEs) are normally fabricated from PdO conductive film. In this paper, we propose a method to increase the emission current of SCE. The experiment result shows the emission current can be increased from 5.32 μ A to 7.58 μ A by changing the voltage polarity exerted to the nano-scale gaps.

----- Break -----

15:00 - 15:	40 Room 402	
FED4: Field Emitters (3)		
Chair: Co-Chair:	M. Sasaki, Univ. of Tsukuba, Japan M. Nagao, AIST, Japan	
FED4 - 1 15:00	The Characteristics of Suppressor to Control an Emission Angle for Micro-Column Built in Field Emitter	
	Y. Neo, A. Koike, Y. Takagi, T. Fujino, M. Nagao [*] , T. Yoshida [*] , H. Murata ^{**} , K. Sakai ^{**} , T. Aoki, H. Mimura	
	Shizuoka Univ., Japan [*] Nat. Inst. of Advanced Ind. S&T, Japan ^{**} Meijo Univ., Japan	
The Micro-c	olumn was proposed as electron beam application, suc	

The Micro-column was proposed as electron beam application, such as microscope and lithography. According with the basic principle of reduction law, the structure was redesigned and the beam spot diameters were estimated correctly. In this time, the new functioned electrode, named suppressor, was introduced to the initial emission angle.

FED

FED4 - 2 Work Function Measurement of Y-Oxide/W(100) 15:20 Surface by Using of Photoemission Electron Microscope

T. Kitaguchi, K. Furuta, H. Nakane Muroran Inst. of Tech., Japan

A cathode material of a low work function is needed to achieve a high performance electron source. We measured the work function of W(100) surface modified with Y_2O_3 by using of photoemission electron microscope. The work function of Y-oxide/W(100) surface is measured to be 2.7 eV.

Author Interviews

16:20 - 17:20

Sponsor:

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Asia Display 2011

Kunshan, China

SID 2011

International Symposium, Seminar and Exhibition

May 15-20, 2011

Los Angeles, California, U.S.A.

Workshop on Organic LED Displays

Wednesday, December 1

13:20 - 14:50

Main Hall

OLED1: OLED Keynote & Materials

Chair: Y. Kijima, Sony, Japan Co-Chair: T. Inoue, TDK, Japan

OLED1 - 1: *Invited* Challenges Towards the Next-Generation 13:20 OLED Materials and Devices

T. Tsutsui

Kyushu Univ., Japan

Progresses in materials and devices in OLEDs in these twenty years have been summarized, and present attainments of research and development in OLEDs are discussed. Then issues needed for further studies for the progress in science and technology on OLEDs are discussed.

OLED1 - 2: *Invited* Highly Efficient Fluorescent Blue OLED 13:55 Based on New Electron Transport Materials with High Electron Mobility

S. Kusano, M. Nagaoka, E. Takahashi, S. Fukuchi, T. Fukuchi, N. Yokoyama Hodogaya Chem., Japan

A series of new electron transporters showing high electron mobility and high Tg has been developed. I-V-L characteristics of blue OLED were measured in temperature range of 28-80°C. Material with higher mobility showed minor temperature dependence of driving voltage, and evident temperature dependence of current efficiency is discussed.

OLED1 - 3 Optimization of Carrier Balance in Phosphorescent 14:20 Polymers for Highly Efficient OLED Devices

G. Motomura, M. Suzuki, T. Shimizu, S. Tokito^{*} NHK, Japan ^{*}Yamagata Univ., Japan

We have evaluated the carrier transport properties in phosphorescent polymers having carrier transport and phosphorescent units. The mobility observed by Time-of-Flight measurements depended on the concentration ratio of carrier transport units. An external quantum efficiency of 14.5% in OLEDs using phosphorescent polymers was achieved by optimizing the carrier balance.

OLED1 - 4 Study of Carrier Injection in PDOF/Ca Interface by 14:35 Using Carrier Transfer Simulation Method

I. Yamashita, H. Onuma, R. Nagumo, R. Miura, A. Suzuki, H. Tsuboi, N. Hatakeyama, A. Endou, H. Takaba, M. Kubo, A. Miyamoto Tohoku Univ., Japan

We analyzed the carrier injections in PDOF/Ca interfaces by using carrier transfer simulation method based on a quantum chemistry calculation and Monte Carlo methods. We investigated the relationship between the interface structures and carrier injection properties.

----- Break -----

15:00 - 16:10

Main Hall

OLED2: OLED Soluble Technologies

Chair: K. Nakayama, Yamagata Univ., Japan Co-Chair: T. Wakimoto, Merck, Japan

OLED2 - 1: *Invited* Soluble Hole Injection Materials Applicable 15:00 to Hybrid and Printed OLED Devices

K. Monzen, N. Nakaie, T. Yamada

Nissan Chem. Inds., Japan

We are developing the inks for wet coating, named *ELsource* that can be used as hole injection layer in OLED devices. The luminance of hybrid OLED device using the latest ink has increased two times more than that using conventional ink.

OLED2 - 2 A High-Performance Hybrid OLED Device Assisted 15:25 by Evaporated Common Organic Layers

T. Higo, T. Matsumoto, T. Imai, T. Yoshinaga, Y. Obana, T. Hirano, T. Sasaoka, T. Urabe Sony, Japan

We propose a novel OLED structure named "Super Hybrid OLED", which is consisted of polymer and small molecule layers. The Super Hybrid OLED has excellent performance in the blue device (0.14, 0.09) of current efficiency of 6.1 cd/A. Both red and green Super Hybrid devices showed equivalent performances to all-polymer devices.

OLED2 - 3 A Novel Solution Processable Hole-Transport 15:40 Polymer and Its Applications on Organic Electroluminescent Devices

J.-H. Li, A. Raju, P. Almar, T. Hirai, M. Bown, K. Ueno Commonwealth Scientific & Ind. Res. Org., Australia

A new solution processable hole-transport material (HTL) and the according devices of fluorescence and phosphorescence are demonstrated in this presentation. Results showed that the device performances based on this HTL are comparable with the ones with traditional HTL, NPD.

OLED2 - 4 Highly Efficient Solution-Processed 15:55 Phosphorescent Organic Light Emitting Diode Using Polymer Host

T. Sawabe, I. Takasu, Y. Mizuno, T. Sugizaki, A. Wada, T. Ono, J. Yoshida, S. Enomoto, A. Hirao, I. Amemiya, C. Adachi^{*}

Toshiba, Japan ^{*}Kyushu Univ., Japan

We report a highly efficient solution-processed blue phosphorescent organic light-emitting diode (OLED) with maximum external quantum efficiency (EQE) of 20.9% and the maximum power efficiency of 40 lm/W. Our results show that solution-processed OLEDs can achieve high efficiency close to the theoretical limit.

----- Break -----

16:40 - 18:05

Main Hall

OLED3: OLED Display Applications

Chair:	S. Aratani, Hitachi, Japan
Co-Chair:	A. Mikami, Kanazawa Inst. of Tech., Japan

OLED3 - 1: *Invited* 15-in. RGBW Panel Using Two-Stacked White 16:40 OLED and Color Filter for TV Applications

C.-W. Han, S.-H. Pieh, H.-S. Pang, J.-M. Lee, H.-S. Choi, S.-J. Bae, H.-W. Kim, W.-S. Ha, Y.-H. Tak, B.-C. Ahn LG Display, Korea

We fabricated 15-in. HD panel employing the two-stacked WOLEDs and color filter, of which color gamut is up to 101.2% (CIE1976). The WOLEDs exhibit a current efficiency of 61.3 cd/A and a power efficiency of 30 lm/W at 1000 nit and their CIE coordinate is (0.340, 0.334).

OLED3 - 2 High Efficient Top Emitting OLED Micro Display for 17:05 Personal Display Application

C. Y. Park, S. Lee, C.-H. Hyun, S. K. Kang, B.-C. Kwak^{*}, H.-S. Lim^{*}, O.-K. Kwon^{*}, H. K. Chung

Samsung Mobile Display, Korea ^{*}Hanyang Univ., Korea

A 0.4-in. VGA OLED Micro Display composed of Si wafer backplane and white OLED was demonstrated. A high current efficiency of 18.4 cd/A (conversion white efficiency 4 cd/A) for single optical path length top emitting white OLED was achieved. A HMD using OLED Micro Display was demonstrated for personal display application.

OLED3 - 3 Design of the LTPS Process Compatible High 17:20 Performance Distributed Bragg Reflector (DBR) Using High k Dielectrics

D. Kwon, J. Yoon, C. Im, I. Lee, J. Lee, S. Kim Samsung Mobile Display, Korea

The high performance DBR consisted of multi SiO_2 /high k dielectric layers was developed. For low temperature poly-Si (LTPS) process compatibility, we designed it as a gate dielectric also. We achieved color gamut over 100% and improved light efficiency over 80% without degradation of thin film transistor (TFT) property.

OLED3 - 4 Rapid Thermal Annealing (RTA) Skipped Bottom 17:35 Emission 5 Mask AMOLED Displays with a Low k Organic Interlayer

I. Lee, C. Im, D. Kwon, J. Yeo, J. Yoon, J. Kim, Y. Kim, J. Lee, S. Kim

Samsung Mobile Display, Korea

The world first LTPS 5 mask AMOLED panel was designed by placing the gate and the pixel on the same plane. With RTA process skipped, we achieved mobility of 81 cm²/Vs for the TFT with an organic interlayer. Finally, LTPS 5 mask 12.1-in. WXGA AMOLED panel was fabricated without RTA process.

OLED3 - 5L OLED-on-CMOS Based Single Chip Microdisplay 17:50 and Image Sensor Device

R. Herold, U. Vogel, B. Richter COMEDD, Fraunhofer Inst. for Photonic MicroSyss., Germany

After first reports of the principle of a single chip mircodisplay and camera device, this paper presents the first characterization results of a chip with active matrix camera. Operation will be explained by block-schematic. A second part shows the characterization results of the camera and the display.

Author Interviews

18:00 - 19:00

9:00 - 10:1	5 Room 204	
FLX4/OLED4: Flexible OLED		
Chair: Co-Chair:	T. Kamata, AIST, Japan S. Naka, Univ. of Toyama, Japan	
FLX4/ OLED4 - 1	Solution-Processed Organic Films of Multiple Small- Molecules and White Light-Emitting Diodes	
9:00	W. Dongdong, W. Zhaoxin, Z. Xinwen, J. Bo, L. Shixiong, W. Dawei [*] , H. Xun	
	Xi'an Jiaotong Univ., China	

*Univ. of Arkansas, USA

We found that the spin-coated films of NPB, and blends of NPB and DPVBi, though having lower densities, were more uniform than their vacuum-deposited counterparts. Using the spin-coated films of NPB:DPVBi as mixed host, doped with blue and yellow dyes, new white organic light-emitting devices (WOLEDs) were demonstrated.

FLX4/ Flexible OLED Encapsulation by Glass Base OLED4 - 2 Technology 9:20 G. Chen, S.-T. Yeh, P.-I Shih, J.-L. Wu, K.-Y. Cheng, L.-Y. Jiang, Y.-Y. Chang ITRI, Taiwan

A flexible OLED encapsulation process was successfully developed with glass base OLED mass production equipment. These flexible encapsulation OLED devices have good flexibility and environment reliability. We expected this approach will be the important way to manufacture the flexible OLED devices using currently most OLED equipment facility.

FLX4/Graphene Sheet Synthesized with MicrowaveOLED4 - 3Eradiation and Interlinked by Carbon Nanotubes for9:40High-Performance Transparent Flexible Electrodes

G. Xin, W. Hwang, N. Kim, H. Chae Sungkyunkwan Univ., Korea

High quality graphene was obtained though microwave irradiating expansion following a solution process. By combining Carbon Nanotubes (CNTs) as bridges between graphene flakes, allowed the fabrication of high performance conductive films with conductivities and optical properties: $181 \ \Omega sq^{-1}$ at 82.2% transmittance after chemical treatment and doping.

FLX4/ Fabrication of QVGA Flexible Phosphorescent OLED4 - 4L AM-OLED Display using Ink-jet Printing 10:00 M. Suzuki, H. Fukagawa, G. Motomura, Y. Nakajima, M. Nakata, H. Sato, T. Shimizu, Y. Fujisaki, T. Takei, S. Tokito*, T. Yamamoto, H. Fujikake NHK, Japan *Yamagata Univ., Japan

We demonstrated a 5-in. QVGA flexible phosphorescent AM-OLED display driven by OTFTs on a plastic substrate. Cross-linked olefin polymer was used as the gate insulator. Phosphorescent polymer materials were used for emitting layer of OLEDs, which were patterned by ink-jet printing. Color moving images were achieved by the display panel.

----- Break -----

10:40 - 11:50	Room 501
OLED5: OLED Device Technologies	

Chair: K. Monzen, Nissan Chem. Inds., Japan Co-Chair: H. Kuma, Idemitsu Kosan, Japan

OLED5 - 1: *Invited* Surface-Light-Emitting Transistors Based on 10:40 Vertical-Type Metal-Base Organic Transistors

> K. Nakayama, Y.-J. Pu, J. Kido Yamagata Univ., Japan

The metal-base organic transistor (MBOT) is a promising verticaltype organic transistor composed of simple layered structure and it can drive large current with low voltage. MBOT also can be applied for surface-light-emitting transistors by combining with OLED materials that realize both functions of OLED and OTFT.

OLED5 - 2 Performance Improvement of White Phosphorescent 11:05 Organic Light-Emitting Diodes by Using Composite Host Structure to Enhance the Carrier Injection

F.-S. Juang, L.-A. Hong, C.-Y. Chen, S.-H. Wang, Y.-S. Tsai, Y. Chi^{*}, H.-P. Shieh^{**}

Nat. Formosa Univ., Taiwan ^{*}Nat. Tsing Hua Univ., Taiwan ^{**}Nat. Chiao-Tung Univ., Taiwan

Device characteristics of phosphorescent OLEDs with composite host structure were investigated by co-doping hole and electron transport-type hosts in emitting layer. The improved of charge carrier injection and confined of exciton within recombination zone were achieved. White OLED shows the efficiencies of 34.5 cd/A and 24 lm/W at 1000 cd/m².

OLED5 - 3 Withdrawn

OLED5 - 5LHigh-Efficient White Organic Light-Emitting Diodes11:20with a Three-stack Multi-Photon Emission Structure

Shingo Ishihara Hitachi, Japan

We have investigated 3-stack MPE WOLEDs with all phosphorescent emitters. The current efficiency and the power efficiencies obtained were 129 cd/A and 27 lm/W at 0.1 mA/cm², respectively.

OLED5 - 4 Low Temperature Color Filter on Thin Film 11:35 Encapsulation AMOLED for Flexible Top Emission

S. Kim, H. S. Shim, H.-J. Kwon, Y. T. Chun, I. Kee, S. Y. Lee, S. Lee^{*}, J. H. Kwack^{*}, D. Han^{*}, M. S. Song^{*}, S. Kim^{*}

Samsung Elect., Korea *Samsung Mobile Display, Korea

We developed low temperature color filter on thin film encapsulation AMOLED panel for flexible display, which are performed under 90°C to be compatible to OLED device. Here, new optical system composed of LTCF and OLED micro cavity, can demonstrate high outdoor readability, low power consumption, and a wide viewing ability.

----- Lunch -----

13:20 - 16:20

Poster/A.I. Room

Poster OLEDp: OLED Technologies

OLEDp - 1 UV-Influence Suppressed on the Device Characteristic of a-IGZO Thin-Film Transistors Using Solution Based TiOx

C.-W. Chou, H.-H. Lu, H.-C. Ting, T.-H. Shih, C.-Y. Chen, Y.-S. Lin

AU Optronics, Taiwan

The TiO_x film was proposed to lower the ultra-violet (UV) influence on the device characteristics of amorphous indium gallium zinc oxide (a-IGZO) thin-film transistors (TFTs). After UV treatment, a-IGZO TFTs passivated with TiOx film showed less shift and degradation on electrical characteristics.

OLEDp - 2 High Transparency Organic Light-Emitting Diodes Based on Multilayer Transparent Electrodes

J. Choi, H. Cho, S. Yoo KAIST, Korea

We present organic light-emitting diodes (OLEDs) based on multilayer transparent electrodes (MTEs) which exhibit luminance over $8000cd/m^2$ and turn-on voltage of 2.7 V. The MTEs consist of Ag/Cs₂CO₃ cathode with a ZnS capping layer. Our OLEDs show 82% of peak transmittance (at 600 nm) and 73% average transmittance in the visible region.

Thursday

OLEDp - 3 Optimization of Micro Lens Array (MLA) Pattern for the Improvement of Light Extraction Efficiency in OLED Devices

H. J. Lee, H. K. Bae, B.-S. Kim, C. S. Oh, C.-G. Son^{*}, L. S. Park Kyungpook Nat. Univ., Korea

*Yeungnam Univ., Korea

In this paper we discussed the effect of micro lens array (MLA) pattern fabricated on the glass substrate of organic light emitting diode (OLED) for improvement of light extraction efficiency. The effect of MLA on light extraction efficiency from OLED was examined by the fabrication of various MLA on the devices.

OLEDp - 4 Highly Polarized Electroluminescence from OLEDs with a Quarter-Wave Retardation Plate Films and a Reflective Polarizer

B. Park, Y. H. Huh, Y. I. Lee, J. C. Shin, H. G. Jeon Kwangwoon Univ., Korea

We present a highly polarized OLED using a quarter-wave plate film and a reflective polarizer, which exhibited emissions of 13,400 cd/m^2 with peak efficiency of 10.3 cd/A and degree of polarization over 40. These are almost two times higher than those of the polarized OLED using only a reflective polarizer.

OLEDp - 5 Improvement of Luminance Distribution in Transparent OLED by Using ITO/APC/ITO Top Electrode

T. Uchida, M. Yahata, K. Sakurai, K. Yamada, T. Satoh, T. Tamura

Tokyo Polytechnic Univ., Japan

We fabricated films with both high electrical conductivity and high optical transparency by using Zn-doped In oxides (IZO) with an inserted thin Ag-Pd-Cu (APC) film. Transparent organic light-emitting diodes (OLEDs) with an IZO/APC/ IZO top electrode indicated better luminance uniformity than the device with a single IZO cathode.

OLEDp - 6 High Hole Conduction Technology for OLEDs

J. H. Yu, W. S. Jeon, J. S. Park, D. C. Lim, Y. J. Doh, J. W. Choi, Y. H. Son, J. H. Kwon Kyung Hee Univ., Korea

An interesting high hole conduction configuration with extremely low driving voltage characteristics in phosphorescent green OLEDs is reported. The configuration of a hole transporting layer (HTL)/ electron extraction layer (EEL)/ HTL results in 1.1×10^{-2} cm²/Vs hole mobility at electric field of 0.1 MV/cm².

OLEDP - 7 Properties of Organic Light Emitting Diodes with Very Thin MoO₃ Layer and Characterization of the MoO₃ Layer Deposited on ITO Anode

S. Yoshida, M. Kawamura, Y. Abe Kitami Inst. of Tech., Japan

With a MoO₃ hole injection layer, device performance of prepared OLEDs was improved significantly. The results showed optimum thickness of the MoO₃ to be 1.0 nm. Coverage of ITO surface was not complete with MoO₃ of that thickness by AFM observation. It became complete with the MoO₃ of 2.0 nm.

OLEDp - 8 Fluorescence Analysis of ITO-Sputtering Damage of an Organic Film

N. Takada, S. Hoshino, K. Suemori, T. Kamata, N. Ibaraki, S. Suenaga^{*}, B. Tanaka^{*}, N. Hamanaga^{*}, K. Aoe^{*}, E. Tao^{*}

AIST, Japan ^{*}Choshu Ind., Japan

The fluorescence damage analysis technique taking account of the optical interference effect and exciton diffusion/quenching mechanism was developed and ITO (Indium-tin-oxide) sputtering damage to an Alq₃ (tris(8-hydroxyquinoline) aluminum) film was evaluated. Using the model that sputtered ITO particles scrape off Alq₃ surface, we elucidated Alq₃ film damage of about 5nm.

OLEDp - 9 Pre-Metered Horizontal Dipping Method for Simple Fabricating Large OLEDs

B. C. Park, H. G. Jeon, K. H. Choi Kwangwoon Univ., Korea

Pre-metered horizontal dipping (H-dipping) was studied for fabricating OLEDs by using concave meniscus of used solutions. H-dipped OLEDs were fabricated with high performance; maximum efficiency of 19.3 cd/A with 40,600 cd/m². Patterned OLEDs on 5.6-in. substrates were successfully fabricated, implying that H-dipping holds great potential for large-area OLEDs.

OLEDp - 10 Withdrawn

OLED

OLEDp - 11 New Small Molecule Host System for Slution-Pocessed Red Phosphorescent OLEDs

Y. H. Son, K. H. Kim, W. S. Jeon, J. S. Park, D. C. Lim, Y. J. Doh, J. W. Choi, J. H. Kown Kyung Hee Univ., Korea

High efficiency solution-processed red phosphorescent OLEDs with new small molecule mixed host systems are reported. This fabricated red phosphorescent OLED with (lr(phq)₂acac) dopant and 2-TNATA: TPBI mixed host has a driving voltage of 5.2 V and maximum current and power efficiencies of 17.8 cd/A and 11.3 lm/W, respectively.

OLEDp - 12 Combination of Inorganic Hole Injection Layer and Organic Hole Transport Layer in OLED Technology

- Z. Hotra^{*,**}, P. Stakhira^{*}, V. Cherpak^{*}, D. Volynyuk^{*},
- L. Voznyak^{*}, N. V. Kostiv^{*}

^{*}Lviv Polytechnic Nat. Univ., Ukraine ^{**}Rzeszow Univ. of Tech., Poland

In this work we proposed OLED structure with inorganic copper iodide (Cul) as hole injection layer combine with organic nickel phtalocyanine (NiPc) as hole transport layer. It was shown that combine inorganic Cul hole injection layer and organic NiPc as hole transport layer reduced operating voltage and improved OLED performance.

OLEDp - 13 Novel and High Efficient Yellow Phosphorescent Iridium Emitters

H.-L. Huang, T.-C. Chao, M.-R. Tseng ITRI, Taiwan

We investigated and synthesized different orientation and substituted group of the thieno-pyridine framework organo-iridium yellow complexes (PO-01, PO-01-TB). The electroluminescent current efficiencies of the devices were from 62.8 cd/A to 64.8 cd/A under the brightness of 1000 cd/m² and EQE were all above 18.5% to 20.4%.

OLEDp - 14 Highly Operational Color Stability of Blue Organic Light-Emitting Diode

T.-L. Chiu, P.-Y. Lee, C.-H. Hsiao^{*}, J.-H. Lee^{*}, C.-Y. Chen^{*}, M.-K. Leung^{*}

Yuan Ze Univ., Taiwan ^{*}Nat. Taiwan Univ., Taiwan

A color stability blue organic light-emitting device (B-OLED) with blue phosphorescent dopant iridium(III)bis(4,6-difluorophenyl-pyridinato- N,C^2)picolinate (FIrpic) was demonstrated in this paper by fine-tuning its doping concentration. Under continuous operation, the maximum color coordinate variation of B-OLEDs with FIrpic concentration 3~15% is Δx =0.008 and Δy =0.02 as applied voltage from 4.5 to 11V.

OLEDp - 15 Fabrication of Thin Film by Plasma Polymerization and Application to Organic Light Emitting Device

S. Ojiro, R. Koyama, S. Hikita, Y. Sato, S. Yoshikado Doshisha Univ., Japan

Thin film appricable to light emitting device was deposited using plasma polymerization of benzene monomer by discharge at 13.56 MHz. The effects of discharge power and electrode distance on the quality were investigated. Sharp infra-red absorption peak caused by C=C expansion and contraction of benzene ring was observed around 133 Pa.

OLEDp - 16 Fabrication of 4-Wavelength White Organic Light-Emitting Diodes Including Two Emissive Layers and Three Primary Colors

Y.-H. Kim, S. Y. Lee, W. Song, M. Meng, H. J. Yang, K. W. Kim, W. Y. Kim Hoseo Univ.. Korea

4-wavelengh white organic light-emitting diode concluding three primary colors was fabricated using two emissive layers. White emission characteristics of the OLED such as CIE coordinates, efficiency, and max luminescence were (0.32, 0.37) at 6 V, 7.1 cd/A at 199 cd/m², and 10659 cd/m² at 8 V, respectively.

OLEDp - 17 High Color-Stability for White Organic Light Emitting Devices by Using Phosphorescent Sensitizer Fluorescent

F.-S. Juang, L.-A. Hong, C.-J. Hsiao, S.-H. Wang, M.-H. Ho^{*}, C.-H. Chen^{*}

Nat. Formosa Univ., Taiwan *Nat. Chiao Tung Univ., Taiwan

High color-stability white-OLED was achieved by using a yellow dopant in phosphor-sensitized emitter and optimizing the interlayer thickness. Device shows the E.Q.E. of 8.2%, and the efficiency of 21.5 cd/A with CIE (0.40, 0.46) at 20 mA/cm². The shift of $CIE_{X,Y}$ down to (-0.001, -0.001) from 20 to 200 mA/cm².

OLEDp - 18 Inorganic Nanolaminates on Polymer Substrates as Gas-Diffussion Barriers in Flexible Electronics Structures

J. -H. Choi, Y. -W. Park, J. W. Jeong, T. H. Park, H. J. Choi, E. H. Song, D.-J. Ham, J.-W. Lee^{*}, C.-H. Kim^{*}, B.-K. Ju

Korea Univ., Korea *Cheil Inds., Korea

A SiO₂/Al₂O₃ nanolaminate gas-diffusion barrier film on a plastic substrate was proposed. The Ca-test indicates that such laminate films can effectively suppress the void defects of an inorganic layer, and are significantly less sensitive against moisture permeation. This nanostructure is verified as being useful in highly water-sensitive flexible organic electronics.

OLEDp - 19 Improved Lifetime of Highly Flexible OLEDs Based on Multilayer Transparent Electrodes with Enhanced Barrier Performance

S. Park, K. H. Jung, C. Yun, H. Cho, B.-S. Bae, S. Yoo KAIST, Korea

We present multilayer transparent electrodes (MTEs) fabricated on polyethylene naphthalate (PEN) substrates coated with organicinorganic hybrimers that lead to improved barrier characteristics. Lifetime measurement shows that flexible organic light-emitting diodes (OLEDs) with these MTEs have a reliability that is far superior to ITObased counterparts under repeated bending.

OLEDp - 20 Evaluation Technology to Verify Flexible Gas Barrier Property Based on Electrical Calcium Degradation for Electronics Application

E. H. Song, Y. W. Park, J. W. Jeong, J. H. Choi, T. H. Park, H. J. Choi, B. K. Ju Korea Univ., Korea

Ca-test was designed to evaluate barriers property by checking current changing through the tested calcium cell. We introduce newly designed Ca-test model which can measure about two times faster than formal model. Moreover this structure can be bent, so we can analyze barrier property degradation by forcing bending stress.

OLEDp - 21 Transfer-Printed Integrated Circuits for Display Backplanes

C. A. Bower, D. Gomez, K. Lucht, B. Cox, D. Kneeburg Semprius, USA

Conventional thin-film transistor (TFT) backplanes do not exhibit the performance required for current-driven active-matrix OLED (AMOLED) displays. Here, we report on the latest results of fabricating active-matrix display backplanes using transfer-printed high-performance integrated circuits. We will present the print yield and print accuracy, as well as strategies for backplane fabrication.

OLEDp - 22 The Electrical Characteristics of Organic Light Emitting Diodes Applied Organic Photo Sensor for Emotional Lighting Applications

J. W. Jeong, Y. W. Park, T. H. Park, J. H. Choi, H. J. Choi, E. H. Song, J. I. Lee^{*}, H. Y. Chu^{*}, B. K. Ju

Korea Univ., Korea *Elect. & Telecommun. Res. Inst., Korea

This paper reports on a study of the emission properties of organic light emitting diodes (OLEDs) controlled by an organic photo sensor (OPS) for emotional lighting applications. The luminance of the OLED increased from 283.4 cd/m² to 1134 cd/m² when the OPS was exposed to different illumination levels.

OLEDp - 23 The Influence of Operating Temperature on the Electrical Characteristics of Pentacene Thin-Film Transistors

L.-Y. Chiu, C.-C. Tai, W.-Y. Chou, F.-C. Tang, H.-L. Cheng Nat. Cheng Kung Univ., Taiwan

The effect of temperature on the electrical characteristics of pentacene-based organic thin-film transistors (OTFTs), including mobility, threshold voltage and hysteresis behaviors, was investigated. Increased charge mobility and enlarged hysteresis were observed at higher temperature, suggesting that the environmental thermal energy plays an important role to device performance of PEN-based OTFTs.

OLEDp - 24 Withdrawn

OLEDp - 25 The Study of the Performance of Organic Solar Cells by the Electrode and Characteristics of Interfacial Layers

N. S. Knag^{*,**}, J.-W. Yu^{***}, I.-D. Kim^{**}, J.-M. Hong^{**}, B.-K. Ju^{*}

*Korea Univ., Korea **Korea Inst. of S&T, Korea ***Kyung Hee Univ., Korea

We reported on the effect of organic photovoltaics by conductivity of interlayer such as PEDOT:PSS and TCO (Transparent conducting oxide) such as ITO, which is used P3HT and PCBM. And, we have measured with exactly defined shadow mask to study effect of solar cell efficiency according to conductivity of hole transfer layer.

OLEDp - 26L Electroluminescence Properties of Novel Hyper-Branched Light-Emitting Polymers Based Devices

R.-H. Lee, W.-S. Chen, Y.-Y. Wang Nat. Chung Hsing Univ., Taiwan

A series of hyper-branched polyalkylfluorenes (HBPFs) with an electron-conducting group, triazine and a hole-conducting group, triphenylamine as molecular cores were synthesized by the Suzuki coupling reaction. This series of HBPFs with different conjugated lengths were end-capped with a hole-conducting group, triphenylamine, and a rigid moiety, tetraphenylsilane.

OLEDp - 27L Surface Plasmon Enhanced Optoelectronic Performance of a Conjugated Polymer Using Ag Dot Arrays

J. Y. Kim, K. H. Cho, Y. Yeo, K. C. Choi KAIST, Korea

In this work, the optoelectronic performance of a conjugated polymer with silver dot arrays was investigated. The silver dot fabrication based on the imprint method resulted in a 2.7-fold enhancement of the integrated PL intensity by successfully coupling between the surface plasmon and excitons in the emitting layer.

OLEDp - 28L Solution Processed White Light Emitting Devices Using a Novel Orange Triplet Emitter

J.-Y. Liao, T.-C. Chao, J.-S. Lin, M.-R. Tseng Material & Chem. Res. Labs. Ind. Tech. Res. Inst. (ITRI), Taiwan

The solution processed white light emitting devices composed of a novel orange emitter, PO-01-TB, and the blue emitter, FIrpic, are studied. Devices with efficiencies of 22 cd/A and 10 lm/W are reported by mixing the orange and blue emitters into PVK/OXD-7 matrix.

OLEDp - 29L The Other Crucial Factor Dominates the Holes Injection Efficiency of Ultra-thin Anode Buffer Layer on Organic Light Emitting Devices

S.-Y. Chu, Y.-C. Chen, H.-H. Huang, P.-C. Kao^{*} Nat. Cheng Kung Univ., Taiwan ^{*}Nat. Chiayi Univ., Taiwan

In this study, we have investigated surface energy of ITO substrates modified by ultra-thin buffer layers plays crucial factor as important as energy barrier. With larger surface energy, organic light emitting devices could get superior performance even there exist larger barrier between ultra-thin buffer layer modified ITO and organic layer.

OLEDp - 30L Synthesis and Characterization of Novel Blue-Light-Emitting Fluorene-Carbazole Copolymers with Boryl Substitutions

Y.-H. Chen, Y.-Y. Lin, Y.-C. Chen^{*}, J. T. Lin^{*}, R.-H. Lee, R.-J. Jeng Nat. Chung Hsing Univ., Taiwan ^{*}Academia Sinica. Taiwan

Novel carbazole/fluorene-Based copolymers with dimesitylboron pendants were synthesized by Suzuki polymerization for blue lightemitting diodes. Different energy levels and electroluminescence performances were observed for the copolymers via tuning the conjugation length of the side chain.

OLEDp - 31L Metal Mask Printing Method for Organic Light-Emitting Diodes Fabrication

H. Ishiguro, S. Naka, H. Okada Univ. of Toyama, Japan

We have investigated "metal mask printing method" for organic light emitting diodes, which is simple technique for short-tact time, largearea and high-resolution device fabrication. Maximum luminance of 270 cd/m² was obtained for self-aligned single layer device.

OLEDp - 32L Enhanced Electron Injection into Alq₃ Based OLEDs Using a Thin Potassium Carbonate Buffer Layer

P.-C. Kao, C.-C. Chang, S.-I. Lin Nat. Chiayi Univ., Taiwan

A cathode buffer layer of potassium carbonate (K_2CO_3) was used to improve the electro-optical properties of organic light-emitting diodes (OLEDs). The improvement can be attributed that the electron-injection efficiency was enhanced due to a lower electron injection barrier, which improves the charge carrier balance in OLEDs.

----- Break -----

16:40 - 18:05

Room 501

AMD5/OLED6: AM-OLED

Chair: D. Pribat, SungKyunKwan Univ., Korea Co-Chair: Y. Fujisaki, NHK, Japan

AMD5/InvitedProcess Development of Amorphous Indium-OLED6 - 1:Gallium-Zinc-Oxide Thin-Film Transistors for Large16:40Size AMOLED Applications

H.-C. Ting, H.-H. Lu, T.-H. Shih, L.-C. Lee, C.-W. Chou, L.-P. Shin, S.-S.Wang, T.-C. Wan, C.-Y. Chen, Y.-H. Lin

AU Optronics, Taiwan

In this paper, we will show how to approach a-IGZO TFTs AMOLED in Gen 6 Fab currently. We evaluated the TFTs structure from bottom gate coplanar to BCE type with Mo/AI/Ti as S/D electrode. Using photosensitive organic passivation layer and TiO_x coating to improved the device performance and stability.

AMD5/ High Mobility Oxide Semiconductor TFT for Circuit OLED6 - 2 Integration of AM-OLED 17:05 E. Fukumoto, T. Arai, N. Morosawa, K. Tokunaga, Y. Terai, T. Fujimori, T. Sasaoka Sony, Japan

We have developed a high mobility and high reliability oxide semiconductor TFT which used ITZO as a channel material. Its mobility and Δ Vth after 20,000sec of BTS test were 30.9 cm²/Vs and 0.1 V. We have achieved a stable enhancement type TFT, which realizes circuit integration for AM-OLED.

AMD5/ OLED6 - 3 17:25	A New Simple Pixel Circuit Compensating the Threshold Voltage for AMOLED Displays
	YI. Hwang, YS. Park, KN. Kim, BH. Kim, B. H. Berkeley, SS. Kim, BD. Choi [*]
	Samsung Mobile Display, Korea [*] Sungkyunkwan Univ., Korea

We propose new simple pixel compensation circuits with three or four thin film transistors (TFTs) and one capacitor. In addition to compensating the deviation of the threshold voltage of the driving TFTs, we can compensate IR-drops and reduce the number of components in compensation circuits with these novel circuits.

AMD5/ 4.1-in. Full Color AMOLED Driving by Top Gate OLED6 - 4 Nanocrystalline Silicon Thin Film Transistor Array 17:45 K.-Y. Ho, H.-C. Lin, H.-S. Dai, P.-F. Lee, C.-C. Hsu, S.-Y. Peng, C.-W. Lin, C.-H. Cheng, B.-C. Kung, W.-Y. Chao, J.-Y. Yan, H.-C. Cheng ITRI, Taiwan

High performance nanocrystalline silicon thin film transistors are achieved with top gate staggered structure. The nc-Si is directly deposited by 13.56 MHz plasma enhanced chemical vapor deposition (PECVD) at 200°C. Good device perf ormance, uniformity, and reliability make it possible to be integrated into active matrix organic light emitting diode (AMOLED) applications.

Author Interviews

18:00 - 19:00

Workshop on 3D/Hyper-Realistic Displays and Systems

Thursday, December 2

9:00 - 10:20		Room 412
	3D1: Holography and 3D Display	

Chair: T. Horikoshi, NTT DoCoMo, Japan Co-Chair: K. Yamamoto, NICT, Japan

 3D1 - 1:
 Invited
 Spatial Imaging Based on Extremely High

 9:00
 Definition Computational Holography — Wave-Field

 Oriented 3D Imaging —

K. Matsushima Kansai Univ., Japan

Extremely high-definition displays beyond Super Hi-Vision give us a new horizon in the field of 3D imaging. This paper introduces spatial 3D imaging brought by computational holography and techniques for numerical propagation of wave-fields that make it possible to create the spatial 3D images.

3D1 - 2 9:20	24 Mega Pixels Phase Electroholography
	T. Shimobaba, H. Nakayama, N. Masuda, N. Takada [*] , T. Ito
	Chiba Univ., Japan *Shohoku College, Japan

We report a phase-type electroholography that can reconstruct 3D objects from 24-mega pixels phase-type CGHs, with large and wideviewing angle. To solve the problems of the size and viewing angle, we used 12 phase modulated LCDs. For real-time calculation, we used a GPU cluster and the wave-recording plane method.

3D1 - 3Simplified Novel Look-Up Table Method Using9:40Compute Unified Device Architecture

Z. Ali, J.-H. Park, N. Kim Chungbuk Nat. Univ., Korea

In this study, we have exploited the parallel nature of the computations involved in the process of digital holography using novel look-up table method. We utilize CUDA enabled GPU to accelerate each step of the digital holography. Our simulation results confirm that the GPU implementation is much faster than CPU.

3D1 - 4L Imaging Characteristics of Array of Dihedral Corner 10:00 Reflectors by Use of Gaussian Beam Decomposition

S. Yokoyama^{*,**}, K. Nitta^{*}, O. Matoba^{*}, S. Maekawa^{**} ^{*}Kobe Univ., Japan ^{**}NICT, Japan

A methodology to analyze an imaging optics with dihedral corner reflector array is reported. This methodology is based on the Gaussian beam decomposition and achieves results of analysis with simple operation for beam propagation. Usefulness of the methodology is verified and novel characteristics obtained by the methodology are reported.

3D1 - 5L A Real-Time Color Electrohorographic 10:10 Reconstruction System Using a Multi Graphics Processing Unit Processing Unit

N. Takada, H. Nakayama^{*}, S. Awazu^{*}, Y. Ichihashi^{**}, T. Shimobaba^{*}, N. Masuda^{*}, T. Ito^{*}

Shohoku College, Japan ^{*}Chiba Univ., Japan ^{**}NICT, Japan

Electroholography is a technique for realizing three-dimensional (3-D) television. We developed a color electroholographic system consisting of three liquid-crystal display panels and three graphics processing units. Thesystem succeeded in animating 3-D images composed of about 1,500 points in each light's primary color at nearly video-rate.

----- Break -----

10:40 - 12:00

Room 412

3D2: 3D Display (1)

Chair:	K. Matsushima, Kansai Univ., Japan
Co-Chair:	S. Yano, NHK, Japan

3D2 - 1: Invited 3-D Display Interaction

10:40 M.-C. Park, H.-D. Lee, J.-Y. Son* Korea Inst. of S&T, Korea *Daegu Univ., Korea

Interactions take place as two or more objects and/or beings effect upon one another. 3-D display enhances visual presence and enriches personal experience. 3-D display interaction is effective to exchange and share of thoughts, feelings, experiences and ideas. Our researches are introduced in the aspect of 3-D display interaction.

3D2 - 2: Invited 3D Volumetric Scanned Light Display with 11:00 Multiple Fiber Optic Light Sources

B. T. Schowengerdt, E. J. Seibel Univ. of Washington, USA

A custom array of 16 singlemode optical fibers positions the end of each fiber a different distance from a collimating lens, placing light from each fiber at a different focus level. The superimposed multifocal beams are raster-scanned to generate a volumetric display, with each fiber writing to a different layer.

3D2 - 3 LC Grin Lens for a Multi-View 3D Display

11:20 P. W. Wu, W. L. Chen, C. H. Shih, W. M. Huang AU Optronics, Taiwan

A 5-view 2.83-in. 2D/3D switchable displays with low crosstalk and low driving voltages were fabricated. By changing different applying voltages, suitable LC orientations are configured to obtain good 3D performance for displays of different optimal viewing distance design.

3D2 - 4Moiré Pattern Reduction by Using Special Designed11:40Parallax Barrier in an Autostereoscopic Display

W.-T. Yen, C.-L. Wu, C.-L. Wu, C.-H. Tsai, C.-J. Chou ITRI, Taiwan

To minimize the moiré effect, we simulate the relationship of brightness distribution and various design parameters of the parallax barrier. According to the simulation results, a combination of multiple parameters was chose to obtain a moiré free autostereoscopic display based on the concept of mutual compensation among the design parameters.

----- Lunch -----

13:20 - 16:20

Poster/A.I. Room

β

Poster 3Dp: 3D/Hyper-Realistic Displays and Systems

3Dp - 1 An Evaluation Method of Cross-Talk on Stereoscopic LCD with Frame Sequential Method and a Directional Backlight System

A. Sakai, A. Hayashi, T. Kometani, H. Ito Eizo Nanao, Japan

There are two types of cross-talk on stereoscopic LCD based frame sequential method with a directional backlight system. One is optical cross-talk in a directional backlight system, and the other is caused by slow response of LC panel. This paper considers about a method for evaluating them overall.

3Dp - 2 Perceived Depth Change between Real Objects with Different Visual Acuities of Both Eyes

K. Sadakuni, T. Inoue, H. Yamamoto, S. Suyama Univ. of Tokushima, Japan

In stereoscopic display, the amount of perceived depth change is quickly decreased when both eyes have different visual acuities. On the contrary, in real object, the amount of perceived depth change is gradually decreased when both eyes have different visual acuities.

3Dp - 3 Study of 3D-Image Influence on Visual Region by EEG Analysis

C.-Y. Chen, M.-D. Ke, Y.-R. Pan, C.-P. Chen, S.-W. Cheng Nat. Yunlin Univ. of S&T. Taiwan

The electroencephalograms (EEG) of visual region from 60 volunteers were measured during watching a 3D movie. While the volunteers viewing a movie, α wave decreased but β wave increased in the occipital zone (visual region). Besides, there was no difference between viewing 2D and 3D movies.

3Dp - 4 Evaluation of Gray to Gray Performance in Stereoscopic Displays

W.-C. Tsai, M.-H. Yang, H.-S. Ruan, C.-W. Chen, K.-C. Chang, K.-S. Wang

AU Optronics, Taiwan

Methods of analyzing crosstalk in stereoscopic displays with arbitrary gray level are demonstrated. We proposed novel viewpoints which are based on gray to gray look-up table to quantify ghosting artifact and are applicable to all types of stereoscopic displays.

3Dp - 5 The Fabrication of Autostereoscopic Panel Used Four-Level Diffractive Splitter on a Quartz Substrate

C.-Y. Chen, W.-C. Hung, Q.-L. Deng, Y.-R. Chang Nat. Yunlin Univ. of S&T, Taiwan

In this paper, a new autostereoscopic panel used diffractive splitter is fabricated on a transparent quartz substrate. The diffractive efficiency of the quartz four-level blaze grating can reach 55.3%, that the device can replace the lenticular type or barrier type autostereoscopic panel, and make the brightness of panel much increased.

3Dp - 6 Three-Dimensional Display Using a Roof Mirror Grid Array and a Prism Sheet

Y. Maeda^{*}, D. Miyazaki^{*,**}, N. Hirano^{*}, S. Maekawa^{*} ^{*}Osaka City Univ., Japan ^{**}NICT, Japan

We developed a three-dimensional display using a roof mirror grid array, which is an optical imaging element that forms a real image, and a rotating prism sheet. The use of the rotating prism sheet can reduce a blur caused by diffraction at the roof mirror grid array.

3Dp - 7 Reflective 3D LC Display with Patterned Retarder

K.-S. Bae, U. Cha, Y.-H. Kim, J.-H. Kim, C.-J. Yu Hanyang Univ., Korea

We report a stereoscopic 3D liquid crystal display in a reflective type. Using the cholesteric liquid crystal with a patterned retarder, two orthogonal polarization states are obtained and thus the stereoscopic images are constructed.

3Dp - 8 A New Basis Representation for Multiview Image Using Directional Sampling

T. Yamada, T. Fujii Tokyo Inst. of Tech., Japan

To compress or interpolate the multiview image efficiently, we propose a new basis representation. By using directional sampling, we apply directional 3D-DCT and directional 3D-DWT to three dimensional data. In the experimental results, the proposed method showed better quality than previous method, not only in the objective/ subjective evaluation.

3Dp - 9 Development of a Novel Virtual Reality 3D Display: the "J-Display"

W. J. Tam, C. Vázquez Commun. Res. Ctr., Canada

A novel type of stereoscopic 3D display to improve sense of virtual reality is proposed. The display has a curvilinear surface that allows stereoscopic objects to be viewed as being naturally "grounded" and not cut off as with standard displays. A tabletop prototype is described and future development is discussed.

3Dp - 10 A Scent-Emitting Thin Type LED Display Device with a Porous Screen, and It's Application

A. Tomono, H. Katsuyama, K. Tomono^{*} Tokai Univ., Japan ^{*}Wartburg College, USA

We propose a new method where scents are ejected through the display in order to enhance the reality of the visual images. A thin LED panel filled with tiny pores was made for this experiment, and an air control system using a blower was placed behind the display screen.

133

3Dp - 11 Holographic Optical Elements for Stereoscopic Vision on LCD Panel

W.-C. Su, C.-Y. Chen^{*}, Y.-F. Wang^{*}, H.-W. Ho^{*}

Nat. Changhua Univ. of Education, Taiwan ^{*}Nat. Yunlin Univ. of S&T, Taiwan

A holographic image splitter for stereoscopic effect on liquid crystal display panel is developed in this study. We designed and generated a special holographic optical element to replace the traditional image splitter in a stereoscopic display panel. Experimental results support the idea well.

3Dp - 12 Full Color Rewritable Photorefractive Large Area Display Material

M. Yamamoto, P. Wang, T. Gu, W. Lin, H. Wanyun, O. Siddiqui, A. Bablumyan^{*}, A. Ordyan^{*}, P. Blanche^{*}, R. Voorakaranam^{*}, N. Peyghambarian^{*} NITTO DENKO Tech., USA

NITTO DENKO Tech., USA *Univ. of Arizona, USA

Organic polymer-based photorefractive materials which have both better diffraction efficiency and longer grating persistency have been improved. The materials were succeeded in principle-proving concept of highly image-persistent and rewritable holographic display systems. By using materials, we are aiming for developments of holographic display devices such as medical imaging devices.

3Dp - 13L 3D Display with No Physical Constraints Force Feedback Function

M. Tsuboi, S. Kimura, M. Fukumoto, T. Horikoshi NTT DoCoMo, Japan

A 3D display with force feedback function is proposed. In proposed system, neither physical connections to outer point, actuators, nor batteries are needed to pen-type device. Also, horizontal motion parallax is achieved and no conflicts between the position of 3D images and pen-type device.

3Dp - 14L Variable Parallax 3D Display for Mobile Application

H. Song, Y.-S. Choi, K.-H. Choi, J.-M. Bae, H.-S. Lee, S.-Y. Lee

Samsung Elect., Korea

A variable parallax 3D display with a backlight unit having partitions in which a direction of light extraction angle can be regulated are proposed. Such concept was implemented in a prototype and verified that it could switch 3D parallax images between a landscape mode and portrait mode.

3Dp - 15L Turn-type Color 3-D Display System Using Arrays of LEDs

T. Shimizu, Y. Sakamoto, I. Fukuda Kanazawa Inst. of Tech., Japan

We developed a depth sampling type 3-D display system. The system is designed to capable of displaying a three-dimensional image by turning LEDs (Light Emitting Diodes) arrays. Recently, we successfully improved the brightness of the 3D display system. This report provides a detailed description of this improvement.

3Dp - 16L Impact of Spatial 3D Imaging by Extremely High-Definition Computational Holography

K. Matsushima, H. Nishi, Y. Arima, K. Higashi, M. Nakamura, S. Nakahara Kansai Univ., Japan

Spatial 3D images created by high-definition computational holography are actually demonstrated. The demonstrated 3D images are static images at this stage. However, these presage the great future of 3D displays beyond the Super Hi-Vision because of its strong sensation of depth, which never has been caused by conventional 3D systems.

----- Break -----

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16:40 - 18	:00 Room 413	
	3D3/DES3: 3D System and Content	
Chair: Co-Chair:	JY. Son, Daegu Univ., Korea T. Fujine, Sharp, Japan	
3D3/ DES3 - 1: 16:40	Invited Full HD and Super-High Image Quality 3D Plasma TV Technology	
	K. Tasaka, M. Kawashima, K. Suetsugi, M. Ishizuka, T. Yamashita, Y. Sugio	
	Panasonic, Japan	

This paper introduces the basic concept of Full HD and High Image Quality 3D Plasma Theater System and the key technology of Full HD and Super-High Image Quality 3D Plasma TV which was realized by the newly developed technology of Plasma panel improvement and new 3D system technology of both Plasma panel and 3D eyewear.

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3D3/InvitedReal-Time 2D-to-3D Conversion: BasicDES3 - 2:Concepts and Practical Use17:00K. Yamada, Y. Suzuki

JVC Kenwood Holdings, Japan

This paper describes the algorithm for our original 2D-to-3D conversion technology, which is beginning to be used for both consumer and professional apparatuses to fulfill the growing need for high quality 3D contents. The algorithm has advantages in quality, numerical complexity, no need of frame memory and very low latency.

3D3/ Invited From 3D technology to New Styles of Visual DES3 - 3: Images 17:20 Million A Octo V Alfabeted

7:20 M. Ikeo, A. Saito, Y. Nishida NHK Media Tech., Japan

The desire to visualize our imagination in new ways has encouraged the evolution of the media, while technical innovation has inspired our imagination. However, recent rapid advances in digital technology are leading the media not to represent human imagination but to mirror the actual world with ever greater reality. Can filmmakers' imagination catch up with the hyperrealism of the visual media? Content creators must shed the bonds of 3D images and develop new styles of visual images.

3D3/ Invited 3D Video Formats and Compression for DES3 - 4: Content Distributions

17:40

H. Kimata

NTT, Japan

Usage of 3D video would increase as the growth of 3D content production. The suitable 3D video format depends on the purpose in applications. This paper summarizes 3D video formats and compression technologies distinguished by purposes and it addresses the trends of stereoscopic video and multi-view video formats.

Author Interviews

18:00 - 19:00

Friday, December 3

10:40 - 12:10		Room 502
	VHF8/3D4: 3D Human Factors	
Chair: Co-Chair:	S. Clippingdale, NHK, Japan H. Yamamoto, Univ. of Tokushima, Japan	

VHF8/
3D4 - 1:InvitedSafety in 3D Broadcast, and Study in 3D10:40Y. Imai, K. Imanishi, T. Okunaga

SKY Perfect JSAT, Japan

SKY Perfect TV started broadcasting 3D channel from June 2010 and carried out the test shooting and the examination for a safe and easy-to-watch 3D broadcast. We studied the cause of fatigue and discomfort in watching 3D image by using images of soccer game and that of a woman.

VHF8/ 3D4 - 2 11:10	Evaluation of Viewability to Hyper-Realistic Picture
	N. Suzuki [*] , S. Yano ^{*,**}
	*NICT, Japan
	**NHK, Japan

This paper provides a subjective and objective evaluation of the viewability of hyper-realistic images. First, we examined the preferable viewing distance for images of different sizes, including monoscopic and stereoscopic images. Second, we measured the eye movements of participants in a previous experiment comparing preferable with non-preferable viewing distance.

VHF8/Measurement of Accommodation and Vergence3D4 - 3Responses while Viewing Two-View and Multi-View11:303D Displays

H. Mizushina, I. Negishi, H. Ando^{*}, S. Masaki Advanced TeleCommun. Res. Inst. Int., Japan ^{*}NICT, Japan

We measured accommodation and vergence responses simultaneously while viewing two-view 3D display based on polarized glasses and multi-view 3D display based on parallax barrier. Difference between two-view and multi-view conditions was observed in the vergence response, but not in the accommodation response.

VHF8/Influence of Luminance Gradient on Three3D4 - 4Dimensional Perception for Real Object and Digital11:50Image

K. Iwauchi^{*,**}, T. Takahashi^{**}, T. Eda^{**}, T. Ishikawa^{**}, M. Ayama^{**} ^{*}Sharp, Japan ^{**}Utsunomiya Univ., Japan

We investigated 3D perception using real objects and digital images. The results indicate that the absolute luminance value of the brightest area and the luminance gradient are the two most important factors for 3D perception of real objects, whereas a degree of gradient enhancement is needed for digital images.

13:20 - 14:40

Room 502

3D5: 3D Image Quality

Chair: M.-C. Park, Korea Inst. of S&T, Korea Co-Chair: T. Mishina, NHK, Japan

3D5 - 1:InvitedCrosstalk in 3D-TV: Modeling, Adaptive13:20Cancellation Algorithms and Perceptual Validation

L. Kerofsky, Y. Yoshida^{*}, S. Deshpande, I. Sezan Sharp Labs. of America, USA ^{*}Sharp, Japan

Reduction of crosstalk for active glasses 3D-TV is analyzed. Crosstalk is characterized defining in-range and out-of-range pixel pairs. A distance minimizing algorithm cancels in-range crosstalk. Subjective quality improvement is validated. An adaptive algorithm reduces crosstalk due to out-of-range values while preserving image quality.

3D5 - 2Human Factor for 3D Angular Uniformity Intensity13:40Tolerance

R.-W. Liao, C.-S. Cheng, C.-H. Shih, W.-M. Huang AU Optronics, Taiwan

We propose a simple human factor experiment to know the threshold 3D AIU (angular uniformity intensity) of human eyes. We design different patterns corresponding to 3D AIU% to simulate the real case of human eyes. According to results, we can define the threshold 3D AIU is 98.82%.

3D5 - 3A New Method for Quality Control of Shutter14:00Glasses 3D Displays

P. Boher, T. Leroux, V. C. Patton ELDIM, France

We use a videoluminance meter to check the quality of shutter glasses 3D displays rapidly and easily. A dedicated pattern is applied to check simultaneously the effect of the grey level on the other eye and of the temporal synchronization. The visual impact of grey level instabilities is precisely quantified.

3D5 - 4 Effects of Overlapping Images on Image Flipping in 14:20 Autostereoscopic Displays H. Ujike^{*,*2}, S. Uehara^{*,*3}, G. Hamagishi^{*,*4}, K. Taira^{*,*3}, T. Koike^{*,*5}, C. Kato^{*,*5}, T. Nomura^{*,*6}, T. Horikoshi^{*,*7}, K. Mashitani^{*,*8}, A. Yuuki^{*,*9}, K. Izumi^{*,*10}, Y. Hisatake^{*,*11}, N. Watanabe^{*}, Y. Nakano^{*,*12} ^{*}Japanese Ergonomics Nat. Committee, Japan *2AIST, Japan ^{*3}Toshiba, Japan *4Sonv Mobile Display, Japan ^{*5}Hitachi, Japan *6Sharp, Japan *7NTT DoCoMo, Japan *8Sanyo Elec., Japan *9 Mitsubishi Elec., Japan *103D Consortium, Japan *11 Toshiba Mobile Display, Japan *12 YOSH Consultancy, Japan

The factors affecting image flipping along different views in multiview autosrereoscopic displays were experimentally investigated. Our results indicated that (i) overlapping images reduce image flipping and also image sharpness, (ii) those effects of overlapping images weaken with larger number of views per IOD.

----- Break -----

15:00 - 16:20

Room 502

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3D6: 3D Display (2)

Chair: T. Fujii, Tokyo Inst. of Tech., Japan

Co-Chair: T. Koike, Hitachi, Japan

3D6 - 1: Invited Advantages of 3D Displays in Mobile Devices 15:00 T. Horikoshi

NTT DoCoMo, Japan

Small portable displays offer several advantages over large 3D-TVs. This paper describes the mobile environment, and shows that portable displays well suit the realization of multi-view 3D service. A head tracking system is also introduced that can effectively widen the stereoscopic viewing space of portable 3D displays.

3D6 - 2 3D Viewing Experience in Mobile Contexts 15:20 M Columna T, Jäurna F, M Differ

M. Salmimaa, T. Jävenpää, M. Pölöen Nokia Res. Ctr., Finland

User opinions on viewing angles and display size of handheld (auto) stereoscopic display in different contexts were studied. The optical characteristics of the display were determined. Results indicated that users preferred larger displays, especially with longer viewing durations. The viewing freedom was thought to be appropriate for all the contexts.

3D6 - 3Effects of an Extra Diffuser between VZFO and15:40Display Panel in a Multiview 3-D Imaging Systems

J.-Y. Son, Y. Vaspanov^{*}, M.-C. Park^{**}, H. Lee, S. Yeon

Daegu Univ., Korea ^{*}Hanyang Univ., Korea ^{**}Korea Inst. of S&T, Korea

The crosstalk value changes by diffusers between VZFO and image display panel are measured in the multiview 3-D imaging geometry. The experiment informs that most diffusers can decrease moirés appearing in the system but increase crosstalk, however, a certain diffuser can be used to reduce moirés without the crosstalk problem.

3D6 - 4Multi-View Image Capture for Glasses Free Multi-16:00view 3D Displays

S. Gurbuz, S. Yano^{*}, S. Iwasawa, H. Ando NICT, Japan ^{*}NHK, Japan

In this paper, we provide an overview of our multi-view image capture system. More specifically, we propose scene content based novel image alignment method for multi-camera image capture systems that are necessary to achieve good 3D image quality.

Author Interviews 16:20 – 17:20

Workshop on Applied Vision and Human Factors

Wednesday, December 1

13:20 - 14	50 Room 412
	VHF1: Lightness Perception
Chair: Co-Chair:	Y. Shimodaira, Shizuoka Univ., Japan T. Matsumoto, Sony, Japan
VHF1 - 1 13:20	Border Detection between Two Stimuli in Various Surround Luminance Conditions
	T. Ishikawa, T. Suzuki, T. Suzuki,T. Kawai [*] , O. Koyama [*] , T. Eda ^{**} , M. Ayama
	Utsunomiya Univ., Japan *Canon, Japan **Int. Univ. of Health & Welfare. Japan

Border detection between two stimuli was investigated over a wide range of reference luminance conditions for various surround luminance levels. Results indicated that luminance contrasts for border detection exhibit a U-shaped curve against the reference luminance, and are discussed in relation to physiological properties of human visual system.

VHF1 - 2Informational Representation for Image Quality13:40Degradation Activating Accommodation Mechanism
in Subjective Evaluation Process

T. Matsui

Gunma Univ., Japan

We measure accommodative responses to three kinds of compound drifting waves composed of drifting sine, square and missing fundamental square waves with an infrared optometer, and clarify which information representation (accommodative cue) for image degradation, i.e., spatial frequency structures or spatial features, activates the accommodation mechanism in subjective evaluation process.

VHF1 - 3 Impact of Ambient Illumination Levels and Viewing 14:00 Angles to Perceptual Contrast Ratio of Display

W. Lv, H. Xu, M. R. Luo^{*} Zhejiang Univ., China ^{*}Univ. of Leeds, UK

A visual experiment was performed to find the just noticeable difference (JND) of lightness under different viewing conditions on an LCD display. The impact of ambient illumination and viewing angles to the perceptual contrast ratio was revealed. The present results can be used to verify and develop perceptual contrast models.

VHF1 - 4LPurity Discrimination for Spectrally Mixed Light in
the Mesopic Condition

Y. Ikegaya, G. Ohashi, Y. Shimodaira, Y. Shibata^{*}, H. Serizawa^{*} Univ. of Shizuoka, Japan

*Koito Manufacturing, Japan

Purity discrimination on monochromatic light and mixed light was studied in the mesopic condition. With correction on luminance ratio of pure color light of dominant wavelength to white light for colored light, thresholds of purity discrimination for monochromatic light and mixed light can be expressed in a unified manner.

VHF1 - 5LInfluence of Multi-colored Unevenness on White14:35Uniformity Evaluation of an LED Backlight

K. Nagamine, S. Tomioka, Y. Masakura^{**}, T. Tamura^{*}, Y. Shimpuku

Sony, Japan *Tokyo Polytechnic Univ., Japan **Tokyo Univ. of Tech., Japan

We analyzed the relationship between viewer perception of the degree of the white uniformity of an LED backlight and photometric data measured by a 2D colorimeter and found that multi-colored uneven evaluation stimuli had a stronger influence on the results than similarly colored uneven stimuli.

----- Break -----

15:00 - 16:	20 Room 412	2	
VHF2: Color Perception			
Chair: Co-Chair:	T. Matsumoto, Sony, Japan K. Masaoka, NHK, Japan		
VHF2 - 1 15:00	Artificial Hue Adaptation: Novel Technique to Help Easy Color Discrimination for Dichromatic Vision Preserving Color Saturation		
	S. Ohtsuka, S. Suzuki, S. Oishi, S. Oka, S. Fukumoto Kagoshima Univ., Japan		

A novel technique for helping color vision deficiency is proposed. The features of this technique are, (a) utilization of a pair of original and hue-rotated color images, and (b) paired images enable color vision deficiency observers to distinguish between both B-Y and R-G opponent colors by alternating these images arbitrarily.

VHF2 - 2 KANSEI Evaluation of Color Images Corrected for 15:20 Color Anomalies Assessed by Deuteranomalous and Normal Observers

Y.-C. Chen, I. Takahashi^{**}, Y. Guan, T. Ishikawa, H. Eto^{*}, T. Nakatsue^{*}, J. Chao^{**}, M. Ayama Utsunomiya Univ., Japan

*Sony, Japan *Chuo Univ., Japan

To investigate effectiveness of 'color-weak correction' to the KANSEI evaluation for color deficient observers, test images corrected with 5 levels of color-weakness were assessed by normal and anomalous trichromat. In some images, corrected image showed the best performance for deuteranomalous indicating the effectiveness of color-weak correction.

VHF2 - 3Skin-Color Palette Applying to Visual Assessment15:40and Color Measurement of FPD

S.-H. Chen, H.-S. Chen, Y.-H. Chao, M. R. Luo*

Nat. Taiwan Univ. of S&T, Taiwan ^{*}Univ. of Leeds, UK

Visual assessment and physical color measurement methods have been widely used for evaluating color quality of Flat Panel Displays. In this study, a color selection method is proposed including a skin-color palette surrounding a reference image. The method is useful to analyze skin color quality on displays.

VHF2 - 4 Low Color Gamut Application in Netbook and 16:00 E-Book

H. Zhang, L. Mao, J. Chen, S. Zhang, Y.-W. Chiu, T.-C. Chung, T.-S. Jen InfoVision Optoelect., China

A new concept of integrating low color gamut of the color filter (CF) with color engine (CE) technology to improve the performance of the TFT LCD has been developed in this paper. An 11.6-in. module was fabricated for evaluation. By using the photo resistance with special specifications, it could achieve 33% NTSC standard with all the thickness of R, G, and B photo resistance equal to 1.39 μ m, and Transmittance increase 23%. The insufficiency of chromaticity issue can be suppressed by color engine technology.

----- Break -----

16:40 - 18:10

VHF3: Color Reproduction

Chair: K. Masaoka, NHK, Japan Co-Chair: T. Kurita, NICT, Japan VHF

Room 412
VHF3 - 1: Invited High-Fidelity, Wide-Gamut, High-Functionality 16:40 Color Imaging Technology: Natural Vision and Its Future

M. Yamaguchi Tokyo Inst. of Tech., Japan

This paper reports the image and video technology that breaks through the limitation of RGB-based color, called Natural Vision, which incorporates the multispectral and multiprimary color imaging technologies for high-fidelity, wide-gamut, high-functionality color imaging and display.

VHF3 - 2 Is CIE Matching Mandatory for Color Accuracy 17:10 Using Filter Based Colorimeters?

P. Boher, T. Leroux, V. C. Patton ELDIM, France

We demonstrate that CIE matching is mandatory to achieve good color accuracy using a color filter system. When tristimulus calibration is applied, CIE matching ensures excellent color stability even if spectral fluctuations take place. In addition, small deviations from the CIE curves can be measured and used to improve color accuracy during the measurements.

VHF3 - 3 Development of High-Reproduction Color Index and 17:30 Evaluation of Viewing Angle

T. Matsumoto, S. Haga, T. Nakatsue, H. Eto, Y. Akiyama Sony, Japan

We developed a High-reproduction Color index (HR) to evaluate the accuracy of color reproduction on TV and report viewing angle measurement by using HR scores, which can evaluate color reproduction performance not only by color shifts caused by off-center viewing angles but also by the color reproduction in front view.

VHF3 - 4 Accurate Estimation Method of XYZ for Colors of 17:50 Images on an LCD

K. Ono, Y. Simodaira

Shizuoka Univ., Japan

An accurate estimation of tri-stimulus value of XYZ for colors of images displayed on an LCD is proposed even if it doesn't satisfy the additive color mixture. The method enables us to estimate XYZ with the average color difference of less than unity.

Author Interviews 18:00 - 19:00

Thursday, December 2

9:00 - 12:00 Poster/A.I. Room

Poster VHFp: Applied Vision and Human Factors

VHFp - 1 Boys and Girls Perceived Subjective Color Reproduction in Global LCD Brands

W. Mphepö^{*,**}, M. Wang^{**}, J. Zhou^{**}, D. Gao^{**}, Z. Tang^{**} ^{*}Nat. Chiao Tung Univ., Sweden ^{**}Beijing 2nd High School Attached to Beijing Normal Univ., China

What is the highest average subjective color reproduction capability users in the largest market today can expect to get from some of the major brands like Apple, Toshiba, HP, Sony, IBM/Lenovo etc? The answer is no where near 100% and some barely break 50% in important demographics.

VHFp - 2 Relationship of Legibility, Border Contrast in Colors and Visual Fatigue

H.-Y. Hsiao, H.-S. Chen Nat. Taiwan Univ. of S&T, Taiwan

4 experiments were designed on LCD monitors to explore the relationships of legibility, border contrast and visual fatigue. The result hints adjacent color pairs in the combinations aren't recommended. And using the stronger border contrast aren't suggested, which may make text reading not smoothly, and bring visual fatigue easily.

VHFp - 3 Psychophysical Analysis of Paint Colors for Wide Color Gamut Display

J. W. Jang, J. J. Yoo, H. Hong, H.-H. Shin LG Display, Korea

A series of physical measurements and psychophysical experiments using commercially available 1279 paint samples was performed in order to visually confirm the necessity of wide-gamut displays. Through the physical measurements, 3.8% of the samples were located out of BT.709 gamut. It was also 2.2% of the samples were visually perceivable.

VHF

VHFp - 4 Measuring Method of Viewing Angle Range Using Color Difference

Y. Fukai, K. Arata, N. Komine, T. Li, T. Arai, T. Igarashi, Y. Sano Toyo Univ., Japan

We propose measuring method of viewing angle range using color difference. As a result of evaluation of image quality factors such as maximum luminance, gamma value and others as well as conventional contrast ratio, correlation of the color difference with subjective evaluation turned out to be the highest.

VHFp - 5 Color Differences Formulae for High Dynamic Range Projectors

P.-L. Sun, C.-P. Chueh, H.-S. Chen Nat. Taiwan Univ. of S&T, Taiwan

CIE color-difference formula CIEDE2000 is important for image quality assessment but it does not take background luminance level, dynamic range, simultaneous contrast and crispening effect into account. The study presents a color difference formula to deal with these factors for assessing color fidelity of high dynamic range projectors.

VHFp - 6 Visually and Quantitatively Evaluating Rendering Image Performance for Vertical Stripe RGB Pixel with Various Repeated Units on the LCD

Y.-C. Wang, C.-R. Sheu Nat. Cheng Kung Univ., Taiwan

We demonstrate the evaluation of rendering image performance with respect to visual perception and numerical comparisons. Using FFT analysis, it is easily observed the difference with various units. Three typical repeated units with vertical stripe RGB sub-pixel are studied in this paper, which are Stripe, Mosaic and Pentile1 repeated units.

VHFp - 7 Contrast Ratio Analysis for Back-Lit Dimming LCD

S.-Y. Pan, K.-C. Chang, C.-W. Chen, K.-S. Wang AU Optronics, Taiwan

CR value will affect image quality, but may not be said that it is better for human perception with higher CR. The CR is dependent on measurement methods. This paper will discuss the effectiveness of different CR measurement methods. And provide some comments on human perception sensitivity for CR index.

VHFp - 8 Spot Mura Quantification Analysis for LED Edge-Lit Display

H.-S. Ruan, S.-Y. Pan, C.-W. Chen, K.-S. Wang AU Optronics, Taiwan

We use CCD camera system instead of human inspectors' eyes to judge the Spot Mura level for Edge-lit LED Backlight and furthermore more objectively obtain an appreciate value. Therefore we develop a suitable analysis algorithm to quantify it by connecting CCD camera system measurement values with human inspectors' experience.

VHFp - 9 Robustness of Image Quality Factors in Different Environment Illumination

S. Mori, G. Ohashi, Y. Shimodaira Shizuoka Univ., Japan

The purpose of this study is to examine the robustness of image quality factors in various environment illuminations using the parameter design in the field of quality engineering. Experimental results showed that image quality factors are or are not liable to be influenced by various environment illuminations.

VHFp - 10 Measurement of Cerebral Blood Flow Volume While Viewing 2D and 3D Images

H. Isono

Nippon Inst. of Tech., Japan

We measured cerebral blood flow volume while subjects viewed a 3D image immediately after viewing a 2D image. The results indicated that cerebral blood flow volume in the occipital lobe of the cerebrum is larger and there is greater brain activity while viewing 3D images than while viewing 2D images.

VHFp - 11 Effects of Image Quality Attributes on Stereoscopic 3D TV

K. T. Kim, Y.-H. Kim, Y. G. Lee, Y. J. Kang, H. E. Kim, G. H. Kim, C.-W. Kim Inha Univ., Korea

In this paper, human visual experiments are performed to verify effects of five image attributes on the stereoscopic 3D LCD TVs. Experimental results indicate that degree of cross talk is one of the most important factors affecting the image quality on the stereoscopic 3D LCD TVs.

VHFp - 12L Accurate Color Conversion for Multi-primary Displays with Three-primary Color Conversion and Linear Programming

M. Takaya, T. Mori, Y. Shimodaira^{*} Numazu Nat. College of Tech., Japan ^{*}Shizuoka Univ., Japan

We propose a method to improve the accuracy of multi-primary-color conversion, which is based on linear programming. Existing accurate conversion methods for three-primaries and linear programming were combined to reduce color difference caused by color-tracking. The accuracy of the proposed method was 30 times higher than that of linear programming.

VHFp - 13L Color Conversion Method for Multi-Primary Display to Reduce False Contours

T. Mori, M. Takaya, Y. Amano^{*}, Y. Shimodaira^{*} Numazu Nat. College of Tech., Japan ^{*}Shizuoka Univ., Japan

This paper proposes a color conversion method for a multi-primary display to reduce false contours. Color conversion was adapted to mathematical programming. The color signals were obtained by SUMT and Newton's method. As a result, false contours have been reduced with a small color difference.

VHFp - 14L Research on Acquiring Color Signal for High Fidelity Color Camera

Y. Kandori, Y. Shimodaira Shizuoka Univ., Japan

On a prototype camera intending to satisfy Luther condition, color acquisition accuracy of less than unity is achieved when it adopts a color conversion matrix of 3x4 with an invariable term under light sources of D65, Cool White, Horizon, TL84 and A.

----- Lunch -----

Room 412 VHF4/DES1: Multi Primary (1) Chair: K. Sekiya, Tohoku Univ., Japan Co-Chair: T. Matsumoto, Sony, Japan VHF4/ Invited Measuring Light and Color: An Introductory

DES1 - 1: Talk to Colorimetry

13:20

N. Ohta

Rochester Inst. of Tech., USA

Colorimetry is quantifying colors, that is, an art of expressing colors by numbers. There are two classes of quantification: color appearance system and color mixing system. The gist of the two methods will be introduced.

VHF4/A New Evaluation Method of Color ReproductiveDES1 - 2Performance and Evaluation of Multi-Primary Color13:50Display

M. Teragawa, T. Kanda, T. Fujine, M. Sugino, Y. Miyanaga^{*} Sharp, Japan ^{*}Hokkaido Univ., Japan

This paper proposed new evaluation of color reproductive performance, and evaluated MPC display. We used coverage ratio against object color for evaluation of outer frame structure, and CDI for evaluation of inner structure. We clarified MPC display was suitable for expressing object colors and had advantage of smooth color reproduction.

VHF4/Color Reproduction of Multi-Primary Color Display:DES1 - 3Numerical Analysis Method and Application to14:10Lower Power Consumption

T. Fujine, M. Teragawa, N. Ohta^{*} Sharp, Japan ^{*}Rochester Inst. of Tech., USA

We analyze color reproduction of multi primary color (MPC) display, and propose to calculate primary amount of color mixing for MPC in minimum power consumption by linear programming. As an example, we analyze characteristics of RGB+Y four primary color system in comparison with RGB system.

VHF4/ DES1 - 4 14:30	A Numerical Evaluation across Multi-Primary Color Systems
	A. Yoshida, K. Yoshiyama, K. Tomizawa, K. Nakamura, Y. Yoshida, M. Teragawa, Y. Yamamoto*, N. Ohta**
	Sharp, Japan

*CIS Labs., Japan **Rochester Inst. of Tech., USA

We conducted a numerical analysis over several Multi-Primary Color (MPC) display systems consisting of RGB + Cyan primaries. We compared the results with our previous results (RGB + Yellow and RGB + White) for indicating characteristics of different MPC systems in terms of luminance reproduction and power consumption.

----- Break -----

Room 412

VHF5/DES2: Multi Primary (2)

Chair: N. Ohta, Rochester Inst. of Tech., USA Co-Chair: T. Matsumoto, Sony, Japan

VHF5/ Invited Four Primary Color (RGB+Y) Displays: The DES2 - 1: Latest Technologies and Advantages 15:00 M. Tara agure

M. Teragawa Sharp, Japan

This paper reviews the latest RGB+Y four primary color LCD technologies and the advantages. RGB+Y LCD has advantages for not only color reproducibility but also power consumption, in addition, higher resolution. RGB+Y LCD along with UV2A can make LCD-TV improved in all ways.

VHF5/ High Resolution Reproducibility of Multi-Primary DES2 - 2 Color Displays

15:40 K. Yoshiyama, H. Furukawa, N. Kondoh, S. Nakagawa, Y. Yoshida

Sharp, Japan

In this paper, we focus on high resolution characteristic of Multi-Primary Color (MPC) display, and show that horizontal resolution can be approximately twice for stripe-patterned four-primary color display by the combination with advanced sub pixel signal processing.

VHF5/Advanced RGBW Display Image Process UsingDES2 - 3Sub-pixel Rendering16:00M.-C. A. Kao, P.-L. Hsieh, H.-T. Lin

Chunghwa Picture Tubes, Taiwan

A novel image process has been developed to transform RGB into RGBW. It comprise the "RGBW mapping algorithm" is used to adjust color of image. And the "Virtual resolution scaling" is used to increase the apparent resolution. And the "W signal controlling" is used to increase sunlight readability.

----- Break -----

16:40 - 18:00

Room 412

VHF6: Moving Image Quality and Backlight System

- Chair: T. Kurita, NICT, Japan Co-Chair: K. Masaoka, NHK, Japan
- VHF6 1 Image Quality for Motion Pictures by Using Eye-16:40 Tracking Technology

Y.-Y. Chang, H.-S. Chen, R. M. Luo*

Nat. Taiwan Univ. of S&T, Taiwan ^{*}Univ. of Leeds, UK

The purpose of this study is to find the relation between the psychophysical quantities (i.e., colorfulness, naturalness, visual comfort, preference, shadow / highlight detail) and image quality for motion pictures. Eye-tracking technology is introduced to collect the gazing areas which are attractive to the observers.

VHF6 - 2 Investigation of Color Breakup Measurement 17:00 Method Using a Moving Camera System

Y.-Y. Lai, K.-N. Wu, M.-L. Tai*

ITRI, Taiwan *Chunghwa Picture Tubes, Taiwan

Field-sequential display is an eco-friendly production but color-breakup (CBU) is the significant problem. A novel CBU detects and analysis technique using the moving camera and the image processing method had proposed to evaluate the degree of CBU. This method could present a useful index to recognize the CBU phenomenon.

VHF6 - 3Study and Experiment of Color Breakup in a 6-in.17:20Color Sequential Display

C.-C. Tsai, S.-H. Yu, Y.-H. Cheng, W.-C. Tai Chunghwa Picture Tubes, Taiwan

A 6-in. Color Sequential Display prototype has been developed. Some solutions of reducing color breakup has been discussed and experimented on the provided prototype. Color breakup has been roughly specified into static one and dynamic one. The proposed combination driving method can effectively reduce the color breakup.

VHF6 - 4Effect of Backlight Dimming Methods on the17:40Perceived Contrast of Complex Images

H.-I. Baek, J.-W. Kwon, S.-H. Kim, M.-J. Lim, H.-H. Shin LG Display, Korea

Effect of different backlight dimming methods on the perceived contrast of complex images on the LCDs was subjectively compared and a good dependency on the image types was found. In some extreme cases, several times higher native contrast ratio was found to be required to compensate the perceived contrast difference.

Author Interviews

18:00 - 19:00

Friday, December 3

9:00 - 10:15	Room 502
	VHF7: Display Human Factors
Chair: Co-Chair:	T. Wake, Kanagawa Univ., Japan S. Clippingdale, NHK, Japan
VHF7 - 1 9:00	Sociological Factors and LCD Subjective Image Quality (SIQ) W. Mphepö ^{*,**} , J. Bingrui ^{**} , L. Mi ^{**} , W. Yimeng ^{**} [*] Nat. Chiao Tung Univ., Sweden ^{**} Beijing 2nd High School Attached to Beijing Normal Univ., China

Do sociological factors - cultural & ethnic background, gender, age, education level etc. have impacts on LCD Subjective Image Quality [SIQ] perception? Experiment with 750 Chinese and Korean individuals reveal sociological impacts of 40% or higher. And last but not least, Apple displays are not always best.

9:40

VHF7 - 2 Secure Display with Head-Tracking Viewing Zone 9:20

H. Yamamoto, K. Kajimoto, S. Suyama Univ. of Tokushima, Japan

We propose a new type of secure display that employs face-detection with a camera. Optical encryption prevents eavesdropping of display signal and limits the viewing zone three-dimensionally. The viewing zone is moved to track the viewer's face. The experimental results shows the effectiveness of the proposed head-tracking secure display.

VHF7 - 3 Visual Cryptography on Color Video Displays

C.-H. Wen

Nat. Taiwan Univ. of S&T, Taiwan

Visual cryptography can encrypt the visual information by computer and decrypt the information via human eyes. This paper proposed a new scheme and decrypted the secret image by the way of video sequence. By showing the encrypted images frame-by-frame in front of visual display terminal, the decrypted information is noticeable.

VHF7 - 4L New HMI Solutions for Automotive Night Vision 10:00 Systems

P. Knoll

Karlsruhe Inst. of Tech., Germany

First and second generation Night Vision Enhancement Systems with image presentation in the dashboard present a Camera-picture in the dashboard, in the center console area or on the windscreen. Results of ergonomic investigations with different HMI solutions are presented. Conclusions for a possible third generation are made.

----- Break -----

10:40 - 12	2:10 Room 5	02
	VHF8/3D4: 3D Human Factors	
Chair: Co-Chair:	S. Clippingdale, NHK, Japan H. Yamamoto, Univ. of Tokushima, Japan	
VHF8/ 3D4 - 1:	Invited Safety in 3D Broadcast, and Study in 3D Channel Starting Service	
10:40	Y. Imai, K. Imanishi, T. Okunaga	
	SKY Perfect JSAT, Japan	

SKY Perfect TV started broadcasting 3D channel from June 2010 and carried out the test shooting and the examination for a safe and easy-to-watch 3D broadcast. We studied the cause of fatigue and discomfort in watching 3D image by using images of soccer game and that of a woman.

VHF8/	Evaluation of Viewability to Hyper-Realistic Picture
3D4 - 2	N. Suzuki [*] , S. Yano ^{*,**}
11:10	[*] NICT, Japan
	**NHK, Japan

This paper provides a subjective and objective evaluation of the viewability of hyper-realistic images. First, we examined the preferable viewing distance for images of different sizes, including monoscopic and stereoscopic images. Second, we measured the eye movements of participants in a previous experiment comparing preferable with non-preferable viewing distance.

VHF8/Measurement of Accommodation and Vergence3D4 - 3Responses while Viewing Two-View and Multi-View11:303D Displays

H. Mizushina, I. Negishi, H. Ando^{*}, S. Masaki Advanced TeleCommun. Res. Inst. Int., Japan ^{*}NICT, Japan

We measured accommodation and vergence responses simultaneously while viewing two-view 3D display based on polarized glasses and multi-view 3D display based on parallax barrier. Difference between two-view and multi-view conditions was observed in the vergence response, but not in the accommodation response.

VHF8/Influence of Luminance Gradient on Three3D4 - 4Dimensional Perception for Real Object and Digital11:50Image

K. Iwauchi^{*,**}, T. Takahashi^{**}, T. Eda^{**}, T. Ishikawa^{**}, M. Ayama^{**}

^{*}Sharp, Japan ^{**}Utsunomiya Univ., Japan

We investigated 3D perception using real objects and digital images. The results indicate that the absolute luminance value of the brightest area and the luminance gradient are the two most important factors for 3D perception of real objects, whereas a degree of gradient enhancement is needed for digital images.

Author Interviews

16:20 - 17:20

Supporting Organizations:

Technical Group on Information Display, ITE Technical Committee on Electronic Information Displays, Electronics Society, IEICE

Workshop on Projection and Large-Area Displays and Their Components

Wednesday, December 1

13:20 - 16:20

Poster/A.I. Room

Poster PRJp: Projection

PRJp - 1 A LCoS Microdisplay with Low Voltage Driving

G.-J. Lee, J.-H. Kim, K.-J. Yang, H.-K. Lyu, Y.-H. Lee^{*}, H.-J. Chung^{*}, B.-D. Choi

Daegu Gyeongbuk Inst. of S&T, Korea ^{*}Kumoh Nat. Inst. of Tech., Korea

A 0.28-in. SVGA LCoS panel with low power consumption was proposed for portable applications. For low operation voltage, a transmission gate was used for pixel switch in the proposed pixel structure so that any video signal within the power supply range can be stored in pixel capacitor.

15:00 - 16:25		Room 402
	PRJ1: Illumination Systems	
Chair: Co-Chair:	K. Li, Wavien, USA H. Nakano, Barco, Japan	

PRJ1 - 1:InvitedFull HD 3D Projector with Dual Engine and15:00Single Projection Lens

S.-G. Lee, S.-O. Yeo, W.-W. Park, S.-Y. Park, S.-H. Park, J.-W. Kim, J.-K. Lee, S.-H. Kim

LG Elect., Korea

The full HD 3D projector using passive polarization glasses has been developed to give a brighter 3D image on screen for the user. The dual engine and single projection lens system, the MHCM technology and digital processing & auto calibration technology provide a high quality 3D image for the user.

PRJ1 - 2Development of a High Brightness Dual-Lamp15:25Projector

A. Yamada, K. Kojima, H. Kida, K. Samejima, J. Someya, H. Sugiura

Mitsubishi Elec., Japan

A projector has been developed that can display distinct pictures even in spacious and bright places. Two lamps are provided in a unique optical system to assure the brightness of 7,000 lumens and the high contrast ratio of 2,000 to 1, which are both the highest in the class.

PR

PRJ1 - 3Increased LED Brightness with Recycling for15:45Projection Applications

K. Li

Wavien, USA

This paper describes different approaches using LED recycling to increase the outputs at with separate recycled RGB LEDs for high power, recycled white LEDs for medium power, and single packaged RGB LEDs with recycling for low power. Gain ranges from 50% to over 100% have been achieved.

PRJ1 - 4L Long Life Dual Paraboloid Reflector Lamp 16:05 Optimized for 3LCD and LCOS Projection Systems

K. Li

Wavien, USA

Dual Paraboloid Reflector (DPR) has been demonstrated to extend lifetime of lamps by a factor of up to 5X. The DPR lamps have also been used with tapered light pipes suitable for DLP projectors. In this paper, a DPR system designed for used with 3LCD and LCOS system is shown.

Author Interviews

18:00 - 19:00

Thursday, December 2

9:00 - 10:20		Room 409
	PRJ2: New Projection Applications	
Chair: Co-Chair:	B. Schowengerdt, Univ. of Washington, USA H. Kikuchi, NHK, Japan	ι.
PRJ2 - 1 9:00	Monolithic Low Cost Plastic Light Guide Colour See-Through Personal Video Glas	for Full sses
	K. Sarayeddine, P. Benoit, G. Dubroca, X. H Optinvent, France	ugel

Low cost see-through personal video glasses technology for consumer market was developed. Monolithic transparent plastic light guide with an array of small surface mirrors enables a bright image with a field of view of 27 degrees in an esthetic form factor.

PRJ2 - 2 Projection Displays in Avionics

9:20

D. Cuypers, H. D. Smet^{*}, X. Hugel^{**}, G. Dubroca^{**}, A. V. Calster^{*}

imec, Belgium ^{*}Ghent Univ., Belgium ^{**}Optinvent, France

Avionics represents a specialized area of display applications. A possible future development in this field is a single display cockpit environment with touch input capabilities. Such a seamless, tiled cockpit display based on short throw wide angle projectors is developed in the European Project ODICIS. The current results are discussed in this contribution.

PRJ2 - 3Roll to Roll Patterned Film for Effective Low9:40Luminance Pico Projection Display Applications

W. Mphepö^{*,**,***}, Z. Yiyi^{***}, Y. Wei^{***}, W. Yan^{***}, Q. J. Feng^{***}

*Nat. Chiao Tung Univ., Taiwan **Chalmers Univ. of Tech., Sweden ***Beijing 2nd High School Attached to Beijing Normal Univ., China

Tinted vehicle windows are for different uses among which are providing privacy, reducing transmitted sun light in hot climates and for aesthetics. The herein reported work was geared towards retaining these traditional aspects of tinted vehicle windows while adding a new display aspect component for custom display applications.

PRJ2 - 4L A New Light Control System for 3LCD Projectors 10:00 Enabling Contrast Improvement with Enhancing Energy Saving

H. Horiguchi, H. Yoshimoto, T. Yamada, K. Fukuhara, L. Schreel^{*}, J.-J. van den Bergh^{*}, B. Dilles^{*}, S. Sonoda^{*}

Seiko Epson, Japan *Philips Innovative Applications N.V., Belgium

We developed a new light control system for 3LCD projectors. This system continually optimizes both the lamp brightness according to the image and the white balance deviations that occur due to lamp power changes. The system enhances contrast ratio by approximately five times and also realizes reduction of energy consumption.

----- Break -----

Room 409

10:40 - 11:55

PRJ3: Pico-Projectors

Chair:	M. Niesten, Microvision, USA
Co-Chair:	T. Hayashi, 3M APAC, Japan

PRJ3 - 1: *Invited* 1 mm x 7 mm Full-Color Pico Projector Using 10:40 Scanning Optical Fiber

B. T. Schowengerdt, R. S. Johnston, C. M. Lee, C. D. Melville, E. J. Seibel

Univ. of Washington, USA

We have developed a 1-mm x 7-mm light scanning engine, projecting full-color images through a vibrating optical fiber tip and miniature lens system. The projection head and RGB light sources can be separated and tethered together by any desired length of optical fiber, enabling flexible device configurations.

PRJ3 - 2: *Invited* Pico Projector with Anamorphic Illumination 11:05 System

C.-K. Liu, C.-C. Liao, K. Wang, Y.-J. Chen^{*} Coretronic, Taiwan ^{*}Nat, Central Univ., Taiwan

The development of a RGB LED projection engine with anamorphic illumination system is reported in this paper. Projector equipped with this engine could produce more than 50 lumens with WVGA resolution. The volume of optical engine and projector are 108 cc and 252 cc, respectively.

PRJ3 - 3: Invited Scanning Laser Beam Pico Projector

11:30 M. Niesten, T. Masood, J. Miller, S. Shinzawa Microvision, USA

The smallest high resolution projector engine to date has been developed for high volume manufacturing. This projector has a 720 resolution at a height of 7 mm and a volume of 5 cc. Future scanning laser beam projectors will be even smaller.

PRJ3 - 4 Withdrawn

----- Lunch -----

14:50 - 16:25

Room 409

PRJ4: Laser Projection and Despeckling Technologies

Chair:	H. Kanayama, Sanyo Elec., Japan
Co-Chair:	T. Suzuki, JVC KENWOOD Holdings, Japan

PRJ4 - 1: *Invited* The Evolution and Trends of Laser Projection 14:50 Displays

S. Shikama

Setsunan Univ., Japan

The laser was first demonstrated just half-century ago (1960). Research and development of laser projection displays had been reported from the early stage of the laser history. In this paper, evolution and trends of laser projection displays are presented including the key issues; optical systems and components, speckle noise reduction.

PRJ4 - 2: *Invited* Development of Wide Scan Angle and High-15:15 Speed Optical Scanning Devices

J.-H. Park, J. Akedo AIST, Japan

Metal-based optical MEMS scanning devices employed an AISToriginal MEMS driving method, Lamb wave resonance piezoelectric driving method. It achieved large optical scan angles of 100° or greater at high scanning speeds (over 25 kHz) and low driving voltages (20 V), those are required to be used in practical projection displays.

PRJ4 - 3: Invited A Despeckler Based on a Single FLC Cell

15:40 I. Kompanets, A. Andreev Lebedev Physical Inst., Russia

The speckle-noise in images displayed by the laser projection system is suppressed in real time when a laser beam passes through a single FLC cell where spatially inhomogeneous phase light modulation takes place due to special FLC material and electric pulse regime.

PRJ4 - 4Despeckling Method with Variable Speckle16:05Generator Utilizing Photopolymer Film

K. Ishida, M. Kurashige, T. Takanokura, Y. Ohyagi, M. Watanabe

Dai Nippon Printing, Japan

Removing laser speckle which generates on a screen is important in laser projection. In this paper, different speckle patterns are superimposed continuously by giving small movement or changing direction of light to volume phase holographic beam shaper utilizing photopolymer film, which makes speckle invisible. Speckle contrast of 0.03 is achieved.

----- Break -----

16:35 - 18:00

Room 409

PRJ5: Digital Signage and Large Venue Projectors

Chair: M. D. Perkins, Christie Digital Syss. Canada, Canada Co-Chair: S. Shikama, Setsunan Univ., Japan

PRJ5 - 1: *Invited* Micro Tiles - An Expandable Flexible Tiled 16:35 Display System

M. D. Perkins

Christie Digital Syss. Canada, Canada

MicroTiles is a video display system that can be used to create large displays out of an array of small, modular units. The architecture is described along with how it meets the needs of Digital Out-Of-Home applications. Primary goals of this system are flexibility, resolution, and ease of installation.

PRJ5 - 2 Multiple Directional Viewing Projection Display 17:00 Based on the Incident-Angle-Independent Diffusion Angle Quantizing Technology Angle Quantizing Technology

T. Kawakami, B. Katagiri, T. Ishinabe, T. Uchida*

Tohoku Univ., Japan ^{*}Sendai Nat. College of Tech., Japan

We have devised an incident-angle-independent, quantized-diffusionangle screen and have realized a multiple directional viewing projection display system using double-side lenticular lens. Our display system has advantages of easy alignment for multiple projectors, and capability of multiple different images simultaneously according to viewing angle at any distance from the screen.

PRJ5 - 3High Resolution Projection Systems with High17:20Dynamic Range Capabilities

B. Maximus, P. Candry, H. Nakano^{*} Barco Simulation, Belgium ^{*}Barco Tokyo, Japan

This paper focuses on an important aspect of the development of high dynamic range capabilities on high resolution LCOS projection systems for Simulation applications, namely the bitdepth which is required from the input of the projector up to the reproduction of the image.

PRJ5 - 4 Adaptive Brightness and Color Conversion 17:40 Projection System by Color Tuning Optical Engine

M. Maeda, K. Arai, M. Haraguchi, T. Abe, S. Tanase, K. Mashitani, M. Inoue, H. Kanayama Sanvo Elec., Japan

The newly developed projection system realizes adaptive combination of high brightness and wide color gamut. This projector features a fourth liquid crystal panel, "Color Tuner", with 3LCD optical engine, which controls yellow-light separately from RGB lights of UHP lamp.

Author Interviews

18:00 - 19:00

Supporting Organizations:

Technical Group on Information Display, ITE Laser Display Technology Research Group, Optical Society of Japan

BANQUET

Wednesday, December 1, 2010 19:30 – 21:30 Crowne Grand Ball Room (2F) ANA Crowne Plaza Fukuoka See page 9 for details

EXHIBITION

12:00 – 18:00 Wednesday, Dec. 1, 2010 10:00 – 18:00 Thursday, Dec. 2, 2010 10:00 – 14:00 Friday, Dec. 3, 2010

2F Lobby, 4F Lobby Fukuoka International Congress Center

Free admission with your registration name tag

Workshop on Electronic Paper

Wednesday, December 1

13:20 - 16:20

Poster/A.I. Room

Poster EPp: Electronic Paper

EPp - 1 High Performance and Colorful Active Matrix Electrophoretic Display

C.-M. Lu, M.-C. Weng, Y.-C. Chen, H.-H. Chen, W.-T. Tseng, H.-T. Yu

Chunghwa Picture Tubes, Taiwan

CPT has successfully developed the 6-in. colorful AMEPD panel of the micro-capsule with the color filter. The colorful EPD technology is necessary because the market demand of the colorful E-book is so strong. Therefore, we present a full-color display with the color filter covered on the 6-in. AMEPD panel.

EPp - 2 Realization of Vivid Image Projection in a Bright Room Using Electronic Paper Screen

T. Kinjo, M. Omodani, T. Yoshida^{*} Tokai Univ., Japan ^{*}Freelance Profession, Japan

We have suggested a new projection system which can realize high contrast image projection in a bright room. It is consisted of electronic paper screen, LED projector and LED room light. We have confirmed that twice higher contrast than the conventional projection system is achieved by our new system in a bright room environment.

EPp - 3 Behavior of Image Sticking in Bistable Display Using Cholesteric LC

M. Fukuda, Y. Kurosaki, M. Nose, T. Watanuki Fujitsu Labs., Japan

Image sticking, which refers to the slight difference in brightness due to the previous image remaining, is a serious problem with bistable displays using cholesteric liquid crystals. Image sticking occurs after the electric field is removed, so it is greatly affected by the surface condition of the electrode.

EPp - 4 A High-Efficiency and Crosstalk-Free Pen Tracking Scheme for Passive Matrix Single-Layered Color Cholesteric LCD

Y.-S. Chang, C.-C. Hsu, C.-J. Chen, C.-C. Liang, C.-C. Wu, C.-H. Wu, C.-Y. Chen ITRI, Taiwan

A high-efficiency and crosstalk-free pen tracking scheme is proposed for high performance handwriting on low-cost passive-matrix (PM) cholesteric LCDs. With the proposed scheme, the crosstalk issue can be overcome and the handwritten paths are locally reinforced for high image quality. Furthermore, pixels are updated in-parallel for high handwriting speed.

EPp - 5 Driving Method of Choleristic LC and Its Applications

P.-H. Chiu, S.-F. Liu, S. Chen, C.-Y. Shen, H.-A. Li Chunghwa Picture Tubes, Taiwan

This paper applies less than 30 V voltage to drive cholesteric liquid crystal, and get different optical performances by different driving schemes. We could apply these characteristics to different applications, like monochrome content with quicker page turn speed, while color content with slower one.

EPp - 6 A Development of Color-Filter-Free Electrowetting Color Display by Using Ink Jet Printing Technology

S.-W. Kuo, K.-L. Lo, W.-Y. Cheng, Y.-S. Ku, H.-H. Lee, Y.-H. Tsai, P.-P. Cheng, J.-W. Shiu, C.-Y. Chen^{*}, Y.-S. Huan^{*}

ITRI, Taiwan *Nat. Chiao Tung Univ., Taiwan

We evaluated the single layer EWD device by using various colored oils without adopting color filter. The color mediums were various colored oil that dosed into sub-pixels by ink jet printing technology. Simulation was also utilized to analyze the phenomenon of unstable fluid movement.

EPp - 7L New Bistable Mode of Electrowetting Light Valve

I.-C. Hsieh, Y.-J. Li, H.-H. Huang^{*} Nat. Chung Hsing Univ., Taiwan ^{*}D & Y Intelligent, Taiwan

In this study, a new electrowetting mode is embedded in a light valve structure pixel which the surface tension is moderated on junction of water/oil system. The tested panel demonstrated that bistable behavior of the oil extraction/spread motion by different driving methods.

Ψ

EPp - 8L A 3.5-in. Transflective Color Active Matrix Electrowetting Display

C.-Y. Chen, C.-Y. Wang, S.-J. Chang, H.-Y. Chang, C.-Y. Chou, W.-T. Liao, W.-C. Wang Wintek, Taiwan

In this paper, we proposed the panel design, fabrication processes and optical performances of a 3.5-in. transflective AMEWD. Accompany with the dipping process to dose the black oil into the pixels on the COA substrate, the color AMEWD could become more simple, feasible and scalable.

EPp - 9L Novel High Contrast Bistable Reversed-TN-LCD for Electronic Paper

R. Takahashi, Y. Toko^{*}, S. Saito, T. Takahashi Graduate School of Kogakuin Univ., Japan ^{*}Stanley Elec., Japan

A reflective type of Reversed (R) TN-LCD with the bistable switching was developed. The switching between the R-TN state and the splaytwist state is done by changing the direction of applied electric field. Optimizations of cell parameters are done to achieve the high contrast reflection type of the bistable R-TN-LCD.

----- Break -----

16:40 - 18	:00 Room 204
	FLX3/EP1: Flexible Electronic Paper
Chair: Co-Chair:	Y. Masuda, Bridgestone, Japan H. Fujikake, NHK, Japan
FLX3/ EP1 - 1 16:40	Large Area and High Precision Organic TFT Array of A4 Size with 200 ppi on Plastic Substrate by Microcontact Printing Technique
	K. Yase AIST, Japan

We have succeeded in driving a high resolution polymer network liquid crystal display (PNLCD) by using OTFT array obtained by microcontact printing (μ CP) method. By optimizing the fabrication condition, 200 ppi with the pixel size of 125 μ m on A4 size plastic substrate was achieved.

FLX3/ EP1 - 2 Development of Flexible Electronic Paper with Transparent Polymer Electrodes Prepared through Directly Printing Approach 17:00 M. Nishii, Y. Iwabuchi, H. Kotsubo, R. Sakurai, Y. Masuda, R. Hattori^{*} Bridgestone, Japan *Kyushu Univ., Japan

A 4.0-in. diagonal and 88 dpi flexible electronic paper with line-shaped electrodes composed of transparent conductive polymer of PEDOT/ PSS was prepared and passive matrix images were successfully displayed. The line-shaped electrodes of the conductive polymer were directly formed onto the flexible PET substrate by using screen printing method.

FLX3/	Flexible Color Ch-LC E-Papers
EP1 - 3 17:20	SC. Chen, HY. Chen, CC. Liang, CL. Chin, CW. Chen, JY. Su
	ITRI. Taiwan

This paper proposes flexible color Ch-LC e-papers. By adding photochiral dopant, single substrate flexible Ch-LCD becomes sensitive to UV light. Therefore, UV exposure can cause the discontinuous change in the helical pitch of the Ch-LC pixels to locally colorize the e-paper. After being colorized, the color e-paper can be electrically driven to update the displayed content. In this paper, the 50 dpi color R2R Ch-LC e-paper is implemented.

FLX3/
EP1 - 4Preliminary Evaluation of LED Photo-Addressing
on ChLCD Electronic Paper17:40W.-J. Li, C.-J. Li, M.-Y. Lu, B.-W. Xiao, T.-T. Chang,
K.-J. Hu
ITRI, Taiwan

We have done a preliminary work on photo-addressing method for Chlcd electronic paper with auxiliary LED light source. The Chlcd electronic paper could be written more efficiently by controlling high luminous intensity LED appropriately. Finally we have realized the prototype of the photo-addressable electronic paper with LED light pen.

Author Interviews

18:00 - 19:00

Thursday, December 2

9:00	- 9:05
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Main Hall

Opening

Opening Remarks 9:00

A. Suzuki, Ricoh, Japan

9:05 - 10	:15							Main	Hall
	EP	2: E	ectropho	ret	ic Disp	lays	6		
Chair: Co-Chair: EP2 - 1:	T. Kita Y. Hott <i>Invited</i>	mura a, R Co	a, Chiba Univ icoh, Japan I or Quality I	/., J mp	apan proveme	nt ir	n Activ	ve Ma	trix
5.05	NS.	Roh,	T. Hwang, S	а у С. К	won, W.	Lee,	S. Kin	n, S. L	im
	Sar	nsur	ng Elect., Kol	rea					
E-Reader	using E	Ink	technology	is	limited	on	black	and	white

E-Reader using E Ink technology is limited on black and white contents, so colorization of e-paper is eagerly awaited to expand the market. In this paper, we will discuss about color of reflective display, comparing with printed paper and what is the key factor to increase the performance.

EP2 - 2:InvitedAdvanced Technology in Electrophoretic9:30Display

Y.-I. Park, S.-H. Paek, O.-N. Kwon, C.-H. Park, C.-D. Kim, Y.-K. Hwang, I.-J. Chung LG Display, Korea

We have developed and demonstrated B5-sized color flexible electrophoretic display and world largest A3-sized flexible electrophoretic display using E-ink micro-encapsulated technology. These EPD displays give us wider applications because of color image and large screen as well as flexibility and paper-like look And we also achieved large flexible electrophoretic display for its application extension to e-newspaper and digital signage.

Thursday

EP2 - 3Understanding Electrophoretic Displays: Transient9:55Current Characteristics of Dispersed Charges in a
Non-Polar Medium

Y. Jeon, P. Kornilovitch, P. Beck, Z.-L. Zhou, R. Henze, T. Koch

Hewlett-Packard, USA

Transient currents of reverse micelles in a non-polar solvent from voltage step stimuli were studied to investigate the electrophoretic behavior of the charges. It showed various time-dependent transients depending on the applied voltage and the charge content. A one-dimensional drift-diffusion model could reproduce the behaviors for various conditions.

----- Break -----

10:40 - 11:55	Main Hall
EP3: Color Electrophoretic Displays	

Chair: M. Omodani, Tokai Univ., Japan Co-Chair: M. Tsuchiya, E Ink, Japan

EP3 - 1: Invited Reflective Electronic Media with Print-Like 10:40 Color

T. Koch, J.-S. Yeo, B. Benson, J. Mabeck, R. Hoffman, V. Korthuis, Z.-L. Zhou, D. Hentz Hewlett-Packard, USA

A novel architecture and proprietary electrically addressable inks have been developed to provide print-like full color reflective digital media. The thin, flexible, low-power media is fabricated with a roll-toroll manufacturing platform, and it is integrated with a multi-component oxide (MCO) thin-film transistor backplane to produce active matrix reflective electronic display.

EP3 - 2: 11:05	Invited Zero-Energy E-Skin				
	KM. H. Lenssen, L. W. G. Stofmeel, M. H. W. M. van Delden, R. J. M. Vullers [*] , H. J. Visser [*] , V. Pop [*]				
	Philips Res. Labs., the Netherlands *imec, the Netherlands				

Bright e-Skin technology makes "green" applications possible, like ecoskin and smart windows. Another "green" aspect is the ultra-low power consumption, which enables "zero-energy" e-Skin, i.e. devices that do not need a battery or connection to an external electrical power supply. As examples, solar-powered and RF-powered e-Skin are presented.

EP3 - 3:InvitedElectro-Osmosis: The Key to In-Plane11:30Electrophoretic Displays

A. Henzen, J. Groenewold*

IRX Innovations, the Netherlands *Denkwerk, the Netherlands

Electrophoretic displays require encapsulation to prevent particle drift. Also, in-plane electrophoresis requires extreme accuracy in driving and pixel layout to provide homogeneous imaging. This new method solves both problems.

----- Lunch -----

Main Hall

EP4: Frontier Research for e-Paper

Chair: S. Maeda, Tokai Univ., Japan Co-Chair: M. Higuchi, NIMS, Japan

EP4 - 1:InvitedHuman Interface Aspects for Realizing13:20Readable Electronic Paper

M. Omodani

Tokai Univ., Japan

We must be able to obtain useful guidelines for e-Paper if we find clear answers for the primitive question why we generally prefer reading on paper than on electronic displays. Several experiments have been performed to extract essential difference between paper and displays from various aspects; readability, fatigue, and efficiency.

EP4 - 2 Novel Display Device with Dual Emissive and 13:45 Reflective Modes by Using Luminescent Lanthanide(III) Complexes and Electrochromic Materials

K. Nakamura, K. Kanazawa, N. Kobayashi Chiba Univ., Japan

A novel display device with dual emissive and reflective display mode is demonstrated. The device consists of luminescent lanthanide(III) complexes (photo- luminescence materials) and an electrochromic material. The device functions as an electrochromic device when bias voltages are applied and as a light-emitting device if excitation lights are irradiated.

EP4 - 3Novel Imaging Device with Reflective and Emissive14:05Mode Driven by Electrochemical Reaction

Y. Watanabe, K. Nakamura, N. Kobayashi Chiba Univ., Japan

We successfully demonstrated novel imaging cell with reflective and emissive mode driven by electrochromic and electrochemiluminescence reactions. This dual-mode cell has simple structure and driving feature which reflective and emissive mode can be controlled by selecting DC and AC driving method, respectively.

----- Break -----

15:00	-16:30
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Main Hall

EP5: Electrochromic Displays

Chair: N.-S. Roh, Samsung Elect., Korea Co-Chair: Y. Toko, Stanley Elec., Japan

EP5 - 1:InvitedElectrochromic Display Using Organic-15:00Metallic Hybrid Polymers

M. Higuchi^{*,**}

*NIMS., Japan **Japan S&T Agency, Japan

To achieve the next generation display that contributes to energy conservation and the saving resource, we created organic-metallic hybrid polymers as new electrochromic material in which multi-colors are expressible and fabricated solid-state electrochromic devices using them. The device properties are introduced in my presentation.

EP5 - 2:InvitedDevelopment of Color Electrochromic15:25Displays Based on Thin Film Transistor

Y. W. Jin, C. H. Noh, J. W. Kim, D. S. Chung, Y. J. Yi, S. J. Jeon, R. R. Das, M. H. Jung, S. Y. Lee Samsung Elect., Korea

We have developed active matrix color electrochromic displays(AMECD) based on a-Si TFTs backplane For the high resolution(100 ppi) and gray scalable(16 levels) display, cross-talk free structure and a unique process to deposit selectively titanium dioxide on each pixel electrode were presented.

EP5 - 3High Performance Electronic Paper Utilizing Leuco15:50Dye

W. Weng, T. Fukuoka, S. Kihara, T. Higuchi, M. Suzuki, T. Shimomura, M. Ono, M. Omodani^{*}

Funai Elec. Advanced Appl. Tech. Res. Inst., Japan ^{*}Tokai Univ., Japan

We have developed a QVGA electrochromic display of 16 gray scale with 300 μ m pixels by using leuco dye. Improving electric scanning procedures and the structure of the device, we attained clear images of 150 μ m pixels with eliminated cross talk and the weaker image flickering.

EP5 - 4 Printed/Coated Electrochromic Non-Volatile 16:10 Displays with Dispersible Prussian Blue Nanoparticles Nanoparticles

T. Kawamoto^{*}, H. Tanaka^{*}, M. Kurihara^{*,**}, M. Sakamoto^{*,**}, T. Kiyoshi^{*,***}, Y. Taguchi^{****}

*AIST, Japan **Yamagata Univ., Japan ***Alps Elec., Japan

By printing/coating electrochromic nanoparticles, we developed new non-volatile displays: a simple display that is switchable between two patterns, and a pixel device that is switchable between blue and white. The devices can work only by application of ca. 1 V. Using the technologies, a pattern-switchable keyboard was fabricated.

----- Break -----

16:40 -	18:00
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Main Hall

EP6: Cholesteric LCDs

Chair:	H. Arisawa, Fuji Xerox, Japan
Co-Chair:	T. Fujisawa, DIC, Japan

EP6 - 1Driving Scheme of Color E-Paper Using Ch-LC for16:40High Image Quality

M. Nose, H. Uehara, T. Shingai Fujitsu Labs., Japan

An improved driving scheme of color electronic paper using cholesteric liquid crystals for high image quality has been developed. The key factors were a contrast ratio and highlights uniformity. The achieved contrast ratio was 8.8 that was higher than newspapers, with 262,000 colors by using 2 different electro-optic responses.

EP6 - 2Fast Driving Scheme for Color Ch-LCD17:00H. Uehara, M. Nose, T. Shingai

Fujitsu Labs., Japan

We developed e-paper based on cholesteric liquid crystals, capable of fast re-write (0.7 seconds) with a high contrast ratio (6.9). Adopting a modified DDS from the high-speed driving method where grayscale is hard to control, the e-paper with a new grayscale control techniques achieves XGA resolution with 64 colors.

EP6 - 3 Spot Color Encapsulated Cholesteric LCD 17:20 O W Char W W Chin C V Wars P W Li

C.-W. Chen, W.-W. Chiu, C.-Y. Wang, P.-W. Liu, K.-W. Lan, C.-Y. Wu ITRI, Taiwan

In this paper, the fabrication of high reflectivity and low driving voltage encapsulated cholesteric liquid crystal display (En-ChLCD) for E-signage application was demonstrated. The performance of 22% reflectivity and 80 V driving voltage were achieved by optimized sheet to sheet coating manufacture process, respectively.

EP6 - 4Large Scale Bistable Cholesteric LCD with Thermal17:40Addressing

C.-Y. Wang, C.-C. Tsai, W.-H. Huang, P.-W. Liu ITRI, Taiwan

In this study we developed a 3-bit gray scale thermal-addressing writer which is able to refresh the image of 28 centimeters wide and 3 meters long cholesteric liquid crystal display in 3.5 minutes. To render color, a single-layer color Ch-LC display was developed for color thermal-addressing.

Author Interviews

18:00 - 19:00

IDW Tutorial in Japanese

Tuesday, November 30, 2010 Room 412 Fukuoka International Congress Center

Detailed information is announced at http://www.sidchapters.org/japan/

Friday, December 3

9:00 - 10:	25	Main Hall
	EP7: Electrowetting and LCDs	
Chair: Co-Chair:	A. Suzuki, Ricoh, Japan G. F. Zhou, Philips Res., the Netherland	
EP7 - 1:	Invited "No Power" (Green) Electrowetti	ng Displays

EP7 - 1: Invited "No Power" (Green) Electrowetting Displays 9:00 for Indicators as LED Replacement

K. Blankenbach, F. Bartels^{*}, J. Rawert^{**}, D. Jerosch^{**}

Pforzheim Univ., Germany *Bartels Mikrotechnik, Germany **ADT, Germany

High reflectivity and transmissive backlight mode are advantages of electrowetting displays; ADT's approach is the only bistable one. This paper deals with LED replacements for energy-saving systems. Achievements are fully compatible integration into LED housings, superior optical performance of electrowetting indicators in bright light compared to LEDs and "in-cell" touch.

EP7 - 2: Invited Electrofluidic Displays – First Prototypes, A 9:25 New Bistable Architecture, and 'Perfect' Segmented Electronic Paper

J. Heikenfeld^{*,**}, S. Yang^{*}, E. Kreit^{*}, M. Hagedon^{*}, K. Dean^{**}, K. Zhou^{**}, S. Smith^{**}, B. Brollier^{**}, J. Rudolph^{**} ^{*}Univ. of Cincinnati, USA ^{**}Gamma Dynamics, USA

Electrofluidic displays transpose brilliant pigment dispersions between a fluid reservoir of small viewable area and a channel of large viewable area. We report recent prototyping progress for the technology, a new multi-stable device architecture, and a novel approach for segmented displays that can display pigment without the optical losses of pixel borders.

EP7 - 3 Three-Terminal Bistable Splay Twist LCD

9:50 C. Y. Lee, M. C. Tseng, H. S. Kwok Hong Kong Univ. of S&T, Hong Kong

A bistable splay-twist LCD is proposed and demonstrated. Such a bistable display consists of two stable states, splay and pi-twisted states. Switching is achieved by using three-terminal electrodes. Optimizations of the optics and electrodes have also been performed. The display is permanent bistable and is suitable for electronic paper applications.

EP7 - 4LNovel Development of AM Electrowetting Display10:10with Color Filter on TFT-Array

H.-H. Lee, S.-W. Kuo, K.-L. Lo, W.-Y. Cheng, P.-P. Cheng, Y.-H. Tsai, Y.-S. Ku, J.-L. Chen, J.-W. Shiu, C.-Y. Wang^{*}, C.-Y. Chen^{*}, S.-J. Chang^{*}, C.-Y. Chou^{*}, H.-Y. Chang^{*}, W.-T. Liao^{*}, W.-C. Wang^{*}

ITRI, Taiwan ^{*}Wintek, Taiwan

An active matrix electrowetting display had been developed by using color filter on TFT-array. We adopted the black matrix and black oil with optical density of 1.2 to improve the optical performance. Due to the polarizer-free structure, this panel could be read easily with low-power backlight compared with traditional LCD.

Author Interviews 16:20 – 17:20

Supporting Organization:

The Imaging Society of Japan

BANQUET

Wednesday, December 1, 2010 19:30 – 21:30 Crowne Grand Ball Room (2F) ANA Crowne Plaza Fukuoka See page 9 for details

Evening Get-Together with Wine

Tuesday, November 30, 2010 18:00 – 20:00 at RACONTER (1F), Fukuoka International Congress Center (Sponsored by Merck Ltd., Japan) See page 9 for details

Workshop on MEMS and Emerging Technologies for Future Displays and Devices

9:00 - 9:05

Room 402

Opening

Opening Remarks 9:00

M. Nakamoto, Shizuoka Univ., Japan

Thursday, December 2

9:05 - 10:25

Room 402

MEET1: Emerging Technologies

Chair: K. Sato, Nagoya Univ., Japan Co-Chair: M. Takamiya, Univ. of Tokyo, Japan

MEET1 - 1: *Invited* Optimisation of CNTs and CNT/ZnO 9:05 Nanostructures for Use as Electron Sources

W. I. Milne^{*,**}, M. Mann^{*}, Y. Zhang^{*}, D. Hasko^{*}, C. Li^{*}

^{*}Univ. of Cambridge, UK ^{**}Kyung Hee Univ., Korea

The aim of this paper is to describe the growth and optimization of ballasted carbon nanotube (CNT) and CNT/Zinc Oxide nanostructures to produce novel electron sources for use in lighting and x-ray applications.

MEET1 - 2: *Invited* Fabrication and Field Emission Properties of 9:30 Vertically Aligned Carbon Nanotubes

Y. Bonnassieux, C. S. Cojucaru, A. Dhar, P. Legagneux*

Ecole Polytech., France *Thales Res. & Tech., France

We present some comparisons concerning field emission from two types of nanostructures, multiwall carbon nanotubes grown by plasma enhanced CVD and metal nanowires grown by electrochemical deposition. Various treatments with simple and low-cost processes are presented in order to decrease the growth temperature and to improve the emitted current uniformity.

MEET1 - 3Enhanced Electron Emission Property of Carbon9:55Nanotube Grown with High Temperature

A. N. Ha, J. H. Ryu, H. M. Oh, N. Y. Bae, E. H. Lee, W. M. Bae, J. Jang, K. C. Park Kyung Hee Univ.. Korea

A electron emission property of carbon nanotube (CNT) emitter grown with high temperature condition is studied. CNTs were grown on Si wafer with different temperature conditions. The electron emission current was enhanced with high growth temperature. The effect of high growth temperature on electron emission properties of CNTs was investigated.

MEET1 - 4Suppress Speckle in Line Scan Display System by10:10Binary Code

W. Gao^{*,**}, M. N. Akram^{*}, G. Ouyang^{*}, Z. Tong^{*}, X. Chen^{*} ^{*}Vestfold Univ. College, Norway ^{**}Beijing Inst. of Tech., China

A set of 2D binary codes are created, phase plates are fabricated by etched glass according to the code. It is introduced in laser based line scan display system to reduce speckle. According to experiment, the phase plate with the code of order 5 successfully reduces speckle contrast to 17.5%.

----- Break -----

10:40 - 12:15

Room 402

MEET2: Fundamental Components, Process Technologies (1)

Chair: W. Milne, Univ. of Cambridge, UK Co-Chair: T. Yatsui , Univ. of Tokyo, Japan

MEET2 - 1: *Invited* Extension of 3D Microstructures on Silicon 10:40 Wafer Realized by Wet Etching

K. Sato

Nagoya Univ., Japan

Advanced bulk micromachining using aqueous tetramethylammonium hydroxide (TMAH) solutions with and without a surfactant Triton X-100 $[C_{14}H_{22}O(C_2H_4O)_n, n = 9-10]$ is developed in order to extend the range of MEMS structures. A wide range of advanced fixed and freestanding microstructures are fabricated.

MEET2 - 2: Invited Large Area Electronics with Organic 11:05 Transistors and Novel Interconnects: EMI Measurement Sheet with Stretchable Interconnects and User Customizable Logic Paper (UCLP) with Ink-Jet Printed Interconnects

M. Takamiya, K. Ishida, T. Sekitani, Z. Ute^{*}, H. Klauk^{*}, T. Someya, T. Sakurai

Univ. of Tokyo, Japan *Max Planck Inst. for Solid-State Res., Germany

Large area electronics, which takes advantage of the flexibility and the low cost per area, is a good application of the organic FETs. In this paper, some examples of large area electronics using organic transistors including an EMI measurement sheet and a User Customizable Logic Paper (UCLP) are shown.

MEET2 - 3: *Invited* Nonlinear Spring of Thin Film Torsion Bar 11:30 with Tension for Micromirror

S. Ogawa, S. Kumagai, M. Sasaki

Toyota Tech. Inst., Japan

Nonlinear spring gives the wider balancing region against the electrostatic actuator. The thin film torsion bar with tension shows the large hard-spring effect. Its displacements are accurately measured using the white-light interferometer. Explanation based on the tension and the vertical shift gives reasonable agreement with the frequency change.

MEET2 - 4L Spherically Curved Guest-Host Display for Use in a 11:55 Contact Lens

J. De Smet^{*}, A. Avci^{*}, R. Beernaert^{*}, D. Cuypers^{**}, H. De Smet^{*,**}

*Ghent Univ., Belgium **imec, Belgium

A spherically curved cavity filled with a dichroic dye doped liquid crystal was made using flexible LCD processing techniques in order to create a contact lens display technology. Processing issues are described and their influence on uniformity and contrast are discussed.

13:20

MEET2 - 5L Speckle Reduction Using a Sinusoidal Rotating 12:05 Grating

S. Egge, M. Nadeem Akram^{*}, V. Kartashov^{**}, U. Österberg, A. Aksnes

Norwegian Univ. of Sci. & Tech., Norway *Vestfold Univ. College, Norway **poLight AS, Norway

Laser illumination in display projectors requires the presence of *speckle* to be reduced. A novel idea for speckle reduction uses the rotation of a diffraction pattern to cover different areas on a diffuse surface, producing independent speckle pattern. A speckle contrast of 0.27 was achieved, with further reduction possible.

----- Lunch -----

13:20 - 14:40 Room 402 MEET3: Optical MEMS and Device Technologies

Chair: Y. Bonnassieux, Ecole PolyTech., France Co-Chair: R. Sawada, Kyushu Univ., Japan

MEET3 - 1: Invited LED Backlighting with Quantum Dots

S. Sadasivan, S. Shah, S. Coe-Sullivan QD Vision, USA

Quantum dots (QDs) are nanomaterials that emit saturated light. In combination with blue LEDs, green and red QDs create white light. QD LCDs show improved color gamut over white LED LCDs. The increased gamut leads to higher perceived brightness. Such benefits make QDs a compelling choice for use in LCDs.

MEET3 - 2: *Invited* Emerging Front Light Technologies for 13:45 Reflective Displays Technologies

R. Rao, R. Grulkhe, M. Mienko, I. Bita Qualcomm MEMS Techs., USA

Reflective Displays are gaining tremendous popularity in mobile devices (e.g. e-readers) due to their sunlight readability and low power consumption. Main contribution to their power efficiencies is lack of backlight. However reflective displays need supplemental front-lighting in darker ambients. We highlight emerging front-lightings based on the work accomplished at Qualcomm.

MEET

MEET3 - 3 A Study of Light Guide Film with External 14:10 Illuminance Backlight Module

Y.-C. Fang, J.-C. Yu, C.-M. Tsai^{*}, C.-H. Huang, B.-R. Hsueh, C.-A. Chen

Nat. Kaohsiung First Univ. of S&T, Taiwan ^{*}Kun Shan Univ., Taiwan

This research proposes the concept of Back Light Unit(BLU) with external illuminance. This special optical design may introduce the external light into BLU in order to improve the power-saving. One is for 14-in. monitor, which has 21% improvement. Another for 3.5-in. display might have improvement 15%.

MEET3 - 4 Will Display Type LED Light Source Suitable for the 14:25 Matching of the Chlorophyll/PAR Spectrum?

C. R. Ou, J. S. Wang, H. P. Lo, L. Tasi Hsiuping Inst. of Tech., Taiwan

LED illuminating technologies provide a promising future for plant growth and global farming. However, there are misunderstandings and the disadvantages for part of the LED based application to the plant growth system. Discussion and recommendation based on the comparison of the spectrums will be present.

----- Break -----

15:00 - 16:20

Room 402

MEET4: Displays and Imaging

Chair: S. Coe-Sullivan, QD Vision, USA Co-Chair: M. Sasaki, Toyota Tech. Inst., Japan

MEET4 - 1: Invited Successful Optical MEMS and their 15:00 Application

R. Sawada

Kyushu Univ., Japan

Optical MEMS is one of the most promising and successful targets of the application of MEMS technology. There has been developing various kinds of category of this field. Some topics will be shown in this presentation; analogue mirror and sensors such as displacement sensor. Packaging and bonding technology are also hot topics as is always the case. In addition to such topics sensor in living body will be shown as a new topics in this field.

MEET4 - 2: *Invited* MEMS Based Time Multiplexed Optical 15:25 Shutter (TMOS) Full Color Display

D. V. Ostrand, R. Ramakrishnan Uni-Pixel Displays, USA

The most significant challenge in making a full color MEMS display with a deformable membrane is the membrane. It must have the correct optical, mechanical and electrical properties. The membrane we have developed for TMOS[™] fulfills these challenges.

MEET4 - 3 Review of Microdisplay Device and System 15:50 Components for Optogenetic and Optical Neural Guided Experiments

C. R. Ou, C.-I. Shen^{*} Hsiuping Inst. of Tech., Taiwan ^{*}Nat. Chung Hsing Univ., Taiwan

Optogenetic technology is been consider as one of the most promising biomedical breakthrough for neuron science. The contribution of the display technology for the neuron science research will be report, and the common platform for optogenetic and optical neuro guiding device will be addressed.

MEET4 - 4 Switching Property of Carbon Nanotube Emitters by 16:05 Using MOSFET

W. M. Bae, J. H. Ryu, N. Y. Bae, H. M. Oh, E. H. Lee, A. N. Ha, J. Jang, K. C. Park Kyung Hee Univ., Korea

The electron emission current of CNTs was well switched with a low voltage with MOSFET. The switching properties of CNT emitters was studied. For 500 μ A emission current switching, the electron emitter keeps constant electron emission current between 1300 V and 2100 V region with 0.02 % variation.

----- Break -----
16:40 - 17:55

Room 402

MEET5: Fundamental Components, Process Technologies (2)

Chair: D. V. Ostrand, Uni-Pixel Displays, USA Co-Chair: R. Rao, Qualcomm MEMS Techs., USA

MEET5 - 1: Invited Increased Spatial Homogeneity in a Light-16:40 Emitting InGaN Thin Film Using a Phonon-Assisted Optical Near-Field Process

T. Yatsui, M. Ohtsu

Univ. of Tokyo, Japan

We report a self-assembly method that produces greater spatial uniformity in InGaN thin films using optical near-field desorption. Spatial homogeneity in the In fraction was reduced by introducing additional light during the photo-enhanced chemical vapour deposition of InGaN.

MEET5 - 2Development of Full-Color Active-Matrix Quantum17:05Dot Light Emitting Diode Displays

P. Kazlas, Z. Zhou, M. Stevenson, Y. Niu, C. Breen, J. Perkins, S.-J. Kim, G. Mahan, J. Steckel, S. Coe-Sullivan, J. Ritter

QD Vision, USA

Quantum dot light emitting diodes are a printable thin film electroluminescent technology that delivers exceptional color and efficiency at low cost of manufacture for display and solid-state lighting applications. We report on our progress developing efficient, stable QLEDs for full-color active-matrix displays, including recent advances in device performance and lifetime.

MEET5 - 3 Sharp and Uniform Conductive Ceramic Transfer 17:20 Mold Field Emitter Arrays

K. Suzuki, M. Nakamoto, J. H. Moon Shizuoka Univ., Japan

Sharp and uniform conductive ceramic $Cr_3Si \cdot SiO_2$ Transfer Mold field emitter arrays with less than 5.0 nm tip radius have been developed by Transfer Mold method to realize the low operation voltage and stable vacuum nanoelectronic devices for lamps, backlight units, and electric propulsion engines for satellites and spaceships.

MEET5 - 4L Processing of Interferometric MEMS-type Reflective 17:35 Display using Photoresist as Sacrificial Layer

H.-C. Park, Y.-S. Kim Hongik Univ., Korea

In this study, an attempt was made to utilize photoresist as a sacrificial layer in the processing of interferometric type MEMS reflective displays. The results indicated that the photoresist became dissolved in etching solution more cleanly, making the process more productive and economic.

MEET5 - 5L Transmittance Enhancement in an IZO/Ag/IZO 17:45 Transparent Electrode Using Surface Plasmon

S. H. Oh, S.-M. Lee, K. C. Choi KAIST, Korea

In this work, an IZO/Ag/IZO structured transparent electrode was investigated through a silver annealing process. A silver layer was independently deposited in an additional annealing process. This method resulted in an increment of 7% of the transmittance through the successful formation of a silver layer with a corrugated surface.

Author Interviews

18:00 - 19:00



Workshop on Display Electronic Systems

Thursday, December 2

9:00 - 12:00

Poster/A.I. Room

Poster DESp: Display Electronic Systems

DESp - 1 Adaptive Frame Rate Modulation Architecture for Power Saving

D.-W. Kuo, J.-S. Liao, H.-H. Chen, W.-T. Tseng, C.-R. Lee

Chunghwa Picture Tubes, Taiwan

Chunghwa Picture Tubes, LTD. (CPT) has presented an algorithm of power saving for TFT LCD. This technique could change regional frame rate according to what kind of image data is displayed. If the image is static state, the frame rate can be reduced that can also reduce power consumption.

DESp - 2 Novel Signal Interface for TFT-LCD Module Test Using Power Line Communication Method

J. M. Lee, H. S. Kim, J. H. Yoo, S. Y. Han Samsung Elect., Korea

We firstly proposed the power line communication as novel signal interfaces in the LCD module test. Comparing with conventional auto contact, low failure rate and high speed communication were achieved. No side effect of electromagnetic interference was observed, meaning that PLC could be a promising signal interface in the future.

DESp - 3 A Novel Passive Matrix Drive Scheme for Bistable Chiral Splay Nematic LCDs

J. G. Ying, S. B. Kwon, C. G. Jhun, Y. M. Lee, K. S. Kim, D. C. Jeong Hoseo Univ., Korea

In this paper we discuss a novel passive matrix drive scheme for bistable chiral splay nematic LCDs. We use three voltage levels for the addressing in this drive scheme. And different from other passive matrix drive schemes, the data voltage is hundreds of mV and the frequency is about 1 Hz.

DESp - 4 High Performance Digital Signage Using Color Sequential Technique

T.-C. Yang, K.-H. Chien, W.-C. Tai Chunghwa Picture Tubes, Taiwan

A high performance digital signage has been developed. Color Senguential Display (CSD) panel which using PWM control RGB LED backlight and color filter less glass composed the digital signage. This high performance digital signage achieves high color gamut, contrast and low power consumption.

DESp - 5L LCD Backlight Controller Using Passive Sigma-Delta Modulator PWM Generator

Y.-M. Lee, K.-S. Lee Sun Moon Univ., Korea ^{*}Univ. of Akron, USA

This works describes a LCD backlight controller using passive $\Sigma\Delta$ modulator PWM generator. In this scheme, a PWM signal corresponding to the ambient light level is generated from the pulse density modulated $\Sigma\Delta$ output. Therefore, the area and power can be reduced compared to conventional PWM generator circuits.

----- Lunch -----

13:20 - 14:50

Room 412

VHF4/DES1: Multi Primary (1)

Chair: K. Sekiya, Tohoku Univ., Japan Co-Chair: T. Matsumoto, Sony, Japan

VHF4/ Invited Measuring Light and Color: An Introductory DES1 - 1: Talk to Colorimetry 13:20 N Obto

N. Ohta

Rochester Inst. of Tech., USA

Colorimetry is quantifying colors, that is, an art of expressing colors by numbers. There are two classes of quantification: color appearance system and color mixing system. The gist of the two methods will be introduced.

VHF4/A New Evaluation Method of Color ReproductiveDES1 - 2Performance and Evaluation of Multi-Primary Color13:50Display

M. Teragawa, T. Kanda, T. Fujine, M. Sugino, Y. Miyanaga^{*} Sharp, Japan ^{*}Hokkaido Univ., Japan

This paper proposed new evaluation of color reproductive performance, and evaluated MPC display. We used coverage ratio against object color for evaluation of outer frame structure, and CDI for evaluation of inner structure. We clarified MPC display was suitable for expressing object colors and had advantage of smooth color reproduction.

VHF4/Color Reproduction of Multi-Primary Color Display:DES1 - 3Numerical Analysis Method and Application to14:10Lower Power Consumption

T. Fujine, M. Teragawa, N. Ohta^{*} Sharp, Japan ^{*}Rochester Inst. of Tech., USA

We analyze color reproduction of multi primary color (MPC) display, and propose to calculate primary amount of color mixing for MPC in minimum power consumption by linear programming. As an example, we analyze characteristics of RGB+Y four primary color system in comparison with RGB system.

VHF4/ A Numerical Evaluation across Multi-Primary Color DES1 - 4 Systems

14:30

A. Yoshida, K. Yoshiyama, K. Tomizawa, K. Nakamura, Y. Yoshida, M. Teragawa, Y. Yamamoto^{*}, N. Ohta^{**}

Sharp, Japan ^{*}CIS Labs., Japan ^{**}Rochester Inst. of Tech., USA

We conducted a numerical analysis over several Multi-Primary Color (MPC) display systems consisting of RGB + Cyan primaries. We compared the results with our previous results (RGB + Yellow and RGB + White) for indicating characteristics of different MPC systems in terms of luminance reproduction and power consumption.

----- Break -----

15:00 - 16	:20 Room 412
	VHF5/DES2: Multi Primary (2)
Chair: Co-Chair:	N. Ohta, Rochester Inst. of Tech., USA T. Matsumoto, Sony, Japan
VHF5/ DES2 - 1: 15:00	Invited Four Primary Color (RGB+Y) Displays: The Latest Technologies and Advantages
	M. Teragawa Sharp, Japan
<u> </u>	

This paper reviews the latest RGB+Y four primary color LCD technologies and the advantages. RGB+Y LCD has advantages for not only color reproducibility but also power consumption, in addition, higher resolution. RGB+Y LCD along with UV2A can make LCD-TV improved in all ways.

VHF5/ High Resolution Reproducibility of Multi-Primary **DES2 - 2 Color Displays** 15:40

K. Yoshiyama, H. Furukawa, N. Kondoh, S. Nakagawa, Y. Yoshida

Sharp, Japan

In this paper, we focus on high resolution characteristic of Multi-Primary Color (MPC) display, and show that horizontal resolution can be approximately twice for stripe-patterned four-primary color display by the combination with advanced sub pixel signal processing.

VHF5/ Advanced RGBW Display Image Process Using **DES2 - 3** Sub-pixel Rendering

16:00 M.-C. A. Kao, P.-L. Hsieh, H.-T. Lin Chunghwa Picture Tubes, Taiwan

A novel image process has been developed to transform RGB into RGBW. It comprise the "RGBW mapping algorithm" is used to adjust color of image. And the "Virtual resolution scaling" is used to increase the apparent resolution. And the "W signal controlling" is used to increase sunlight readability.

----- Break -----

16:40 - 18:00

Room 413

3D3/DES3: 3D System and Content

Chair:	JY. Son, Daegu Univ., Korea
Co-Chair:	T. Fujine, Sharp, Japan

3D3/ Invited Full HD and Super-High Image Quality 3D DES3 - 1: Plasma TV Technology

16:40 K. Tasaka, M. Kawashima, K. Suetsugi, M. Ishizuka, T. Yamashita, Y. Sugio Panasonic, Japan

This paper introduces the basic concept of Full HD and High Image Quality 3D Plasma Theater System and the key technology of Full HD and Super-High Image Quality 3D Plasma TV which was realized by the newly developed technology of Plasma panel improvement and new 3D system technology of both Plasma panel and 3D eyewear.

3D3/InvitedReal-Time 2D-to-3D Conversion: BasicDES3 - 2:Concepts and Practical Use

17:00 K. Yamada, Y. Suzuki

JVC Kenwood Holdings, Japan

This paper describes the algorithm for our original 2D-to-3D conversion technology, which is beginning to be used for both consumer and professional apparatuses to fulfill the growing need for high quality 3D contents. The algorithm has advantages in quality, numerical complexity, no need of frame memory and very low latency.

3D3/ Invited From 3D technology to New Styles of Visual DES3 - 3: Images

17:20 M. Ikeo, A. Saito, Y. Nishida NHK Media Tech., Japan

The desire to visualize our imagination in new ways has encouraged the evolution of the media, while technical innovation has inspired our imagination. However, recent rapid advances in digital technology are leading the media not to represent human imagination but to mirror the actual world with ever greater reality. Can filmmakers' imagination catch up with the hyperrealism of the visual media? Content creators must shed the bonds of 3D images and develop new styles of visual images.

3D3/ Invited 3D Video Formats and Compression for DES3 - 4: Content Distributions

17:40 H. Kimata

NTT, Japan

Usage of 3D video would increase as the growth of 3D content production. The suitable 3D video format depends on the purpose in applications. This paper summarizes 3D video formats and compression technologies distinguished by purposes and it addresses the trends of stereoscopic video and multi-view video formats.

Author Interviews 18:00 – 19:00

Friday, December 3

9:00 - 10:00 Ro		Room 413
	DES4: Display Electronics	
Chair: Co-Chair:	T. Yamamoto, NHK, Japan H. Sasaki, Toshiba, Japan	
DES4 - 1 9:00	The Optimal RGB LED Driving Schem Sequential LCD	e for Color

T. P. Lin, K. T. Hu, C. L. Liu, C. H. Tien^{*} Chunghwa Picture Tubes, Taiwan ^{*}Nat. Chiao Tung Univ., Taiwan

This paper demonstrated a 15-inch color sequential display by using RGB LED-based backlit embedded with a color sensor feedback system. The driving sequence of RGB LEDs is essential for eventual image qualities. And a color sensor feedback system was employed to regulate LED brightness and any customized white point.

DES4 - 2 Withdrawn

DES4 - 3 A Linear 10-Bit DAC for LCD Driver ICs Using 9:20 Charge Subtraction Interpolation

J. Bae, Y. Jang, H. N. Nguyen, S. Lee KAIST, Korea ^{*}Silicon Works, Korea

A linear 10-bit digital-to-analog converter has been designed for LCD driver ICs. The proposed architecture suggests charge subtraction interpolation technique with switched-capacitor DAC. The size of DAC will be decreased around half and DNL, INL simulation results are smaller than 0.04 LSB.

DES4 - 4 On-Chip DC-DC Converter Technique for Mobile 9:40 Flat-Panel Display

Y.-S. Ahn^{*,**}, J.-M. Choi^{*}, J.-S. Lee^{*}, Y.-S. Kim^{*}, H.-S. Oh^{*}, J.-K. Kang^{**} ^{*}Silicon Works, Korea ^{**}Inha Univ., Korea

One of single-chip display driver's components is power management block. Unfortunately, power management block is an interfering. So, a spread spectrum is widely applied technique to reduce EMI. But, power management block using spread spectrum lowers display's image quality. We propose a single-chip display driver for lossless display's image quality.

----- Break -----

10:40 - 12:00 Room 413 DES5: Low Power Technology Chair: H. S. Kaa. Ming Haing Haing Linix of S&T. Taiwan

Chair: H.-S. Koo, Ming-Hsing Univ. of S&T, Taiwan Co-Chair: K. Sekiya, Tohoku Univ., Japan

DES5 - 1: Invited Method to Save Power While Watching TV 10:40 According to Viewer Watching Action

T. Yoshinaga, S. Nagaya, T. Fujita, H. Sakaniwa, H. Ito Hitachi, Japan

We propose a method to conserve TV power according to the viewer's watching action. In this method, a camera is used to classify the action, and the panel backlight power is then automatically controlled. Experimental results indicated the power consumption was reduced by 18.6% using this method.

DES5 - 2: Invited Low-Power Mobile Processor Design for 11:00 Full-HD Video Coding

M. Kimura, K. Iwata, S. Mochizuki, H. Ueda, R. Hashimoto, H. Hatae, H. Watanabe Renesas Elect., Japan

Today's cellular phone must support full high-definition video encoding and decoding. In order to reduce static and dynamic power consumption, this paper introduces multiple power-domain control, dynamic clock control, and video codec architecture based on picture level pipeline manner. Our mobile application processor consumes 342 mW in real-time decoding of Full-HD video.

DES5 - 3 Contrast Ratio Enhancement and Power Saving for 11:20 17.3-in. LCD with Side-Lit LED-Backlight Structure

T.-C. Shen, S.-M. Chang Chunghwa Picture Tubes, Taiwan

This paper proposes a method to calculate the brightness distribution of backlight model for 17.3-in. LCD LED-backlight display. An exact data compensation calculation method is applied to Site-lit LED-backlight structure so that power is conserved and also contrast ratio is increased.

DES5 - 4 Key Feature Highlighting: A High Ambient Display 11:40 and Extreme Display Power Reduction Technology

X. Xu, L. Kerofsky Sharp Labs. of America, USA

Low contrast viewing of LC displays occurs often nowadays which includes high ambient viewing of mobile LC devices and LC TV viewing at extreme low power mode. In this paper, Key Feature Highlighting (KFH) technology is proposed to improve perceived contrast and visibility of images at low contrast viewing conditions.

----- Lunch -----

Room 413

13:20 - 14:40

DES6: Display Quality

Chair:	T. Fujine, Sharp, Japan
Co-Chair:	A. Nagase, Mitsubishi Elec., Japan

DES6 - 1: Invited Halo Artefact Visibility for Local Backlight 13:20 Dimming LCD Systems

M. Hammer, R. Muijs^{*}, E. H. A. Langendijk Philips Consumer Lifestyle, the Netherlands ^{*}Philips Res. Labs., the Netherlands

To increase display contrast, local backlight dimming LCDs have become common practice. However, the spatial resolution of a segmented backlight is typically well below that of the LC-panel. In dark image regions, this may result in undesirable halo artefacts due to light leakage through the panel of the low-resolution backlight image. In this contribution we propose a signal processing approach to determine the visibility of halo artefacts.

DES6 - 2: Invited Universal Overdrive Technology for LCD 13:40 Systems and High-Refresh Rate LCTVs

S.-W. Lee

Kyung Hee Univ., Korea

This paper describes a universal overdrive technology for LCD systems regardless of LC modes. This paper shows a method to simulate transient optical responses of matrix-driven LCDs using dynamic circuit model of LC pixels. Special considerations on the OD technology applicable to high refresh-rate LC TVs will be presented.

DES6 - 3: Invited Mobile Color Depth: A Perceptual Color-14:00 Performance Metric for Mobile Displays

J. Gille, G. U'Ren Qualcomm MEMS Techs.. USA

Display color performance is regularly described by data input format (e.g., 24-bit color) as opposed to perceived number of colors output for a given viewing environment. Mobile Color Depth (MCD) is developed as a vision-based metric quantifying perceived numbers of colors, providing an understandable, unitary, display-performance metric.

DES6 - 4 Subjective Quality Assessment of Adaptive 14:20 Temporal Filter for High Frame-Rate Video

Y. Bandoh, S. Takamura, H. Jozawa NTT, Japan

In the design of an adaptive temporal filter for high frame-rate sequence, it is important to set suitable filter parameter in order to keep subjective quality of down-sampled sequence. In this paper, we clarify relationship between the subjective quality of down-sampled sequence and filter configuration for generating down-sampled sequence.

----- Break -----

15:00 - 16:20

Room 413

DES7: Visible Light Communication

Chair:	S. Ito, Shizuoka Univ., Japan
Co-Chair:	H. Okumura, Toshiba, Japan

DES7 - 1: Invited Visible Light Communication

15:00 S. Haruyama Keio Univ., Japan

Visible light communication is a new way of wireless communication using visible light. Main transmitters used for visible light communication are visible light LEDs and receivers are photodiodes and image sensors. We present new applications which will be made possible by visible light communication technology, such as indoor navigation system.

DES7 - 2: Invited Image Sensor Communication - A New Way 15:40 of Visible Light Communication

N. lizuka

Casio Computer, Japan

Image Sensor communication (ISC) is a new communication technology using two-dimensional image sensors such as CCDs or CMOS sensors. It is a new way of Visible Light Communication (VLC). And it has remarkable features. In this paper, we present the results of feasibility trials and various applications of ISC.

DES7 - 3: Invited A CMOS Image Sensor for Car-to-Car and 16:00 Road-to-Car Optical Communication

S. Itoh, M. S. Z. Sarker, K. Yasutomi, M. Hamai, Y. Iwama, I. Takai^{*}, M. Andoh^{*}, S. Kawahito

Shizuoka Univ., Japan *Toyota Central R&D Labs., Japan

A CMOS image sensor for Car-to-Car and Road-to-Car optical communication is presented. A prototype sensor chip achieves high data rate up to 10 Mbps at the communication distance of over 100 meters while attaining signal light source finding and tracking functions.

Room 413

16:20 - 16:25

Closing

Closing Remarks 16:20

H. Okumura, Toshiba, Japan

Author Interviews

16:20 - 17:20

Supporting Organizations:

Technical Committee on Electronic Information Displays, Electronics Society, IEICE

Technical Committee on Image Engineering, Information and Systems Society, IEICE

Information Sensing Research Committee, ITE

EXHIBITION

12:00 - 18:00 Wednesday, Dec. 1, 2010

10:00 - 18:00 Thursday, Dec. 2, 2010

10:00 - 14:00 Friday, Dec. 3, 2010

2F Lobby, 4F Lobby Fukuoka International Congress Center

Free admission with your registration name tag

SID 2011

International Symposium, Seminar and Exhibition

May 15-20, 2011

Los Angeles, California, U.S.A.

DES

Workshop on Flexible Displays

Wednesday, December 1

13:20 - 13:25

Room 204

Opening

Opening Remarks 13:20

T. Furukawa, Kyodo Printing, Japan

13:25 - 14:30	Room 204
FLX1: Advanced Flexible Display Tecl	hnologies

Chair: H. Naito, Osaka Pref. Univ., Japan

Co-Chair: H. Hirata, Toray Eng., Japan

FLX1 - 1: *Invited* Recent Advances in Flexible Displays of 13:25 e-Paper Application

J.-W. Shiu, W.-W. Chiu, C.-C. Tsai, C.-Y. Huang, J. Chen ITRI, Taiwan

The flexible display reported here is ideal for roll-to-roll process with a simple structure on single substrate. The performance has improved in reflectance and contrast ratio. A thermal addressing method is developed for ultra long e-paper applications with high resolution. Many novel applications of the display are also revealed.

FLX1 - 2 Low Temperature Annealing Amorphous In-Ga-Zn-O 13:50 Thin-Film Transistor on Plastic Substrate

T. Hanada, T. Negishi, M. Soeda, T. Shiro Teijin, Japan

For flexible display development, amorphous In-Ga-Zn oxide thin film transistors were fabricated on plastic substrate at ambient temperature. The transistor structure was coplanar top-gate. After annealing at 150 °C the field-effect mobility was 7.4 cm²/Vs, threshold voltage 0.3 V, subthreshold swing 0.29 V/decade and on-off current ratio 10^8 .

FLX1 - 3 Effect of AC and DC Gate Bias-Stress on the 14:10 Performance of a-IGZO TFTs on Plastic Substrate

M. Mativenga, M. H. Choi, J. W. Choi, J. Jang Kyung Hee Univ., Korea

The effect of AC and DC gate bias stress is investigated in a-IGZO TFTs on polyimide. For the same effective stress time, AC induces a smaller positive ΔV_{th} compared to DC stress, indicating trapping as the main degradation mechanism. The time dependence of ΔV_{th} thus follows the stretched exponential equation.

----- Break -----

15:00 - 16:25

Room 204

FLX2: Printing Fabrication Processes

Chair: M. Funahashi, Kagawa Univ., Japan Co-Chair: T. Furukawa, Kyodo Printing, Japan

FLX2 - 1: *Invited* Low Temperature Wiring Technology for 15:00 Printed Electronics

K. Suganuma, M. Nogi, M. Hatamura, T. Araki, J. Jiu Osaka Univ., Japan

Flexible low temperature wiring methods have been developed. The room temperature curable Ag nanoparticle ink and the Ag carboxylate ink have been successfully developed for temperature sensitive substrates. Ag-urethane conductive adhesive exhibits excellent stretchability on a flexible substrate up to 600% elongation without serious damage.

FLX2 - 2: Invited Development of Low Temperature Printing 15:25 Techniques for Flexible Display Fabrication

T. Kamata, M. Yoshida, T. Kozasa, S. Uemura, N. Takada, K. Suemori, S. Hoshino, N. Ibaraki AIST. Japan

We have developed several kinds of low temperature printing techniques of metal, inorganic semiconductor and dielectric layers for flexible display fabrication. These developed techniques were effective to obtain enough high electronic performance of the printed layer although process temperature was below 100°C.

FLX2 - 3 All-Printed Flexible 5.35-in. Organic TFTs with 150 15:50 ppi Resolution for Electrophoretic Electronic Papers

Y. Ito, R. Matsubara, O. Kina, M. Ishizaki, M. Ito Toppan Printing, Japan

All-printed flexible 5.35-in. VGA electronic papers were successfully driven by organic thin film transistors (OTFTs) with 150 ppi resolution. A poly-ethylene-naphthalate (PEN) film was used for the substrate and all the components were printed without any photo-lithographical process. The printed OTFTs showed over 0.2 cm²/Vs mobility and excellent uniformity.

FLX2 - 4LDevelopment of Printed, High-Performance Organic16:10Semiconductor Devices

G. Lloyd, T. Backlund, P. Brookes, L. W. Tan,
P. Wierzchowiec, S. Bain, J.-Y. Lee, M. James,
J. Canisius, S. Tierney, K. Kawamata^{*}, T. Wakimoto^{*}
Merck Chems., UK

^{*}Merck, Japan

We present our new formulation and material developments enabling high volume and high throughput printing techniques to be used for electronic circuit and backplane production. Performance levels in excess of 2 cm²/Vs, comparable to spin coating are demonstrated for flexographic and gravure based printing techniques for both top-gate and bottom-gate architectures.

----- Break -----

16:40 - 18	:00 Room 204
	FLX3/EP1: Flexible Electronic Paper
Chair: Co-Chair:	Y. Masuda, Bridgestone, Japan H. Fujikake, NHK, Japan
FLX3/ EP1 - 1 16:40	Large Area and High Precision Organic TFT Array of A4 Size with 200 ppi on Plastic Substrate by Microcontact Printing Technique
	K. Yase
	AIST, Japan

We have succeeded in driving a high resolution polymer network liquid crystal display (PNLCD) by using OTFT array obtained by microcontact printing (μ CP) method. By optimizing the fabrication condition, 200 ppi with the pixel size of 125 μ m on A4 size plastic substrate was achieved.

FLX3/Development of Flexible Electronic PaperEP1 - 2with Transparent Polymer Electrodes Prepared17:00through Directly Printing Approach

M. Nishii, Y. Iwabuchi, H. Kotsubo, R. Sakurai, Y. Masuda, R. Hattori^{*}

Bridgestone, Japan ^{*}Kyushu Univ., Japan

A 4.0 in. diagonal and 88 dpi flexible electronic paper with line-shaped electrodes composed of transparent conductive polymer of PEDOT/ PSS was prepared and passive matrix images were successfully displayed. The line-shaped electrodes of the conductive polymer were directly formed onto the flexible PET substrate by using screen printing method.

FLX3/
EP1 - 3Flexible Color Ch-LC E-Papers17:20S.-C. Chen, H.-Y. Chen, C.-C. Liang, C.-L. Chin,
C.-W. Chen, J.-Y. Su
ITRI. Taiwan

This paper proposes flexible color Ch-LC e-papers. By adding photochiral dopant, single substrate flexible Ch-LCD becomes sensitive to UV light. Therefore, UV exposure can cause the discontinuous change in the helical pitch of the Ch-LC pixels to locally colorize the e-paper. After being colorized, the color e-paper can be electrically driven to update the displayed content. In this paper, the 50 dpi color R2R Ch-LC e-paper is implemented.

FLX3/
EP1 - 4Preliminary Evaluation of LED Photo-Addressing
on ChLCD Electronic Paper17:40W.-J. Li, C.-J. Li, M.-Y. Lu, B.-W. Xiao, T.-T. Chang,
K.-J. Hu
ITRI, Taiwan

We have done a preliminary work on photo-addressing method for Chlcd electronic paper with auxiliary LED light source. The Chlcd electronic paper could be written more efficiently by controlling high luminous intensity LED appropriately. Finally we have realized the prototype of the photo-addressable electronic paper with LED light pen.

FLX

Author Interviews 18:00 – 19:00

Thursday, December 2

9:00 - 10:15	5 Room 204
	FLX4/OLED4: Flexible OLED
Chair: Co-Chair:	T. Kamata, AIST, Japan S. Naka, Univ. of Toyama, Japan
FLX4/ OLED4 - 1 9:00	Solution-Processed Organic Films of Multiple Small- Molecules and White Light-Emitting Diodes
	W. Dongdong, W. Zhaoxin, Z. Xinwen, J. Bo, L. Shixiong, W. Dawei [*] , H. Xun
	Xi'an Jiaotong Univ., China [*] Univ. of Arkansas, USA

We found that the spin-coated films of NPB, and blends of NPB and DPVBi, though having lower densities, were more uniform than their vacuum-deposited counterparts. Using the spin-coated films of NPB:DPVBi as mixed host, doped with blue and yellow dyes, new white organic light-emitting devices (WOLEDs) were demonstrated.

FLX4/ Flexible OLED Encapsulation by Glass Base OLED4 - 2 Technology 9:20 G. Chen, S.-T. Yeh, P.-I Shih, J.-L. Wu, K.-Y. Cheng, L.-Y. Jiang, Y.-Y. Chang ITRI, Taiwan

A flexible OLED encapsulation process was successfully developed with glass base OLED mass production equipment. These flexible encapsulation OLED devices have good flexibility and environment reliability. We expected this approach will be the important way to manufacture the flexible OLED devices using currently most OLED equipment facility.

FLX4/ Graphene Sheet Synthesized with Microwave OLED4 - 3 Eradiation and Interlinked by Carbon Nanotubes for 9:40 High-Performance Transparent Flexible Electrodes

G. Xin, W. Hwang, N. Kim, H. Chae Sungkyunkwan Univ., Korea

High quality graphene was obtained though microwave irradiating expansion following a solution process. By combining Carbon Nanotubes (CNTs) as bridges between graphene flakes, allowed the fabrication of high performance conductive films with conductivities and optical properties: $181 \ \Omega sq^{-1}$ at 82.2% transmittance after chemical treatment and doping.

FLX4/ Fabrication of QVGA Flexible Phosphorescent OLED4 - 4L AM-OLED Display using Ink-jet Printing 10:00 M. Suzuki, H. Fukagawa, G. Motomura, Y. Nakajima, M. Nakata, H. Sato, T. Shimizu, Y. Fujisaki, T. Takei, S. Tokito^{*}, T. Yamamoto, H. Fujikake NHK. Japan NHK. Japan

*Yamagata Univ., Japan

We demonstrated a 5-inch QVGA flexible phosphorescent AM-OLED display driven by OTFTs on a plastic substrate. Cross-linked olefin polymer was used as the gate insulator. Phosphorescent polymer materials were used for emitting layer of OLEDs, which were patterned by ink-jet printing. Color moving images were achieved by the display panel.

----- Break -----

10:40

10:40 - 12:10

Room 204

FLX5/AMD4: Flexible Active-Matrix Devices

Chair:	K. Tsukagoshi, NIMS-MANA, Japan
Co-Chair:	T. Shiro, Teijin, Japan

FLX5/ Invited Application of Organic Thin-Film Transistors AMD4 - 1: for Circuits on Flexible Foils

P. Heremans^{*,**}, K. Myny^{*,**}, H. Marien^{**}, E. V. Veenendaal^{***}, S. Steudel^{*}, J. Genoe^{*}, M. Steyaert^{**}, G. H. Gelinck^{****}

^{*}imec, Belgium ^{**}Katholieke Univ. Leuven, Belgium ^{***}Polymer Vision, the Netherlands ^{****}Holst Ctr. TNO, the Netherlands

We present the state of the art of digital and analog circuits (in particular code generators for RFID tags, amplifiers, AC-DC and DC-DC converters) using organic TFTs on plastic foil, and discuss some design considerations needed to overcome today's technology limitations.

FLX5/	Invited A Rollable OTFT-OLED Display
AMD4 - 2: 11:05	I. Yagi, M. Katsuhara, A. Yumoto, N. Kobayashi, M. Noda, R. Yasuda, S. Ushikura, G. Yukawa, N. Hirai, K. Nomoto, T. Urabe
	Sony, Japan

A rollable OLED display, which can be rolled-up in a radius of 4 mm, is driven by a newly-developed OTFT backplane. The backplane equips with an integrated gate driver circuit and it is constructed of OTFTs using a self-developed organic semiconductor, a PXX derivative.

 FLX5/
 The High Stability and Uniformity a-IGZO Thin Film

 AMD4 - 3
 Transistors Array for AM-OLED Application

 11:30
 J.-Y. Yan, H.-C. Yao, Y.-P. Chen, C.-Y. Hung, Y.-Y. Wu,

 K.-Y. Ho, H.-C. Cheng
 ITRI, Taiwan

The high stability and uniformity amorphous InGaZnO₄ TFTs were fabricated on plastic substrate. We optimize the process and abandon the ES layer to reduce photomask and processing time. The mobility, SS and Vth of a-IGZO TFTs is 7.33 cm²/Vs, 0.42 V/dec and 0.79 V. The lifetime of AMOLED is exceeding 10 years.

FLX5/ AMD4 - 4 11:50	Full Color AM-LCDs on Flexible Glass Substrates
	S. Hoehla, S. Garner [*] , M. Hohmann, O. Kuhls, X. Li [*] , A. Schindler, N. Fruehauf
	Univ of Stuttgart, Germany

Univ. of Stuttgart, Germany *Corning, USA

We have realized a full color 4-in. quarter-VGA amorphous Silicon AM-LCD on 75 μm flexible glass substrates. With this work we demonstrate that the incorporated ultra-thin glass substrates have suitable properties to be compatible with a standard color AM-LCD process and achieve active matrix backplanes with reliable performance.

----- Lunch -----

13:20 - 14:45

Room 204

FLX6: Flexible Organic TFT

Chair:	H. Maeda, DNP, Japan
Co-Chair:	K. Yase, AIST, Japan

FLX6 - 1: *Invited* Organic-Inorganic Hybrid Materials 13:20 for Flexible Thin-Film Transistors

H. Naito, T. Nagase, M. Yoshikawa, T. Kobayashi, Y. Michiwaki^{*}, K. Matsukawa^{**}

Osaka Pref. Univ., Japan ^{*}Fuso Chem., Japan ^{**}Osaka Municipal Tech. Res. Inst., Japan

Excellent characteristics of field-effect transistors fabricated using the following hybrid materials have been demonstrated. A hybrid gate insulator of poly(methylsilsesquioxane) exhibits excellent insulating properties, low curing temperature and low surface energy. Hybrid semiconductors, silica nanoparticles added organic semiconductors, exhibit drastic improvement of their wettability on low-surface-energy surfaces.

FLX6 - 2High Performance Organic Semiconductors13:45with High Field-Effect Mobilities and Low Contact
Resistances for Flexible Displays

K. Terai, E. Kawashima, N. Kurihara, H. Nagashima, H. Kondo, M. Saito, H. Nakamura Idemitsu Kosan, Japan

We have succeeded in developing p-type of organic semiconductors with phenylethynyl groups, which have high filed-effect mobilities (>3 $\text{cm}^2 \text{V}^1 \text{s}^{-1}$). We have found that they have lower contact resistances to Au electrodes, and confirmed that they had the potential to be used as a carrier injection layer.

FLX6 - 3 Solution Processed Organic Field Effect Transistors 14:05 from Novel Soluble Dinaphthothienothiophene Precursor

Y. Ikeda, T. Negishi, S. Ohomori, T. Shiro, K. Takimiya^{*} Teijin, Japan ^{*}Hiroshima Univ., Japan

A soluble dinaphthothienothiophene (DNTT) precursor is developed for printed O-FETs. The precursor is annealed in air to produce DNTT, an organic semiconductor with high mobility and durability. O-FETs using the precursor are fabricated on silicon or plastic substrates by spin coating and spray deposition followed by the thermal annealing.

FLX6 - 4 Flexible Field-Effect Transistors Based on a Liquid-14:25 Crystalline Semiconductor Fabricated by the Solution Shared-Deposition Method

M. Funahashi, F. Zhang^{*}, N. Tamaoki^{**}

Kagawa Univ., Japan *Chinese Ac. of Sci., China **Hokkaido Univ., Japan

Thin-film transistors based on Liquid-crystalline phenylterthiophene, 3-TTP-Ph-5 were fabricated with a solution-shared deposition method. The transistors on Si/SiO₂ substrates exhibit the field-effect mobility of the hole reached $8 \times 10^{-2} \text{ cm}^2 \text{V}^{-1} \text{s}^{-1}$ with the on/off ratio of 10^7 . The carrier mobility and the on/off ratio of the field-effect transistors fabricated on a polyimide films improved to be $5 \times 10^{-2} \text{ cm}^2 \text{V}^{-1} \text{s}^{-1}$ and 10^5 , respectively. Their carrier mobilities are retained when the strain reaches 3%.

----- Break -----

15:00 - 16	:00 Room 204		
FLX7/FMC6: Materials & Components for Flexible Displays			
Chair: Co-Chair:	T. Tomono, Toppan Printing, Japan T. Ogura, Nippon Steel, Japan		
FLX7/ FMC6 - 1 15:00	Transparent High Barrier Coating on Flexible Film Substrate by Roll to Roll PECVD System H. Tamagaki, T. Okimoto, T. Segawa Kobe Steel, Japan		

A new Roll to Roll PECVD System, which generates plasma between a pair of rollers, is developed for the deposition of SiOx transparent high barrier coating on film. At SiOx deposition, the deposition rate of 900 nm-m/min and barrier performance (WVTR) below 5x10⁻⁴ g/m²day is demonstrated.

FLX

FLX7/	Robust Folding Structure for a Foldable Display
FMC6 - 2 15:20	HJ. Kwon, H. S. Shim, S. K. Kim, Y. T. Chun, I. S. Kee, S. Y. Lee

Samsung Advanced Inst. of Tech., Korea

Design and analysis of folding structure applied hyperelastic material for foldable display are described. This structure allows to realize extendable and foldable large display using conventional glass panels. From Finite Element Method (FEM) analysis and mechanical and optical experimental results, we can confirm the design of more stable folding structure.

FLX7/ FMC6 - 3 15:40	Direct Connection of LSI Chips to Polyethylene Naphthalate Using Au Cone Bump
	T. Shuto, N. Watanabe, A. Ikeda, T. Higashimachi [*] , T. Asano
	Kyushu Univ., Japan *Sojo Univ., Japan

We show that the direct connection of LSI chip to PEN (polyethylene naphthalate) film can be realized by using Au cone bump for flexible display. More than 10,000 connections at 20 μ m pitch with low resistance can be realized at 150 °C.

Author Interviews 18:00 – 19:00

Friday, December 3

9:00 - 12:0	00 Poster/A.I. Room	
Poster FLXp: Flexible Materials and Devices		
FLXp - 1	High Performance Nanocrystalline Silicon Thin Film Transistors: Mechanical Device Reliability	
	HC. Lin, HS. Dai, KY. Ho, CC. Hsu, SY. Peng, CW. Lin, PF. Lee, CH. Cheng, BC. Kung, WY. Chao, JY. Yan, HC. Cheng	
	ITRI, Taiwan	

High performance nanocrystalline silicon thin film transistors (nc-Si TFTs) on polyimide (PI) substrate are demonstrated successfully. Mechanical reliability of nc-Si TFTs on PI shows an excellent characteristic than hydrogenated amorphous silicon (a-Si:H) TFTs. The TFT density of state proves that the shallow-level or deep-level defects originate from different bending directions.

FLXp - 2 Characteristics Improvement for Flexible a-Si:H Thin Film Transistor with Post Treatment Processes

L.-F. Teng, P.-T. Liu, Y.-T. Chou, Y.-S. Fan Nat. Chiao Tung Univ., Taiwan

The performances of flexible a-Si:H TFTs on stainless foil with and without silicon nitride passivation layer were discussed in this study. The experiment results indicated the reliability of a-Si:H TFTs with passivation layer under mechanical strains was improved. That's related to the hydrogen passivating effect during deposition and post-annealing process.

FLXp - 3 Flexible Ferroelectric-TFTs Using IGZO-Channel and P(VDF-TrFE)

G.-G. Lee, S.-M. Yoon^{*}, J.-W. Yoon, Y. Fujisaki^{**}, H. Ishiwara, E. Tokumitsu

Tokyo Inst. of Tech., Japan ^{*}ETRI, Korea ^{**}Hitachi, Japan

We report on the fabrication of a-IGZO-based flexible nonvolatile memory TFTs with P(VDF-TrFE) ferroelectric polymer on the PEN substrate. Excellent device performances, such as the field effect mobility of 7.1 cm²V¹s⁻¹, the subthreshold swing of 200 mV/dec, and drain current on/off ratio of more than 10^5 were confirmed.

FLXp - 4 Color Shift Analysis of Reflective Flexible Display on Bending Conditions

S.-C. Liao, B.-J. Wen ITRI, Taiwan

The purpose of this study is to analyze the color shift of the reflectivetype cholesteric liquid crystal display (Ch-LCD). Under different radius of curvature by using a flexible-characteristic inspection system with an adjustable light source is presented in this paper. The color shift behaviors of reflective flexible display were discussed.

FLXp - 5 Moisture Permeability of Coating Film on Stainless Steel Foil

N. Yamada, T. Ogura, S. Ito, K. Nose Nippon Steel, Japan

OLEDs fabricated on glass substrates were encapsulated with coated and non-coated stainless steel foils followed by accelerated shelf life test in order to estimate the moisture permeation of the coating film. HP-coated stainless steel foil showed the lowest moisture permeation among the three coated stainless steel foils.

FLX

FLXp - 6 Aluminum Oxide Layer Formation via PEALD for Enhancement of Barrier Properties of Plastic Substrates

J. S. Jang, H. G. Kim, S. S. Kim Kyung Hee Univ., Korea

Aluminum oxide layers were successfully deposited on plastic substrates via plasma enhanced atomic layer deposition (PEALD) process using trimethylaluminum (TMA) and oxygen Several process parameters in PEALD process were optimized. Thin and densely packed aluminum oxide layers deposited via PEALD showed the potentials as promising barrier coating layers for substrates.

FLXp - 7 Colorless Polyimide Substrate for Flexible Display

G. H. Kim, W. J. Lee, J.-Y. Cai^{*}, K.-H. Choi^{*} ETRI, Korea ^{*}KITECH, Korea

Transparent colorless polyimide (C. PI) substrate for flexible display was developed. In order to explore the performance and processability of this substrate, flexible LCDs were fabricated and their characteristics were investigated.

FLXp - 8 Spraying Conductive Transparent Layer on Flexible Thermal-Resistant Substrate

W.-M. Chou, H. H. Yu, H. -H. Lin Nat. Formosa Univ., Taiwan

Polyarylate (PAR) substrate was prepared by hot pressing, and then a conductive polypyrrole (PPy) layer was deposited on its surface by chemical in-situ polymerization. Different temperatures were controlled for PPy preparation. The optical transmittance and surface resistivity of the PPy layers for different polymerization times and reaction temperatures were compared.

FLXp - 9 Stable Flexible Organic Thin Film Transistor with Self-Assembled Monolayers Surface Treatment

C. L. Liao, C. C. Chou, C. W. Liu, K. Y. Chiang, C. Y. Leu, J. M. Ding, J. P. Hu ITRI, Taiwan

We deposited self-assembled monolayers by simple spin-coating technique onto gas barrier/PEN substrate. Spin-cast SAMs had ultra smooth crystalline surface and provided an excellent surface for organic thin film transistors. In fact on the SAM treated gas barrier, OTFT showed mobility of 1.42 x 10^{-2} cm²/Vs and excellent bias stress stability.

FLXp - 10 A Low-Temperature and Highly Reproducible Fabrication Process for High-Mobility Solution-Processed Small Molecule Field-Effect Transistors

T. Endo^{*}, T. Nagase^{*,**}, T. Kobayashi^{*,**}, K. Takimiya^{***}, M. Ikeda^{****,****}, H. Naito^{*,**}

*Osaka Pref. Univ., Japan **The Res. Inst. for Molecular Elect. Devices, Japan ***Hiroshima Univ., Japan ***Nippon Kayaku, Japan ****Ctr. for Organic Photonics & Elect. Res., Japan

A simple, low-temperature, and reproducible fabrication process of di octylbenzothienobenzothiophene top-gate field-effect transistors has been reported. A total of 116 devices exhibit high mobilities of 1.59 \pm 0.40 cm²/Vs, low threshold voltages of -1.48 \pm 3.02 V, and excellent electrical stability against a 10⁴-s-duration gate-bias stress of -1.2 MV/ cm.

FLXp - 11 Electrical Characteristics of Flexible Organic Thin-Film Transistors under Bending Conditions

F.-C. Chen, T.-D. Chen Nat. Chiao Tung Univ., Taiwan

The electrical properties of flexible organic thin-film transistors fabricated on stainless steel substrates were measured under different bending conditions. We found that the compressive strain resulted in an increased mobility while the tensile strain leaded to a decreased one. The strains probably influenced the barrier height between the pentacene grains.

FLXp - 12 Chemical In-Situ Polymerization of Polypyrrole on Transparent Conductive Flexible Polyarylate Substrate

H. H. Yu, S.-C. Huang, H.-F. Lee, W.-M. Chou Nat. Formosa Univ., Taiwan

High optical transmittance, high thermal-resistant and anti-ultraviolet radiation Polyethersulfone (PES) substrate was prepared by hotmelting and thermal annealing process. Single-walled carbon nanotubes (SWCNTs) were dispersed separately with jelly fig pectin solution under sonication first, and then sprayed on PES surface as the conductive transparent layer.

FLXp - 13 New Method for Detecting Permeation Pass Way of Thin Film Encapsulation

J. K. Lee, J. S. Kim, C. K. Yoo, S. Y. Yoon, C. D. Kim, Y. K. Hwang, I. J. Chung LG Display, Korea

We research relations between O/AI ratio and barrier properties of aluminum oxide which has been deposited with varying process voltage controlled reactive sputtering conditions. A new method, using photoluminescence material for detecting defects, is introduced here to evaluate barrier characteristics, especially sizes or density of defects in the barrier layer.

FLXp - 14L Annealing Effect of Low Temperature (< 150 °C) Cat-CVD Gate Dielectric Silicon Nitride Films Diluted With Atomic Hydrogen

K.-S. Keum, K.-M. Lee, J. D. Hwang, Y.-J. Lee, K.-S. No, W.-S. Hong Univ. of Seoul, Korea

We fabricated silicon nitride (SiN_x) films for gate dielectric layers at low temperature (< 150°C) by Cat-CVD system. in-situ annealing was performed without vacuum breaking after SiN_x films depositon. Samples were annealed by oven. As a result, including hydrogen samples show more effective dielectric properties improvement.

FLXp - 15L Characteristics of Silicon Nanocrystals Embedded in the Silicon Nitride Films Deposited by PE-CVD at a Low Temperature

J.-D. Hwang, K.-S. Keum, Y.-J. Lee, K.-M. Lee, S. Jang, M. Han, W.-S. Hong

Univ. of Seoul, Korea

Silicon nitride (SiNx) films prepared by PECVD technique at a low temperature (200 °C). Controlling the gas mixing ratio, $R = [N_2]/[SiH_4]$, and the plasma power can be composition parameter, X, varied from 0.83 to 1.62. Photoluminescence (PL) spectra of these films revealed existence of nano-sized silicon particles.

IDW '11

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Nagoya Congress Center Nagoya, Japan

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Topical Session on Touch Panels and Input Technologies

Wednesday, December 1

13:20 - 14:40		Room 502
	INP1: Touch Panel (1)	

Chair: C. J. Brown, Sharp Labs. of Europe, UK Co-Chair: T. Nakamura, Toshiba Mobile Display, Japan

INP1 - 1: *Invited* In-Cell Touch Panels: A Review of 13:20 Technologies and Applications

C. J. Brown Sharp Labs. of Europe, UK

In recent years touch panels have become a standard feature of portable electronic devices ranging from mobile phones to tablet PCs. In this paper we review the recent progress of in-cell capacitance and optical type touch panel technologies and summarize their prospects in the near future.

INP1 - 2Read-Out Circuit Employing Varying Reference13:40Voltage for Capacitive Touch-Screen

K. Gwak, Y.-S. Jang, S.-G. Lee KAIST, Korea

A new capacitance measuring circuit based on a constant current charging method for a touch-screen read-out is proposed. The method employs a linearly varying reference voltage to a comparator to increase the sensitivity and noise immunity. An 8bit architecture is implemented and proved by simulation with 0.13 um technology.

INP1 - 3A Novel Embedded Touch Display with Integrated14:00Chip Solution

S.-Z. Peng, C.-C. Chan, S.-H. Huang, H.-H. Chen, W.-T. Tseng, C.-R. Lee

Chunghwa Picture Tubes, Taiwan

We propose a novel embedded capacitive touch display with sensing display driver (SDD) IC solution to improve TSP performances. Our novel design is not only integrated touch function and TFT driver into one chip, but also embedded touch panel into display. This novel design is raised up product competition.

INP1 - 4: Invited In-Cell Capacitive Type Touch Sensor Using 14:20 LTPS TFT-LCD Technology

T. Nakamura, S. Tomita

Toshiba Mobile Display, Japan

We discuss in-cell light sensor technologies and describe an LTPS TFT-LCD with in-cell capacitive type touch sensors which amplify voltage change caused by capacitive coupling between the sensor electrode and an input object (user's finger).

----- Break -----

15:00 - 16:20

Room 502

INP2: Touch Panel (2)

Chair: S. Yoon, LG Display, Korea Co-Chair: H. Haga, NEC LCD Techs., Japan

INP2 - 1:InvitedThe Golden Age of Touch Digital life on15:00One's Fingertip

S. Yoon

LG Display, Korea

Touch has been certainly popularized. None of touch technologies is yet perfect but it can be said pretty much matured. But in the other hand, touch at present is only the first step and next step should focus on improving natural human interface.

INP2 - 2 Low Cost Multi-touch Embedded System

15:20 C.-L. Li, J.-S. Liao, H.-H. Chen, W.-T. Tseng, C.-R. Lee Chunghwa Picture Tubes, Taiwan

Chunghwa Picture Tubes, LTD. (CPT) sets up a low-cost multi-touch embedded system that all software and drivers are free except the hardware of this platform. And in this system, multi-touch function is implemented using resistive multi-touch panel. It is satisfied with the result of the operating efficiency of this platform.

INP2 - 3Subjective Analysis on Touch Screen Panel Tapping15:40Properties

J.-H. Lu, Y.-W. Fang, K.-S. Wang, J.-Y. Lee AU Optronics, Taiwan

For verifying the tapping forces on touch screen panels (TSP), we conducted subjective experiments. Tapping forces, surface properties of TSPs and styluses were investigated. Based on the experimental results, the tapping model of TSP could be established.

INP2 - 4 Low Cost and Easy Manufacturing Flexible 16:00 Projective Capacitive Touch Sensing Film C. J. Liu, G. R. Hu, Y. J. Chen, C. J. Tsai, M. H. Wang,

P. H. Wang, W. J. Chiang, C. P. Kung, J. C. Ho, C. C. Lee ITRI. Taiwan

An easy process of high quality of projective capacitive touch sensing film is developed by transparence polymer insulating film with patterning ability, high quality and bendable ITO with low resistance, colorless polyimide substrate with thickness less than $30\mu m$. It costs low by less process time, less expansive equipment.

Author Interviews

18:00 - 19:00

Thursday, December 2

13:20 - 14	:40 Room 413	
INP3: Imaging System		
Chair: Co-Chair:	J. Tanida, Osaka Univ., Japan S. Itoh, Shizuoka Univ., Japan	
INP3 - 1: 13:20	Invited The Impact of a New Camera-System for Medical-Use on the Display Technologies	
	Y. Ide	
	Pixera, USA	

No manuscript was submitted.

INP3 - 2: Invited A Super Hi-Vision Camera Using Three 13:40 33-M-pixel CMOS Image Sensors

- T. Yamashita, R. Funatsu, T. Yanagi^{*}, K. Mitani,
- T. Yoshida^{*}, Y. Nojiri

NHK, Japan ^{*}Hitachi Kokusai Elec., Japan

We developed world's-first camera system that can capture fullresolution Super Hi-Vision images (7680×4320/59.94p, R/G/B-4:4:4). For this system, we also developed a 33-million-pixel CMOS image sensor, an ultra-high-resolution lens, and a signal-processing for correcting lens chromatic aberration in real time. As a result, the limiting resolution was achieved 4,320 TV lines.

INP3 - 3:InvitedMulti-Dimensional Data Acquisition Using a14:00Compound-Eye Imaging System

J. Tanida, R. Horisaki, K. Kagawa Osaka Univ., Japan

Effective methods for multi-dimensional data acquisition are developed using a compound-eye imaging system. The images captured by ommatidia contain multi-dimensional information of the object, and proper processing extracts the information. As applications related to multi-dimensional data acquisition, long-distance observation, focus extension, and generalized sampling are presented.

INP3 - 4A 5-bit qVGA CMOS Image Sensor for Optical14:20Sensor Array in OLED-on-Silicon (OLEDoS)

K. Min, D. Lee^{*}, C. Yoo Univ. of Hanyang, Korea ^{*}Hynix Semiconductor, Korea

An optical sensor array and its readout circuit for OLED-on-silicon (OLEDoS) are described. A qVGA optical sensor array is implemented on a 0.4 inch VGA OLED pixel array in a 0.18 um CMOS process. A 5-bit single-slope analog-to-digital converter with delta reset scheme is adopted for optical sensor readout circuits.

----- Break -----

15:00 - 16:20

Room 413

INP4: 3D Interactive System

Chair: T. Komuro, Univ. of Tokyo, Japan Co-Chair: N. Hashimoto, Citizen, Japan

INP4 - 1: Invited Vision-Based 3D Input Interface Technologies

T. Komuro

Univ. of Tokyo, Japan

Vision-based user interfaces are technologies where human motion is detected by a camera or cameras and is used as input. In this paper we describe advantages and disadvantages, technological issues, and related research of vision-based user interfaces as well as examples of 3D input interface systems that we developed.

INP4 - 2: Invited Tactile Interaction with 3D Images

15:20 H. Shinoda

Univ. of Tokyo, Japan

In this talk, our project on non-contact tactile display is introduced. Radiation pressure by convergent airborne ultrasound beams produces tactile sensations on bare skins, without installing bulky mechanical arms or forcing people to hold/wear special devices. Combining the tactile display with 3D images, we can realize literally touchable 3D images.

INP4 - 3:InvitedA system for Holographic Display without15:40Interference Measurement

K. Nitta

Kobe Univ., Japan

A three-dimensional (3D) image system based on multi vision imaging and wavefront reconstruction is reported. One of the features in our research is to use graphic processing units (GPU) for signal processing. It is shown that the GPU is effective for large scale information processing required in the 3D system.

INP4 - 4:InvitedHigh Density Directional Ray Scan System16:00for Autostereoscopic Displays

Y. Momonoi, M. Sekine^{*}, T. Saishu^{*}, Y. Yamauchi^{*} Toshiba Visual Prods., Japan ^{*}Toshiba, Japan

We introduce a newly developed prototype of a ray scan system for an autostereoscopic display system. This system synthesizes various 3-D images to acquire high-density multiple light rays. One application of this system is capture of birds-eye-view photographic content suitable for a flatbed autostereoscopic display.

Author Interviews 18:00 – 19:00

Asia Display 2011

Kunshan, China

IDW Tutorial in Japanese

Tuesday, November 30, 2010 Room 412 Fukuoka International Congress Center

Detailed information is announced at http://www.sidchapters.org/japan/

Topical Session on Lighting Optics, Devices and Systems

Wednesday, December 1

13:20 - 14	l:25 Room 409
	LIT1: LED Light Source Technologies
Chair:	K. Käläntär, LEIZ Advanced Tech., Japan
Co-Chair:	K. Hara, Shizuoka Univ., Japan
LIT1 - 1:	Invited Recent Developments and Future Prospects
13:20	of LED Technologies for Displays and General

Lighting H. Amano

Nagoya Univ., Japan

An overview of the progress of GaN-based blue light emitting diode (LED) chips will be discussed. Several groundbreaking technologies by which various efficiencies were considerably improved will be shown. In addition, recent progress of UV/DUV LEDs and future prospects of the progress of visible long-wavelength LEDs will be explained.

LIT1 - 2Integration of Imprinting with Rellector for13:45Designing High Efficiency Street-Lamp Module

J.-W. Pan, S.-H. Tu^{*}, C.-W. Fan, S.-H. Lin, J.-Y. Huang, C.-S. Wang

Nat. Chiao Tung Univ., Taiwan ^{*}Genesis Photonics, Taiwan

A cost effective, high throughput, and high yield method for street lamp was proposed in this paper. We integrated the imprinting technology and the reflective optical element to improve the conventional street lamp. The novel design has 40% enhancement in illumination intensity, the uniform illumination and the glare effect elimination.

LIT1 - 3 Withdrawn

LIT1 - 4 Withdrawn

LIT1 - 5L Photoconductivity in Silicon Rich Silicon Nitride 14:05 Films Containing Silicon Nanocrystals Prepared by Catalytic CVD

K.-M. Lee^{*}, J.-D. Hwang^{*}, Y.-J. Lee^{*}, K.-S. Kuem^{*}, K.-S. No^{*}, K. S. Yoon^{**}, S. H. Yang^{**}, W.-S. Hong^{*} ^{*}Univ. of Seoul, Korea ^{**}Samsung Elect., Korea

We fabricated metal-insulator-semiconductor (MIS) capacitors and p-i-n diodes using silicon rich silicon nitride (SRSN) film containing silicon nanocrystals (Si NCs) prepared by catalytic chemical vapor deposition (Cat-CVD). Photo/dark current difference and photo/dark hysterisis appeared in the current-voltage (I-V) and the capacitancevoltage (C-V) curves, respectively.

----- Break -----

15:00 - 16:20

Room 409

LIT2: Backlight

Chair:K. Käläntär, LEIZ Advanced Tech., JapanCo-Chair:M. Shinohara, Omron, JapanOrganizer:FMC-WS

LIT2 - 1Ultra-Slim 7-in. Light-Guide Plate using Roll-to-Roll15:00UV Embossing Process

Y.-Y. Chang, G.-H. Liu^{*}, C.-J. Ting, T.-H. Lin, C.-L. Fu, H.-H. Lin, J.-H. Tsai

ITRI, Taiwan *Epoch Chemtronics, Taiwan

We proposed a 7-in. ultra-slim LGP fabricated by R2R UV embossing process which has the advantage of high throughput and high microstructural transfer rate. The surface plasma treatment is applied to enhance the adhesion. A 0.42 mm prototype with outcoupling etching-dots is achieved with its uniformity more than 70%.

LIT2 - 2 Highly-Collimating Backlighting Systems with 15:20 Multi-Stacked and Multi-Layered Optical Sheets

Y.-Y. Chang, T.-H. Lin, C.-L. Fu, C.-F. Lan, R.-H. Tsai, H.-H. Lin, J.-H. Tsai ITRI, Taiwan

We proposed a highly-collimating backlighting system with multistacked optical sheets. The optical components can be fabricated by ultra-precision diamond tooling and UV embossing. A best FWHM of 6 degree is realizable in an optimized manufacturing process.

LIT2 - 3 Thermal Network Analysis of Edge-Type LED 15:40 Backlight

K. Misono

Miyakonojo Nat. College of Tech., Japan

We developed a thermal network model of edge-type LED backlight. The effects of various design parameters of the backlight on the junction temperature of LED were analyzed by using the L18 orthogonal array. The important design parameters to reduce the junction temperature were clarified.

LIT2 - 4 Analysis of Luminous Flux Measuring Methods for 16:00 Flat Lightings

E. Lee, S.-J. Choi, J.-W. Bae, O.-K. Song, S. Lee, H.-K. Chung Samsung Mobile Display, Korea

R&D for so-called eco-friendly lightings like OLED lamps is rapidly progressing. New devices having flat-panel-shape require different measuring method from conventional ones. Several different measuring methods are analyzed for finding appropriate method for flat lightings. The analysis will be helpful to evaluate and standardize measuring method for flat lightings.

Author Interviews 18:00 – 19:00

Thursday, December 2

10:40 - 11	:50 Room 413	Room 413
	LIT3: Phosphors for Lighting	
Chair: Co-Chair: Organizer:	K. Ohmi, Tottori Univ., Japan R. J. Xie, NIMS, Japan PH-WS	
LIT3 - 1: 10:40	Invited Preparation and Luminescence of Novel Oxysulfide Phosphors for White Light LEDs	
	TM. Chen, TW. Kuo	

Nat. Chiao Tung Univ., Taiwan

Two unprecedented phosphors, CaZnOS:Eu²⁺ and Sr₈Al₁₂O₂₄S₂:Eu²⁺, were prepared and investigated. The PL spectra of both reveal a broad emission band extending from 550 to 700 nm under blue light pumping. Both phosphors exhibit superior luminescence stability than SrS:Eu²⁺ in thermal quenching up to 120°C and great potential for LED application.

Room 409

LIT3 - 2 Luminance Improvement of EL Devices Using 11:10 ZnS-Phosphors Sintered by Vacuum Microwave Process

N. Taguchi, S. Horiguchi^{*}, Y. Uraoka^{*} Image Tech, Japan ^{*}Nara Inst. of S&T, Japan

We improved the luminance of EL devices using ZnS phosphors sintered by the new microwave method that original ZnS powders were previously given mechanical damages to enhance the diffusion of activators inside ZnS. The EL devices dispersed with other inorganic phosphors gave more enhanced luminance and change of luminescent color.

LIT3 - 3 Electric Field Effect by Using Thermal Annealing 11:30 Process for Inorganic Electroluminescent Devices

Y.-H. Chien, K.-F. Chen, C.-C. Chang, M.-Y. Chuang, J.-C. Ho, Y.-Y. Chang, C.-C. Lee, F.-H. Wang^{*}, C.-S. Ho^{*} ITRI, Taiwan ^{*}Nat. Chung Hsing Univ., Taiwan

This work proposes a novel inorganic electroluminescent (IEL) device with a built-in electric charge (BIEC) layer which is called EFBI-PDEL device. Using thermal anneal process to improve device performance under same driving condition: reduce turn-on voltage form 80 V to 35 V, increase brightness form 269.2 nits to 397.3 nits.

----- Lunch -----

13:20 - 14:25 R LIT4: Solid State Projection Light Source

 Chair:
 P. Rudy, Kaai, USA

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 K. Takeda, Seiko Epson, Japan

 Organizer:
 PRJ-WS

 LIT4 - 1:
 Invited State-of-the-Art Continuous-Wave InGaN

 13:20
 Laser Diodes in the Violet, Blue, and Green

 Wavelength Regimes
 J. W. Raring, M. C. Schmidt, C. Poblenz, Y.-C. Chang, B. Li, M. Mondry, R. Craig, P. Rudy, J. S. Speck, S. P. DenBaars, S. Nakamura

Soraa, USA

We present state-of-the-art performance from green, blue, and violet InGaN laser diodes fabricated on nonpolar and semipolar GaN substrates. Using these novel orientations, we demonstrate high power, high efficiency, continuouswave operation from single-lateral-mode electrically pumped laser diodes from 405 nm to 525 nm, including over 60 mW at 520 nm.

LIT4 - 2 Withdrawn

LIT4 - 3 RGB Laser Light Source Module with High 14:05 Efficiency for Large Screen Projectors

A. Furukawa, K. Takahashi, K. Murakami, Y. Maeda, M. Oka^{*}, K. Kimura^{*}, T. Mochizuki^{*}, M. Suzuki^{*}, N. Eguchi^{*} Sony Manufacturing Syss., Japan ^{*}Sony, Japan

A compact and high power laser module with output of 10, 6, and 5 watts for the red green and blue wavelengths has been developed. The very high efficiency of 18% in electro-optical conversion ratio makes it an attractive light source in substitution to xenon lamps for large screen projectors.

Author Interviews

18:00 - 19:00

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The 18th International Display Workshops

December 7-9, 2011

Nagoya Congress Center Nagoya, Japan

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Date	1F Lobby	Main Hall	Room 204	Room 402	Room 409	Room 412	Room 413	Room 501	Room 502	Poster/A.I. Room	2F Lobby 4F Lobby							
Tue., Nov. 30	Registration 17:00-20:00		Evening Get-Together with Wine at RACONTER (1F) 18:00-20:00															
		Opening, Keynote Address 10:20-11:15																
		Invited Address 11:15-12:00																
			1		Lu	nch												
nber 1	Registration 8:00-18:00	OLED1 13:20-14:50	FLX1 13:20-14:30		LIT1 13:20-14:25	VHF1 13:20-14:50			INP1 13:20-14:40	LCTp								
acer					Br	eak	1	1		PRJp	Exhibition							
day, Di		OLED2 15:00-16:10	FLX2 15:00-16:25	PRJ1 15:00-16:25	LIT2 15:00-16:20	VHF2 15:00-16:20	PH1 15:00-16:40	AMD1 15:00-16:25	INP2 15:00-16:20	13:20-16:20	12:00-18:00							
lnes					Br	eak												
Wec		OLED3 16:40-18:05	FLX3/EP1 16:40-18:00		FMC1 16:40-18:00	VHF3 16:40-18:10		AMD2 16:40-17:40	LCT1 16:40-18:05									
			k.							Author Interviews 18:00-19:00								
					Br	eak				11								
				Ba	inquet at the Crow	ne Grand Ball Roo 19:30	om (2F) in ANA Cr -21:30	owne Plaza Fukuc	ka									
	Registration 8:00-18:00	EP2	FLX4/OLED4	MEET1	PRJ2	3D1	PH2	AMD3	LCT2									
		9:00-10:15	9:00-10:15	9:00-10:25	9:00-10:20	9:00-10:20	9:00-10:10	9:00-10:20	9:00-10:25	FMCp VHFp								
		EP3	FLX5/AMD4	MEET2	PRJ3	3D2	LIT3	OLED5	LCT3	DESp 9:00-12:00								
N		10.40-11.55	10.40-12.10	10.40-12.13	Lu	nch	10.40-11.50	10.40-11.50	10.40*11.55									
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ursday,		EP5 15:00-16:30	FLX7/FMC6 15:00-16:00	MEET4 15:00-16:20	PRJ4 14:50-16:25	VHF5/DES2 15:00-16:20	INP4 15:00-16:20	PDP2 15:00-16:20	LCT5 15:00-16:10	3Dp 13:20-16:20								
Thu					Br	eak												
		EP6 16:40-18:00	PDP5 17:00-18:00	MEET5 16:40-17:55	PRJ5 16:35-18:00	VHF6 16:40-18:00	3D3/DES3 16:40-18:00	AMD5/OLED6 16:40-18:05	PH3 16:40-17:50									
		EP7 9:00-10:25	LCT6 9:00-10:20	FED1 9:00-10:00	FMC2 9:00-10:20		DES4 9:00-10:00	AMD6 9:00-10:10	VHF7 9:00-10:15	PDPp								
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ŝ	8:00-13:00		LCT7 10:40-11:55	FED2 10:40-12:10	FMC3 10:40-12:00		DES5 10:40-12:00	AMD7 10:40-12:00	VHF8/3D4 10:40-12:10	9:00-12:00	Exhibition							
mbe					Lu	nch					10:00-14:00							
Dece				FED3 13:20-14:40	FMC4 13:20-14:40	PDP3 13:00-14:40	DES6 13:20-14:40	AMD8 13:20-14:40	3D5 13:20-14:40									
iday,					Br	eak												
Ē				FED4 15:00-15:40	FMC5 15:00-16:20	PDP4 15:00-16:20	DES7 15:00-16:25	AMD9 15:00-16:05	3D6 15:00-16:20									
			1							Author Interviews 16:20-17:20								

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	Leastion		We	dnesday, Dec. 1			Thursday, Dec. 2						Friday, Dec. 3					
	Location	10:20-12:00		PM	PM 18:0		A	M		PM		18:00-19:00	A	M	P	M	16:20-17:20	
Keynote	Main Hall	Opening, Keynote &																
& invited	Boom 204	Invited Addresses											Nanostructured I.C.	New I CD Design				
	D 500				Photo Alignment		High Performance		High Performance	Emerging LC			Nanostructured EO	New LOD Design				
LCT	Room 502				Technology		LC Technology	New Functional LCDs	LCDs	Application								
	Poster/A.I. Room		Pos	ters		A.I.						A.I.					A.I.	
	Room 204							*Flexible Active-Matrix										
					System on Panel			Devices								Nanodevice		
1	Room 501			AM-LCD	& Sensing Device		SITET				*AM-OLED		Organic & Carbon TFT	Oxide TFT (1)	Oxide TFT (2)	& Oxide TFT		
	Poster/A.I. Room					A.I.			Pos	ters		A.I.					A.I.	
FMC	Room 204									*Materials & Components for Elevible Displays								
													Manufacturing	Manufacturing				
	Room 409				Optical Films								Technologies (1)	Technologies (2)	Materials (1)	Materials (2)		
	Poster/A.I. Room					A.I.	Pos	ters				A.I.					A.I.	
	Room 204										Protective Layer				Link Efficience	Desta sting Lange		
PDP	Room 412								Panel Configuration	Picture Quality					High Efficiency	Protective Layer		
	Poster/A L Boom								Tanel Comgutation	T loture Quality		AI	Pos	ters			AI	
	Room 413			Phosphors in General			Phosphors for LEDs					/					7	
РН	Boom 502										Emissive Displays &							
	1100111 302										Phosphors							
	Poster/A.I. Hoom					A.I.			Pos	ters		A.I.	EED: 0 DUUs	Field Fusitions (4)	Field Freitters (0)	Field Fasittees (0)		
FED	Room 402												FEDS & BLUS	Field Emitters (1)	Field Emitters (2)	Field Emitters (3)	A 1	
OLED	FUSIEI/A.I. HOUIII		OLED Keynote	OLED Soluble	OLED Display												A.I.	
	Main Hall		& Materials	Technologies	Applications													
	Room 204						*Flexible OLED											
	Room 501							OLED Device			*AM-OLED							
	Poster/A.I. Room					A.I.		reennoiogies	Pos	ters		A.I.						
	Boom 412						Holography & 3D	3D Display (1)										
	1100111412						Display	SD Display (1)										
3D	Room 413										Content							
	Room 502													*3D Human Factors	3D Image Quality	3D Display (2)		
	Poster/A.I. Room								Pos	ters		A.I.					A.I.	
	Room 412		Lightness Perception	Color Perception	Color Reproduction				*Multi Primary (1)	*Multi Primary (2)	Moving Image Quality							
VHF	Boom E02		5								& Backlight System		Diaplay Human Eastern	*2D Human Eastara				
	Poster/A L Boom					AI	Pos	ters				AI	Display Human Factors	SD Human Factors			AI	
	Room 402			Illumination Systems		7						,					7	
	Boom 409			-			New Projection	Pico-Projectors		Laser Projection &	Digital Signage &							
Filo	1100111 403						Applications			Despeckling Tech.	Large Venue Projectors							
	Poster/A.I. Hoom		Pos	ters		A.I.	Electrophoratio	Color Electrophoretia	Frantiar Bassarah for	Electrophromio		A.I.						
	Main Hall						Displays	Displays	e-Paper	Displays	Cholesteric LCDs		Electrowetting & LCDs					
EP	Room 204				*Flexible Electronic Paper													
	Poster/A.I. Room		Pos	ters		A.I.		_			-	A.I.					A.I.	
L	Room 402						Emerging Technologies	Fundamental Components. Process	Optical MEMS &	Displays & Imaging	Fundamental Components, Process							
MEET								Technologies (1)	Device Technologies		Technologies (2)							
	Poster/A.I. Room											A.I.						
	Room 412								*Multi Primary (1)	*Multi Primary (2)								
DES	Room 413										Content		Display Electronics	Low Power Technology	Display Quality	Communication		
	Poster/A.I. Room						Pos	iters				A.I.					A.I.	
	Boom 204		Advanced Flexible	Printing Fabrication	*Flexible Electronic		*Elexible OLED	*Flexible Active-Matrix	Elexible Organic TET	*Materials & Components								
FLX	Pootor/A L Dec-		Display Technologies	Processes	Paper	A !	. IONDIO OLLO	Devices		tor Flexible Displays		A !		toro				
	Boom 413					A.I.			Imaging System	3D Interactive System		A.I.	Pos					
INP	Room 502		Touch Panel (1)	Touch Panel (2)					maging Gystelli	ob micractive Gystern								
	Poster/A.I. Room			(L)		A.I.						A.I.						
	Boom 409		LED Light Source	Backlight					Solid State Projection									
LIT	Deers 440		Technologies	Daokiigin				Dheenhere for Links	Light Source									
	Poster/A Poom					Δι		Priosphors for Lighting				Δ Ι						
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LUI: Work	snop on LC Scie	ence & rechnologies					VIT: WORKShop on A	ppilea vision & Huma	II FACIOIS				A.I.: AUTOR INTERVIEW	5				

LCT: Workshop on LC Science & Technologies

AMD: Workshop on Active Matrix Displays FMC: Workshop on FPD Manufacturing, Materials & Components

PDP: Workshop on Plasma Displays

PH: Workshop on EL Displays & Phosphors FED: Workshop on Field Emission Display & CRT

OLED: Workshop on Organic LED Displays 3D: Workshop on 3D/Hyper-Realistic Displays & Systems

VHF: Workshop on Applied Vision & Human Factors

PRJ: Workshop on Projection & Large-Area Displays & Their Components

EP: Workshop on Electronic Paper

MEET: Workshop on MEMS & Emerging Technologies for Future Displays & Devices

DES: Workshop on Display Electronic Systems

FLX: Workshop on Flexible Displays INP: Topical Session on Touch Panels & Input Technologies

LIT: Topical Session on Lighting Optics, Devices & Systems

*: Joint Session

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IDW '10 Final program